

STM32F205xx STM32F207xx

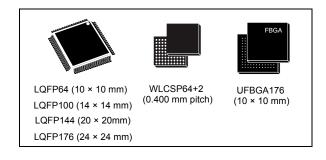
Arm®-based 32-bit MCU, 150 DMIPs, up to 1 MB Flash/128+4KB RAM, USB OTG HS/FS, Ethernet, 17 TIMs, 3 ADCs, 15 comm. interfaces and camera

Datasheet - production data

Features

- Core: Arm® 32-bit Cortex®-M3 CPU (120 MHz max) with Adaptive real-time accelerator (ART Accelerator™) allowing 0-wait state execution performance from Flash memory, MPU, 150 DMIPS/1.25 DMIPS/MHz (Dhrystone 2.1)
- Memories
 - Up to 1 Mbyte of Flash memory
 - 512 bytes of OTP memory
 - Up to 128 + 4 Kbytes of SRAM
 - Flexible static memory controller that supports Compact Flash, SRAM, PSRAM, NOR and NAND memories
 - LCD parallel interface, 8080/6800 modes
- Clock, reset and supply management
 - From 1.8 to 3.6 V application supply + I/Os
 - POR, PDR, PVD and BOR
 - 4 to 26 MHz crystal oscillator
 - Internal 16 MHz factory-trimmed RC
 - 32 kHz oscillator for RTC with calibration
 - Internal 32 kHz RC with calibration
- Low-power modes
 - Sleep, Stop and Standby modes
 - V_{BAT} supply for RTC, 20 × 32 bit backup registers, and optional 4 Kbytes backup **SRAM**
- 3 × 12-bit, 0.5 µs ADCs with up to 24 channels and up to 6 MSPS in triple interleaved mode
- 2 × 12-bit D/A converters
- General-purpose DMA: 16-stream controller with centralized FIFOs and burst support
- Up to 17 timers
 - Up to twelve 16-bit and two 32-bit timers, up to 120 MHz, each with up to four IC/OC/PWM or pulse counter and quadrature (incremental) encoder input
- Debug mode: Serial wire debug (SWD), JTAG, and Cortex®-M3 Embedded Trace Macrocell™

This is information on a product in full production.



- Up to 140 I/O ports with interrupt capability:
 - Up to 136 fast I/Os up to 60 MHz
 - Up to 138 5 V-tolerant I/Os
- Up to 15 communication interfaces
 - Up to three I²C interfaces (SMBus/PMBus)
 - Up to four USARTs and two UARTs (7.5 Mbit/s, ISO 7816 interface, LIN, IrDA, modem control)
 - Up to three SPIs (30 Mbit/s), two with muxed I²S to achieve audio class accuracy via audio PLL or external PLL
 - 2 × CAN interfaces (2.0B Active)
 - SDIO interface
- Advanced connectivity
 - USB 2.0 full-speed device/host/OTG controller with on-chip PHY
 - USB 2.0 high-speed/full-speed device/host/OTG controller with dedicated DMA, on-chip full-speed PHY and ULPI
 - 10/100 Ethernet MAC with dedicated DMA: supports IEEE 1588v2 hardware, MII/RMII

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- 8- to 14-bit parallel camera interface (48 Mbyte/s max.)
- CRC calculation unit
- 96-bit unique ID

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Table 1. Device summary

Reference	Part numbers
STM32F205xx	STM32F205RB, STM32F205RC, STM32F205RE, STM32F205RF, STM32F205RG STM32F205VB, STM32F205VC, STM32F205VE, STM32F205VF, STM32F205VG STM32F205ZC, STM32F205ZE, STM32F205ZF, STM32F205ZG
STM32F207xx	STM32F207IC, STM32F207IE, STM32F207IF, STM32F207IG STM32F207VC, STM32F207VE, STM32F207VF, STM32F207VG STM32F207ZC, STM32F207ZE, STM32F207ZF, STM32F207ZG



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Introduction STM32F20xxx

1 Introduction

This datasheet provides the description of the STM32F205xx and STM32F207xx lines of microcontrollers, based on Arm[®](a) cores. For more details on the whole STMicroelectronics STM32 family refer to Section 2.1: Full compatibility throughout the family.

The STM32F205xx and STM32F207xx datasheet must be read in conjunction with the STM32F20x/STM32F21x reference manual. They will be referred to as STM32F20x devices throughout the document.

For information on programming, erasing and protection of the internal Flash memory, refer to the STM32F20x/STM32F21x Flash programming manual (PM0059).

The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com*.

For information on the Cortex[®]-M3 core refer to the Cortex[®]-M3 Technical Reference Manual, available from the *www.arm.com* website.



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STM32F20xxx Description

2 Description

The STM32F20x family is based on the high-performance Arm[®] Cortex[®]-M3 32-bit RISC core operating at a frequency of up to 120 MHz. The family incorporates high-speed embedded memories (Flash memory up to 1 Mbyte, up to 128 Kbytes of system SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

The devices also feature an adaptive real-time memory accelerator (ART Accelerator™) that allows to achieve a performance equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 120 MHz. This performance has been validated using the CoreMark® benchmark.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers. a true number random generator (RNG). They also feature standard and advanced communication interfaces. New advanced peripherals include an SDIO, an enhanced flexible static memory control (FSMC) interface (for devices offered in packages of 100 pins and more), and a camera interface for CMOS sensors. The devices also feature standard peripherals.

- Up to three I²Cs
- Three SPIs, two I²Ss. To achieve audio class accuracy, the I²S peripherals can be clocked via a dedicated internal audio PLL or via an external PLL to allow synchronization.
- Four USARTs and two UARTs
- A USB OTG high-speed with full-speed capability (with the ULPI)
- A second USB OTG (full-speed)
- Two CANs
- An SDIO interface
- Ethernet and camera interface available on STM32F207xx devices only.

The STM32F205xx and STM32F207xx devices operate in the -40 to +105 °C temperature range from a 1.8 V to 3.6 V power supply. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD} , the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see *Section 3.16*).

A comprehensive set of power-saving modes enables the design of low-power applications.

STM32F205xx and STM32F207xx devices are offered in various packages, ranging from 64 to 176 pins. The set of included peripherals changes with the chosen device. These features make the STM32F205xx and STM32F207xx microcontroller family suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances

Figure 4 shows the general block diagram of the device family.



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Description STM32F20xxx

			able 2. \$	Table 2. STM32F205xx features and peripheral counts)5xx fea	atures ar	ıd peripl	neral co	unts						
Pei	Peripherals		•	STM32F205Rx	¥			STM32F205Vx	-205Vx			SI	STM32F205Zx	05Zx	
Flash memory in Kbytes	Kbytes	128	256	512	292	1024	128	256	512	292	1024	256	512	768 1	1024
SRAM in Kbytes	System (SRAM1+SRAM2)	64 (48+16)	96 (80+16)		128 (112+16)		64 (48+16)	96 (80+16)		128 (112+16)		96 (80+16))	128 (112+16)	
	Backup			4				4					4		
FSMC memory controller	ontroller			9 N						_	Yes ⁽¹⁾				
Ethernet							N								
	General-purpose						10								
	Advanced-control						2								
Timers	Basic						2								
	IWDG						Yes								
	WWDG						Yes								
RTC							Yes								
Random number generator	generator						Yes								
	SPI/(I ² S)						3/(2) ⁽²⁾	(2)							
	1 ² C						8								
USART Comm. interfaces UART	USART UART						4 2								
	USB OTG FS						Yes								
	USB OTG HS						Yes								
	CAN						2								
Camera interface							No								
GPIOs				51				82	2				114		
SDIO							Yes								
12-bit ADC							8								
Number of chann	els			16				16	9				24		
12-bit DAC Number of channels	els						Yes 2								
Maximum CPU frequency	equency						120 MHz	1Hz							
Operating voltage							1.8 V to 3.6 V ⁽³⁾	3.6 V ⁽³⁾							

Table 2. STM32F205xx features and peripheral counts (continued)

Peripherals		STM32F205Rx	×		STM32F205Vx	STM32F205Zx
Operation temperatures			Am	bient temperat	Ambient temperatures: –40 to +85 $^{\circ}$ C /–40 to +105 $^{\circ}$ C	
Operating terriper attal es			•	Junction te	Junction temperature: –40 to + 125 °C	
Package	F9d±07	LQFP64 WLCSP64+2	LQFP64	LQFP64 VLCSP64+2 LQFP64 WLCSP64+2	LQFP100	LQFP144

For the LQFP100 package, only FSMC Bank1 or Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package.

The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode. ۲, On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16). რ.

Table 3. STM32F207xx features and peripheral counts

		מטומ	2	32120	אא וכמו	ממש			iable o. o i Mozrzo/AA leatules allu pelipilelai coulits	ņ			
	Peripherals		STM33	STM32F207Vx			STM32	STM32F207Zx			STM32	STM32F2071x	
Flash memory in Kbytes	(bytes	256	512	892	1024	256	512	892	1024	256	512	292	1024
SRAM in Kbytes	System (SRAM1+SRAM2)							128 (112+16)	3 16)				
	Backup							4					
FSMC memory controller	ntroller							Yes ⁽¹⁾	1)				
Ethernet								Yes					
	General-purpose							10					
	Advanced-control							2					
Timers	Basic							2					
	IWDG							Yes					
	WWDG							Yes					
RTC								Yes	•				
Random number generator	Jenerator Tenerator							Yes					

Description STM32F20xxx

Table 3. STM32F207xx features and peripheral counts (continued)

	Peripherals	STM32F207Vx	STM32F207Zx	STM32F2071x
	SPI/(I ² S)		$3/(2)^{(2)}$	
	1 ² C		ဇ	
USART Comm. interfaces	USART UART		4 2	
	USB OTG FS		Yes	
	USB OTG HS		Yes	
	CAN		2	
Camera interface			Yes	
GPIOs		82	114	140
SDIO			Yes	
12-bit ADC			3	
Number of channe	ils	16	24	24
12-bit DAC Number of channels	Si		Yes 2	
Maximum CPU frequency	quency		120 MHz	
Operating voltage			1.8 V to 3.6 V ⁽³⁾	
Operation tempera	e in ince		Ambient temperatures: –40 to +85 $^{\circ}\text{C/}40$ to +105 $^{\circ}\text{C}$	/-40 to +105 °C
	מותופס		Junction temperature: -40 to + 125 °C	+ 125 °C
Package		LQFP100	LQFP144	LQFP176/ UFBGA176

For the LQFP100 package, only FSMC Bank1 or Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package.

The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode. ر ا

On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16). რ

STM32F20xxx Description

2.1 Full compatibility throughout the family

The STM32F205xx and STM32F207xx constitute the STM32F20x family, whose members are fully pin-to-pin, software and feature compatible, allowing the user to try different memory densities and peripherals for a greater degree of freedom during the development cycle.

The STM32F205xx and STM32F207xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F205xx and STM32F207xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F20x family remains simple as only a few pins are impacted.

Figure 1, Figure 2 and Figure 3 provide compatible board designs between the STM32F20x and the STM32F10xxx family.

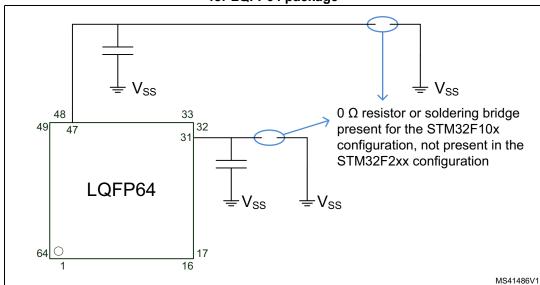


Figure 1. Compatible board design between STM32F10x and STM32F2xx for LQFP64 package

Description STM32F20xxx

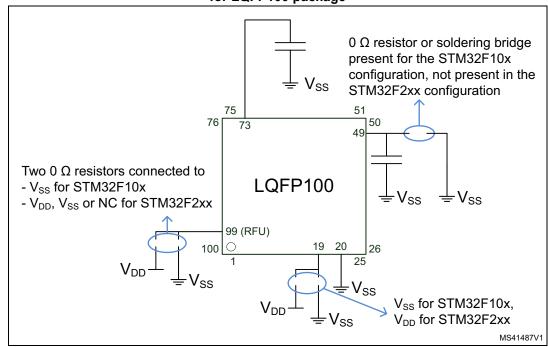
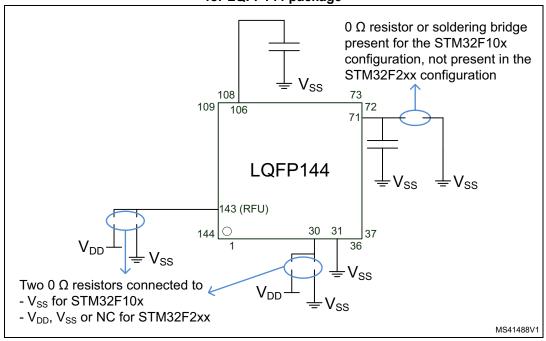


Figure 2. Compatible board design between STM32F10x and STM32F2xx for LQFP100 package

1. RFU = reserved for future use.

Figure 3. Compatible board design between STM32F10x and STM32F2xx for LQFP144 package



1. RFU = reserved for future use.

STM32F20xxx Description

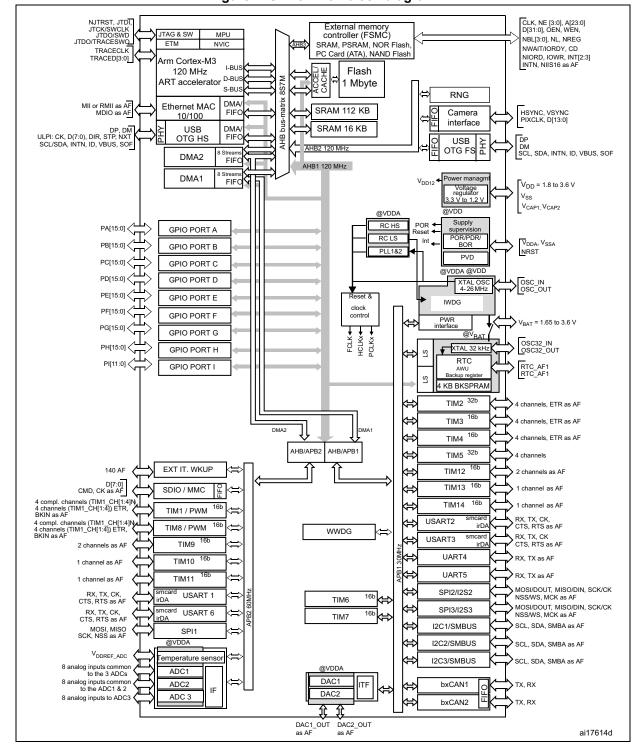


Figure 4. STM32F20x block diagram

- The timers connected to APB2 are clocked from TIMxCLK up to 120 MHz, while the timers connected to APB1 are clocked from TIMxCLK up to 60 MHz.
- 2. The camera interface and Ethernet are available only in STM32F207xx devices.

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3 Functional overview

3.1 Arm[®] Cortex[®]-M3 core with embedded Flash and SRAM

The Arm[®] Cortex[®]-M3 processor is the latest generation of processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The Arm[®] Cortex[®]-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an Arm core in the memory size usually associated with 8- and 16-bit devices.

With its embedded Arm[®] core, the STM32F20x family is compatible with all Arm[®] tools and software.

Figure 4 shows the general block diagram of the STM32F20x family.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard Arm® Cortex®-M3 processors. It balances the inherent performance advantage of the Arm® Cortex®-M3 over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher operating frequencies.

To release the processor full 150 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache which increases program execution speed from the 128-bit Flash memory. Based on CoreMark[®] benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 120 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

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3.4 Embedded Flash memory

The STM32F20x devices embed a 128-bit wide Flash memory of 128 Kbytes, 256 Kbytes, 512 Kbytes, 768 Kbytes or 1 Mbyte available for storing programs and data.

The devices also feature 512 bytes of OTP memory that can be used to store critical user data such as Ethernet MAC addresses or cryptographic keys.

3.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.6 Embedded SRAM

All STM32F20x products embed:

- Up to 128 Kbytes of system SRAM accessed (read/write) at CPU clock speed with 0 wait states
- 4 Kbytes of backup SRAM.

The content of this area is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

3.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS) and the slaves (Flash memory, RAM, FSMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.



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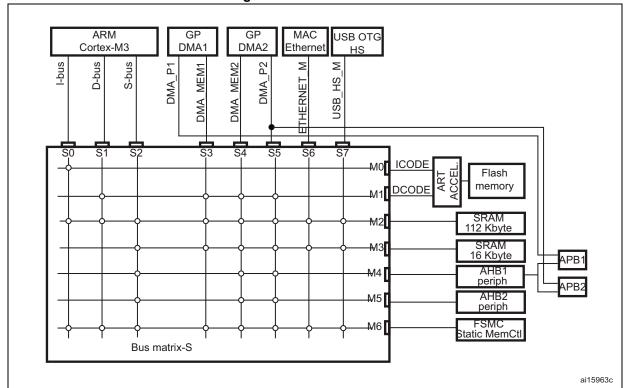


Figure 5. Multi-AHB matrix

3.8 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They share some centralized FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

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The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART and UART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Camera interface (DCMI)
- ADC.

3.9 Flexible static memory controller (FSMC)

The FSMC is embedded in all STM32F20x devices. It has four Chip Select outputs supporting the following modes: PC Card/Compact Flash, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- Write FIFO
- Code execution from external memory except for NAND Flash and PC Card
- Maximum frequency (f_{HCLK}) for external access is 60 MHz

LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

3.10 Nested vectored interrupt controller (NVIC)

The STM32F20x devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 81 maskable interrupt channels plus the 16 interrupt lines of the Cortex[®]-M3.

The NVIC main features are the following:

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.



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3.11 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 23 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 140 GPIOs can be connected to the 16 external interrupt lines.

3.12 Clocks and startup

On reset the 16 MHz internal RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).

The advanced clock controller clocks the core and all peripherals using a single crystal or oscillator. In particular, the ethernet and USB OTG FS peripherals can be clocked by the system clock.

Several prescalers and PLLs allow the configuration of the three AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the three AHB buses is 120 MHz and the maximum frequency the high-speed APB domains is 60 MHz. The maximum allowed frequency of the low-speed APB domain is 30 MHz.

The devices embed a dedicate PLL (PLLI2S) that allow them to achieve audio class performance. In this case, the I²S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

3.13 Boot modes

Downloaded from Arrow.com.

At startup, boot pins are used to select one out of three boot options:

- Boot from user Flash memory
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART1 (PA9/PA10), USART3 (PC10/PC11 or PB10/PB11), CAN2 (PB5/PB13), USB OTG FS in Device mode (PA11/PA12) through DFU (device firmware upgrade).

3.14 Power supply schemes

 V_{DD} = 1.8 to 3.6 V: external power supply for I/Os and the internal regulator (when enabled), provided externally through V_{DD} pins. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates



in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16).

- V_{SSA}, V_{DDA} = 1.8 to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock, 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Refer to Figure 19: Power supply scheme for more details.

3.15 Power supply supervisor

The devices have an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry.

At power-on, POR/PDR is always active and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default BOR threshold levels, or to disable BOR permanently. Three BOR thresholds are available through option bytes.

The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit. On devices in WLCSP64+2 package, the BOR, POR and PDR features can be disabled by setting IRROFF pin to V_{DD} . In this mode an external power supply supervisor is required (see *Section 3.16*).

The devices also feature an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.16 Voltage regulator

The regulator has five operating modes:

- Regulator ON
 - Main regulator mode (MR)
 - Low-power regulator (LPR)
 - Power-down
- Regulator OFF
 - Regulator OFF / internal reset ON
 - Regulator OFF / internal reset OFF

3.16.1 Regulator ON

The regulator ON modes are activated by default on LQFP packages. On WLCSP64+2 package, they are activated by connecting both REGOFF and IRROFF pins to V $_{\rm SS}$, while only REGOFF must be connected to V $_{\rm SS}$ on UFBGA176 package (IRROFF is not available).

V_{DD} minimum value is 1.8 V.



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There are three power modes configured by software when the regulator is ON:

- MR is used in the nominal regulation mode
- LPR is used in Stop modes
 - The LP regulator mode is configured by software when entering Stop mode.
- Power-down is used in Standby mode.

The Power-down mode is activated only when entering Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost).

Two external ceramic capacitors must be connected on V_{CAP_1} and V_{CAP_2} pin. Refer to Figure 19: Power supply scheme and Table 16: VCAP1/VCAP2 operating conditions.

All packages have the regulator ON feature.

3.16.2 Regulator OFF

This feature is available only on packages featuring the REGOFF pin. The regulator is disabled by holding REGOFF high. The regulator OFF mode allows to supply externally a V12 voltage source through $V_{CAP\ 1}$ and $V_{CAP\ 2}$ pins.

The two 2.2 μ F ceramic capacitors must be replaced by two 100 nF decoupling capacitors. Refer to *Figure 19: Power supply scheme*.

When the regulator is OFF, there is no more internal monitoring on V12. An external power supply supervisor must be used to monitor the V12 of the logic power domain. PA0 pin must be used for this purpose, and act as power-on reset on V12 power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset the part of the 1.2 V logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used at power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection at reset or pre-reset is required.

Regulator OFF / internal reset ON

On WLCSP64+2 package, this mode is activated by connecting REGOFF pin to V_{DD} and IRROFF pin to V_{SS} . On UFBGA176 package, only REGOFF must be connected to V_{DD} (IRROFF not available). In this mode, V_{DD}/V_{DDA} minimum value is 1.8 V.

The regulator OFF / internal reset ON mode allows the user to supply externally a 1.2 V voltage source through V_{CAP} 1 and V_{CAP} 2 pins, in addition to V_{DD} .

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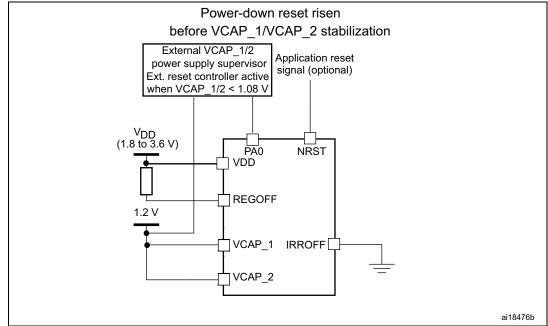


Figure 6. Regulator OFF / internal reset ON

The following conditions must be respected:

- V_{DD} must always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach 1.08 V is faster than the time for V_{DD} to reach 1.8 V, then PA0 must be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach 1.08 V and until V_{DD} reaches 1.8 V (see *Figure 8*).
- Otherwise, If the time for V_{CAP_1} and V_{CAP_2} to reach 1.08 V is slower than the time for V_{DD} to reach 1.8 V, then PA0 must be asserted low externally (see *Figure 9*).
- If V_{CAP_1} and V_{CAP_2} go below 1.08 V and V_{DD} is higher than 1.8 V, then a reset must be asserted on PAO pin.

Regulator OFF / internal reset OFF

On WLCSP64+2 package, this mode activated by connecting REGOFF to V_{SS} and IRROFF to V_{DD} . IRROFF cannot be activated in conjunction with REGOFF. This mode is available only on the WLCSP64+2 package. It allows to supply externally a 1.2 V voltage source through V_{CAP_1} and V_{CAP_2} pins. In this mode, the integrated power-on reset (POR)/ power-down reset (PDR) circuitry is disabled.

An external power supply supervisor must monitor both the external 1.2 V and the external V_{DD} supply voltage, and must maintain the device in reset mode as long as they remain below a specified threshold. The V_{DD} specified threshold, below which the device must be maintained under reset, is 1.8 V. This supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.



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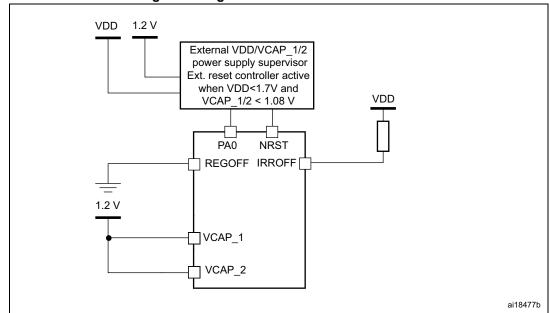


Figure 7. Regulator OFF / internal reset OFF

The following conditions must be respected:

- V_{DD} must always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains (see *Figure 8*).
- PA0 must be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach 1.08 V, and until V_{DD} reaches 1.7 V.
- NRST must be controlled by an external reset controller to keep the device under reset when V_{DD} is below 1.7 V (see Figure 9).

In this mode, when the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled.
- The brownout reset (BOR) circuitry is disabled.
- The embedded programmable voltage detector (PVD) is disabled.
- V_{BAT} functionality is no more available and V_{BAT} pin must be connected to VDD.

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PDR=1.8 V

1.2 V

1.08 V

PA0 tied to NRST

time

ai18473b

Figure 8. Startup in regulator OFF: slow V_{DD} slope, power-down reset risen after V_{CAP-1}/V_{CAP-2} stabilization

1. This figure is valid whatever the internal reset mode (ON or OFF).

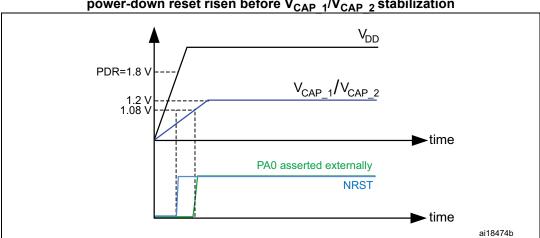


Figure 9. Startup in regulator OFF: fast V_{DD} slope, power-down reset risen before $V_{CAP\ 1}/V_{CAP\ 2}$ stabilization

3.16.3 Regulator ON/OFF and internal reset ON/OFF availability

Regulator OFF / Regulator ON / Regulator OFF / **Package** internal reset ON internal reset OFF internal reset ON LQFP64 LQFP100 Yes No No LQFP144 LQFP176 Yes Yes Yes WLCSP 64+2 REGOFF set to $V_{\mbox{\scriptsize DD}}$ REGOFF set to $V_{\mbox{\footnotesize SS}}$ REGOFF and IRROFF set to V_{SS} and IRROFF set to V_{SS} and IRROFF set to V_{DD} Yes Yes UFBGA176 No REGOFF set to V_{SS} REGOFF set to V_{DD}

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

3.17 Real-time clock (RTC), backup SRAM and backup registers

The backup domain of the STM32F20x devices includes:

- The real-time clock (RTC)
- 4 Kbytes of backup SRAM
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Its main features are the following:

- Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 day of the month.
- Programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes.
- It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.
- Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 µs to every 36 hours.
- A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.

The 4-Kbyte backup SRAM is an EEPROM-like area. It can be used to store data which need to be retained in VBAT and standby mode. This memory area is disabled to minimize power consumption (see *Section 3.18: Low-power modes*). It can be enabled by software.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see Section 3.18: Low-power modes).

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or the V_{BAT} pin.

3.18 Low-power modes

The STM32F20x family supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Stop mode

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC



and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in Low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup.

Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped when the device enters the Stop or Standby mode.

3.19 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery or an external supercapacitor.

V_{BAT} operation is activated when V_{DD} is not present.

The VBAT pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT} , external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When using WLCSP64+2 package, if IRROFF pin is connected to V_{DD} , the V_{BAT} functionality is no more available and V_{BAT} pin must be connected to V_{DD} .

3.20 Timers and watchdogs

The STM32F20x devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

Table 5 compares the features of the advanced-control, general-purpose and basic timers.

Table 5. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	compare	Complementary output	Max interface clock	Max timer clock
Advanced- control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	60 MHz	120 MHz

Table 5. Timer feature comparison (continued)

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary output	Max interface clock	Max timer clock
General	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	30 MHz	60 MHz
purpose	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	30 MHz	60 MHz
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	30 MHz	60 MHz
General purpose	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	60 MHz	120 MHz
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	60 MHz	120 MHz
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	30 MHz	60 MHz
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	30 MHz	60 MHz

3.20.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The TIM1 and TIM8 counters can be frozen in debug mode. Many of the advanced-control timer features are shared with those of the standard TIMx timers which have the same architecture. The advanced-control timer can therefore work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

3.20.2 General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F20x devices (see *Table 5* for differences).

TIM2, TIM3, TIM4, TIM5

The STM32F20x include 4 full-featured general-purpose timers. TIM2 and TIM5 are 32-bit timers, and TIM3 and TIM4 are 16-bit timers. The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.

The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

The counters of TIM2, TIM3, TIM4, TIM5 can be frozen in debug mode. Any of these general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from one to four hall-effect sensors.

TIM10, TIM11 and TIM9

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10 and TIM11 feature one independent channel, whereas TIM9 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

TIM12, TIM13 and TIM14

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM13 and TIM14 feature one independent channel, whereas TIM12 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers.

They can also be used as simple time bases.

3.20.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.

3.20.4 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout



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management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.20.5 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.20.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

3.21 Inter-integrated circuit interface (I²C)

Up to three I²C bus interfaces can operate in multimaster and slave modes. They can support the Standard- and Fast-modes. They support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

3.22 Universal synchronous/asynchronous receiver transmitters (UARTs/USARTs)

The STM32F20x devices embed four universal synchronous/asynchronous receiver transmitters (USART1, USART2, USART3 and USART6) and two universal asynchronous receiver transmitters (UART4 and UART5).

These six interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to communicate at speeds of up to 7.5 Mbit/s. The other available interfaces communicate at up to 3.75 Mbit/s.

USART1, USART2, USART3 and USART6 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.

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Max baud rate in Mbit/s SPI APB Standard Modem **Smartcard** irDA Name LIN features (RTS/CTS) (ISO 7816) master Oversampling Oversampling mapping by 16 by 8 APB2 (max. Х Х USART1 Χ Х Х Х 7.5 60 MHz) USART2 Χ Χ Х Х Х Χ 1.87 Χ Χ Χ Х **USART3** Х Χ APB1 (max. 3.75 30 MHz) UART4 Χ Χ Х UART5 Χ Χ Χ 3.75 APB2 (max. **USART6** Χ Χ Χ Χ Χ Χ 7.5 60 MHz)

Table 6. USART feature comparison

3.23 Serial peripheral interface (SPI)

The STM32F20x devices feature up to three SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1 can communicate at up to 30 Mbits/s, while SPI2 and SPI3 can communicate at up to 15 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

3.24 Inter-integrated sound (I²S)

Two standard I²S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, in half-duplex communication modes, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I²S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I2Sx interfaces can be served by the DMA controller.

3.25 SDIO

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit. The interface allows data transfer at up to 48 MHz in 8-bit mode, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.



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In addition to SD/SDIO/MMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

3.26 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

Peripheral available only on STM32F207xx devices.

The STM32F207xx devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for Ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The STM32F207xx requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). the PHY is connected to the STM32F207xx MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) or 50 MHz (RMII) output from the STM32F207xx.

The STM32F207xx includes the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors (see the STM32F20x and STM32F21x reference manual for details)
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes (4 Kbytes in total)
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

3.27 Controller area network (CAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). The 256 bytes of SRAM which are allocated for each CAN are not shared with any other peripheral.

3.28 Universal serial bus on-the-go full-speed (OTG_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and



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with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator. The major features are:

- Combined Rx and Tx FIFO size of 320 × 35 bits with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 4 bidirectional endpoints
- 8 host channels with periodic OUT support
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed in case bus-powered devices are connected
- Internal FS OTG PHY support

3.29 Universal serial bus on-the-go high-speed (OTG_HS)

The STM32F20x devices embed a USB OTG high-speed (up to 480 Mbit/s) device/host/OTG peripheral. The USB OTG HS supports both full-speed and high-speed operations. It integrates the transceivers for full-speed operation (12 Mbyte/s) and features a UTMI low-pin interface (ULPI) for high-speed operation (480 Mbit/s). When using the USB OTG HS in HS mode, an external PHY device connected to the ULPI is required.

The USB OTG HS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock generated by a PLL connected to the HSE oscillator. The main features are:

- Combined Rx and Tx FIFO size of 1024× 35 bits with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 6 bidirectional endpoints
- 12 host channels with periodic OUT support
- Internal FS OTG PHY support
- External HS or HS OTG operation supporting ULPI in SDR mode. The OTG PHY is connected to the microcontroller ULPI port through 12 signals. It can be clocked using the 60 MHz output.
- Internal USB DMA
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed when bus-powered devices are connected

3.30 Audio PLL (PLLI2S)

The devices feature an additional dedicated PLL for audio I²S application. It allows to achieve error-free I²S sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

The PLLI2S configuration can be modified to manage an I²S sample rate change without disabling the main PLL (PLL) used for CPU, USB and Ethernet interfaces.

The audio PLL can be programmed with very low error to obtain sampling rates ranging from 8 kHz to 192 kHz.



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> In addition to the audio PLL, a master clock input pin can be used to synchronize the I2S flow with an external PLL (or Codec output).

3.31 Digital camera interface (DCMI)

The camera interface is not available in STM32F205xx devices.

STM32F207xx products embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain up to 27 Mbyte/s at 27 MHz or 48 Mbyte/s at 48 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw Bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

3.32 True random number generator (RNG)

All STM32F2xxx products embed a true RNG that delivers 32-bit random numbers produced by an integrated analog circuit.

3.33 **GPIOs** (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain. with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O alternate function configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

To provide fast I/O handling, the GPIOs are on the fast AHB1 bus with a clock up to 120 MHz that leads to a maximum I/O toggling speed of 60 MHz.

3.34 ADCs (analog-to-digital converters)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

Downloaded from Arrow.com.

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The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the timers TIM1, TIM2, TIM3, TIM4, TIM5 and TIM8 can be internally connected to the ADC start trigger and injection trigger, respectively, to allow the application to synchronize A/D conversion and timers.

3.35 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 12-bit monotonic output
- left or right data alignment in 12-bit mode
- · synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{RFF+}

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

3.36 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.8 and 3.6 V. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part must be used.

3.37 Serial wire JTAG debug port (SWJ-DP)

The Arm SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.



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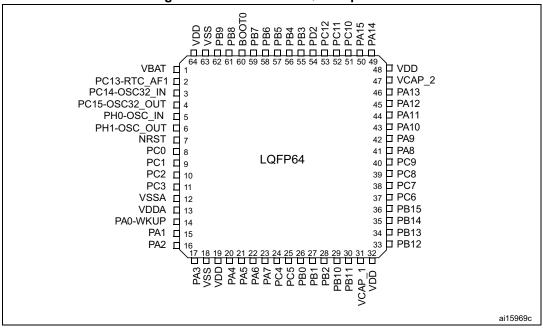
3.38 Embedded Trace Macrocell™

The Arm Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F20x through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

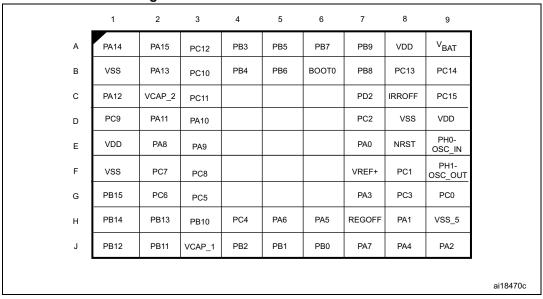
4 Pinouts and pin description

Figure 10. STM32F20x LQFP64 pinout



1. The above figure shows the package top view.

Figure 11. STM32F20x WLCSP64+2 ballout



1. The above figure shows the package top view.

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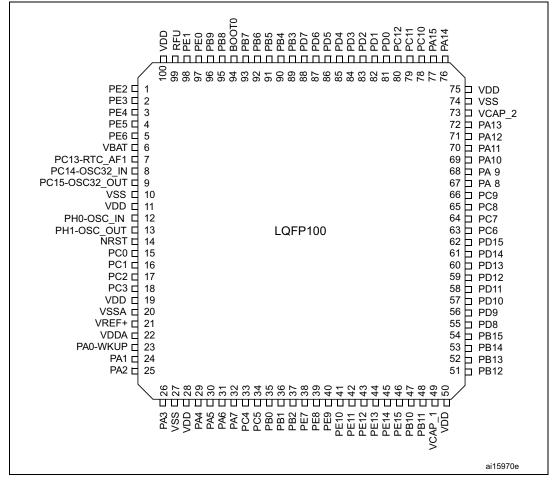


Figure 12. STM32F20x LQFP100 pinout

- 1. RFU means "reserved for future use". This pin can be tied to V_{DD} , V_{SS} or left unconnected.
- 2. The above figure shows the package top view.

4

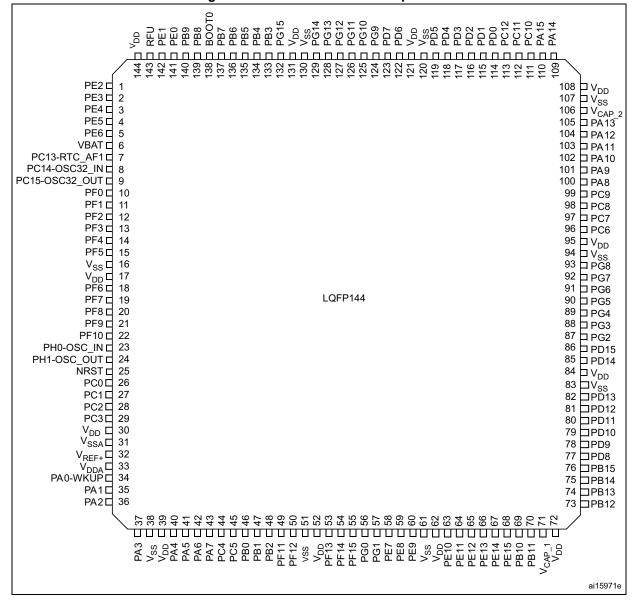


Figure 13. STM32F20x LQFP144 pinout

- 1. RFU means "reserved for future use". This pin can be tied to V_{DD},V_{SS} or left unconnected.
- 2. The above figure shows the package top view.

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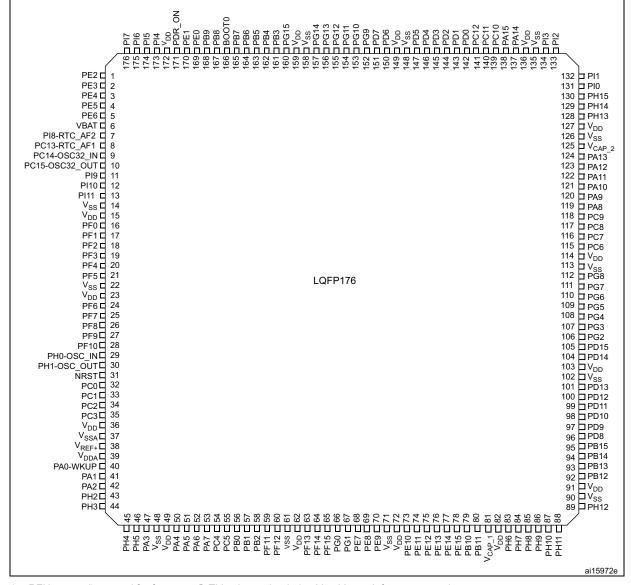


Figure 14. STM32F20x LQFP176 pinout

- 1. RFU means "reserved for future use". This pin can be tied to V_{DD} , V_{SS} or left unconnected.
- 2. The above figure shows the package top view.

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2 11 12 13 14 15 PA13 PE3 PE2 PB8 PG14 PG13 PB4 PB3 PC12 PA15 PE1 PE0 PB5 PD7 PA14 В PE4 PE5 PE6 PB9 PB7 PB6 PG15 PG12 PG11 PG10 PD0 PC11 PC10 PA12 PD6 PI2 С VBAT PI7 PI6 PI5 VDD RFU VDD VDD VDD PG9 PD5 PD1 PI3 PA11 PC13-PI4 PD2 PI9 VSS воото VSS VSS VSS PD4 PH15 PA10 D PD3 PI1 TAMP2 PC14-PI10 PI11 PH13 PH14 PA9 Е PI0 PC15-osc32_out VDD VSS VSS VSS VSS VSS VCAP_2 PC9 VSS PH2 VSS PA8 PH0vss G VSS VDD РН3 VSS VSS VSS VDD PC8 PC7 VSS VSS OSC_IN PH1-PF1 PH4 VSS VSS VSS VSS VSS VSS VDD PG8 PC6 OSC_OUT NRST PF3 PF4 PH5 VSS VDD PG7 PG6 VSS VSS VSS VSS VDD PF7 PF5 VDD VSS VSS VSS VSS VSS PH12 PG5 PG4 PG3 REGOF PF10 PH10 PD15 PF9 PF8 PG2 PH11 PB2 VSS VSS VCAP_1 М VSSA PC0 PC1 PC2 PC3 PG1 PH6 PH8 PH9 PD14 PD13 PA0-WKUP PD12 VREF-PC4 PF13 VDD PE13 PD10 Ν PA1 PA4 PG0 VDD VDD PH7 PD11 PF12 VREF+ PA6 PC5 PF15 PE14 PB13 PD8 PA2 PA5 PE8 PE9 PE11 PB12 PD9 VDDA PA3 PA7 PB1 PB0 PF11 PF14 PE7 PE10 PE12 PE15 PB10 PB11 PB14 PB15 ai17293c

Figure 15. STM32F20x UFBGA176 ballout

- 1. RFU means "reserved for future use". This pin can be tied to V_{DD} , V_{SS} or left unconnected.
- 2. The above figure shows the package top view.

Table 7. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition				
Pin name		specified in brackets below the pin name, the pin function during and after as the actual pin name				
	S	Supply pin				
Pin type	I	Input only pin				
	I/O	Input/ output pin				
	FT	5 V tolerant I/O				
I/O structure	TTa	3.3 V tolerant I/O				
I/O structure	В	Dedicated BOOT0 pin				
	RST	Bidirectional reset pin with embedded weak pull-up resistor				
Notes	Unless otherwise	specified by a note, all I/Os are set as floating inputs during and after reset				
Alternate functions	Functions selected	d through GPIOx_AFR registers				
Additional functions	Functions directly selected/enabled through peripheral registers					

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Table 8. STM32F20x pin and ball definitions

		Di	ns			14DIE 6. 31W32		•			
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	1	1	1	1	A2	PE2	I/O	FT	-	TRACECLK, FSMC_A23, ETH_MII_TXD3, EVENTOUT	-
-	-	2	2	2	A1	PE3	I/O	FT	-	TRACED0,FSMC_A19, EVENTOUT	-
-	1	3	3	3	B1	PE4	I/O	FT	-	TRACED1,FSMC_A20, DCMI_D4, EVENTOUT	-
-	-	4	4	4	B2	PE5	I/O	FT	-	TRACED2, FSMC_A21, TIM9_CH1, DCMI_D6, EVENTOUT	-
-	-	5	5	5	В3	PE6	I/O	FT	-	TRACED3, FSMC_A22, TIM9_CH2, DCMI_D7, EVENTOUT	•
1	Α9	6	6	6	C1	V_{BAT}	S		-	-	-
-	-	-	-	7	D2	PI8	I/O	FT	(3)(4)	EVENTOUT	RTC_AF2
2	В8	7	7	8	D1	PC13	I/O	FT	(3)(4)	EVENTOUT	RTC_AF1
3	В9	8	8	9	E1	PC14/OSC32_IN (PC14)	I/O	FT	(3)(4)	EVENTOUT	OSC32_IN ⁽⁵⁾
4	C9	9	9	10	F1	PC15-OSC32_OUT (PC15)	I/O	FT	(3)(4)	EVENTOUT	OSC32_OUT ⁽⁵⁾
-	-	-	-	11	D3	PI9	I/O	FT	-	CAN1_RX,EVENTOUT	-
-	1	-	-	12	E3	PI10	I/O	FT	-	ETH_MII_RX_ER, EVENTOUT	-
-	-	-	-	13	E4	PI11	I/O	FT	-	OTG_HS_ULPI_DIR, EVENTOUT	-
-	-	-	-	14	F2	V _{SS}	S		-	-	-
-	-	-	-	15	F3	V_{DD}	S		-	-	-
-	-	-	10	16	E2	PF0	I/O	FT	-	FSMC_A0, I2C2_SDA, EVENTOUT	-
-	-	-	11	17	Н3	PF1	I/O	FT	-	FSMC_A1, I2C2_SCL, EVENTOUT	-
-	-	-	12	18	H2	PF2	I/O	FT	-	FSMC_A2, I2C2_SMBA, EVENTOUT	-
-	-	-	13	19	J2	PF3	I/O	FT	(5)	FSMC_A3, EVENTOUT	ADC3_IN9
-	-	_	14	20	J3	PF4	I/O	FT	(5)	FSMC_A4, EVENTOUT	ADC3_IN14
-	-	_	15	21	K3	PF5	I/O	FT	(5)	FSMC_A5, EVENTOUT	ADC3_IN15
-	Н9	10	16	22	G2	V_{SS}	S	-	-	-	-



Table 8. STM32F20x pin and ball definitions (continued)

		Pi	ns			•				eminions (continued)	
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	11	17	23	G3	V_{DD}	S	-	-	-	-
-	,	-	18	24	K2	PF6	I/O	FT	(5)	TIM10_CH1, FSMC_NIORD, EVENTOUT	ADC3_IN4
-	1	ı	19	25	K1	PF7	I/O	FT	(5)	TIM11_CH1,FSMC_NREG, EVENTOUT	ADC3_IN5
-	,	-	20	26	L3	PF8	I/O	FT	(5)	TIM13_CH1, FSMC_NIOWR, EVENTOUT	ADC3_IN6
-	,	-	21	27	L2	PF9	I/O	FT	(5)	TIM14_CH1, FSMC_CD, EVENTOUT	ADC3_IN7
-	-	-	22	28	L1	PF10	I/O	FT	(5)	FSMC_INTR, EVENTOUT	ADC3_IN8
5	E9	12	23	29	G1	PH0/OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN ⁽⁵⁾
6	F9	13	24	30	H1	PH1/OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT ⁽⁵⁾
7	E8	14	25	31	J1	NRST	I/O		-	-	-
8	G9	15	26	32	M2	PC0	I/O	FT	(5)	OTG_HS_ULPI_STP, EVENTOUT	ADC123_ IN10
9	F8	16	27	33	МЗ	PC1	I/O	FT	(5)	ETH_MDC, EVENTOUT	ADC123_ IN11
10	D7	17	28	34	M4	PC2	I/O	FT	(5)	SPI2_MISO, OTG_HS_ULPI_DIR, ETH_MII_TXD2, EVENTOUT	ADC123_ IN12
11	G8	18	29	35	M5	PC3	I/O	FT	(5)	SPI2_MOSI, I2S2_SD, OTG_HS_ULPI_NXT, ETH_MII_TX_CLK, EVENTOUT	ADC123_ IN13
-	-	19	30	36	-	V_{DD}	S	-	-	-	-
12	-	20	31	37	M1	V _{SSA}	S	-	-	-	-
-		-	-		N1	V _{REF-}	S	-	-	-	-
-	F7	21	32	38	P1	V _{REF+}	S	_	-	-	-
13	-	22	33	39	R1	V_{DDA}	S	-	-		-
14	E7	23	34	40	N3	PA0-WKUP (PA0)	I/O	FT	(5)(6)	USART2_CTS, UART4_TX, ETH_MII_CRS, TIM2_CH1_ETR, TIM5_CH1, TIM8_ETR, EVENTOUT	ADC123_IN0, WKUP



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Table 8. STM32F20x pin and ball definitions (continued)

Pins Pins Pins Pins Pins Pins Pins Pins											
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
15	Н8	24	35	41	N2	PA1	I/O	FT	(5)	USART2_RTS, UART4_RX, ETH_RMII_REF_CLK, ETH_MII_RX_CLK, TIM5_CH2, TIM2_CH2, EVENTOUT	ADC123_IN1
16	J9	25	36	42	P2	PA2	I/O	FT	(5)	USART2_TX,TIM5_CH3, TIM9_CH1, TIM2_CH3, ETH_MDIO, EVENTOUT	ADC123_IN2
-	1	-	-	43	F4	PH2	I/O	FT	-	ETH_MII_CRS, EVENTOUT	-
-	-	-	-	44	G4	PH3	I/O	FT	-	ETH_MII_COL, EVENTOUT	-
-	-	-	-	45	H4	PH4	I/O	FT	-	I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	-
-	-	-	-	46	J4	PH5	I/O	FT	-	I2C2_SDA, EVENTOUT	-
17	G7	26	37	47	R2	PA3	I/O	FT	(5)	USART2_RX, TIM5_CH4, TIM9_CH2, TIM2_CH4, OTG_HS_ULPI_D0, ETH_MII_COL, EVENTOUT	ADC123_IN3
18	F1	27	38	48	-	V _{SS}	S	-	-	-	-
	H7				L4	REGOFF	I/O	-	-	-	-
19	E1	28	39	49	K4	V_{DD}	S	-	-	-	-
20	J8	29	40	50	N4	PA4	I/O	ТТа	(5)	SPI1_NSS, SPI3_NSS, USART2_CK, DCMI_HSYNC, OTG_HS_SOF, I2S3_WS, EVENTOUT	ADC12_IN4, DAC_OUT1
21	H6	30	41	51	P4	PA5	I/O	ТТа	(5)	SPI1_SCK, OTG_HS_ULPI_CK, TIM2_CH1_ETR, TIM8_CH1N, EVENTOUT	ADC12_IN5, DAC_OUT2
22	H5	31	42	52	P3	PA6	I/O	FT	(5)	SPI1_MISO, TIM8_BKIN, TIM13_CH1, DCMI_PIXCLK, TIM3_CH1, TIM1_BKIN, EVENTOUT	ADC12_IN6
23	J7	32	43	53	R3	PA7	I/O	FT	(5)	SPI1_MOSI, TIM8_CH1N, TIM14_CH1, TIM3_CH2, ETH_MII_RX_DV, TIM1_CH1N, ETH_RMII_CRS_DV, EVENTOUT	ADC12_IN7



Table 8. STM32F20x pin and ball definitions (continued)

		Pi	ns			•		Ф		, ,	
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
24	H4	33	44	54	N5	PC4	I/O	FT	(5)	ETH_RMII_RXD0, ETH_MII_RXD0, EVENTOUT	ADC12_IN14
25	G3	34	45	55	P5	PC5	I/O	FT	(5)	ETH_RMII_RXD1, ETH_MII_RXD1, EVENTOUT	ADC12_IN15
26	J6	35	46	56	R5	PB0	I/O	FT	(5)	TIM3_CH3, TIM8_CH2N, OTG_HS_ULPI_D1, ETH_MII_RXD2, TIM1_CH2N, EVENTOUT	ADC12_IN8
27	J5	36	47	57	R4	PB1	I/O	FT	(5)	TIM3_CH4, TIM8_CH3N, OTG_HS_ULPI_D2, ETH_MII_RXD3, TIM1_CH3N, EVENTOUT	ADC12_IN9
28	J4	37	48	58	M6	PB2/BOOT1 (PB2)	I/O	FT	-	EVENTOUT	-
-	-	-	49	59	R6	PF11	I/O	FT	-	DCMI_D12, EVENTOUT	-
-	-	1	50	60	P6	PF12	I/O	FT	1	FSMC_A6, EVENTOUT	-
-	-	-	51	61	M8	V _{SS}	S		-	-	-
-	1	1	52	62	N8	V_{DD}	S		1	-	-
-	-	1	53	63	N6	PF13	I/O	FT	1	FSMC_A7, EVENTOUT	-
-	-	1	54	64	R7	PF14	I/O	FT	1	FSMC_A8, EVENTOUT	-
-	-	1	55	65	P7	PF15	I/O	FT	-	FSMC_A9, EVENTOUT	-
-	-	ı	56	66	N7	PG0	I/O	FT	ı	FSMC_A10, EVENTOUT	-
-	-	ı	57	67	M7	PG1	I/O	FT	ı	FSMC_A11, EVENTOUT	-
-	-	38	58	68	R8	PE7	I/O	FT	ı	FSMC_D4,TIM1_ETR, EVENTOUT	-
-	-	39	59	69	P8	PE8	I/O	FT	ı	FSMC_D5,TIM1_CH1N, EVENTOUT	-
-	-	40	60	70	P9	PE9	I/O	FT	-	FSMC_D6,TIM1_CH1, EVENTOUT	-
-	_	-	61	71	M9	V _{SS}	S		-	-	-
-	-	-	62	72	N9	V_{DD}	S		-	-	-
-	-	41	63	73	R9	PE10	I/O	FT	ı	FSMC_D7,TIM1_CH2N, EVENTOUT	-
-	-	42	64	74	P10	PE11	I/O	FT	-	FSMC_D8,TIM1_CH2, EVENTOUT	-



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Table 8. STM32F20x pin and ball definitions (continued)

	Pins Pins Pins Pins Pin p										
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	,	43	65	75	R10	PE12	I/O	FT	-	FSMC_D9,TIM1_CH3N, EVENTOUT	-
-	-	44	66	76	N11	PE13	I/O	FT	-	FSMC_D10,TIM1_CH3, EVENTOUT	-
-	-	45	67	77	P11	PE14	I/O	FT	-	FSMC_D11,TIM1_CH4, EVENTOUT	-
-	-	46	68	78	R11	PE15	I/O	FT	-	FSMC_D12,TIM1_BKIN, EVENTOUT	-
29	НЗ	47	69	79	R12	PB10	I/O	FT	-	SPI2_SCK, I2S2_SCK, I2C2_SCL,USART3_TX,OT G_HS_ULPI_D3,ETH_MII_R X_ER,TIM2_CH3, EVENTOUT	-
30	J2	48	70	80	R13	PB11	I/O	FT	-	I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, ETH_RMII_TX_EN, ETH_MII_TX_EN, TIM2_CH4, EVENTOUT	-
31	J3	49	71	81	M10	VCAP_1	S		-	-	-
32	-	50	72	82	N10	V_{DD}	S		-	-	-
-	1	1	1	83	M11	PH6	I/O	FT	-	I2C2_SMBA, TIM12_CH1, ETH_MII_RXD2, EVENTOUT	-
-	-	1	-	84	N12	PH7	I/O	FT	-	I2C3_SCL, ETH_MII_RXD3, EVENTOUT	-
-	-	1	-	85	M12	PH8	I/O	FT	-	I2C3_SDA, DCMI_HSYNC, EVENTOUT	-
-	-	i	-	86	M13	PH9	I/O	FT	-	I2C3_SMBA, TIM12_CH2, DCMI_D0, EVENTOUT	-
-	-	-	-	87	L13	PH10	I/O	FT	-	TIM5_CH1, DCMI_D1, EVENTOUT	-
-	-	-	-	88	L12	PH11	I/O	FT	-	TIM5_CH2, DCMI_D2, EVENTOUT	-
-	-	-	-	89	K12	PH12	I/O	FT	-	TIM5_CH3, DCMI_D3, EVENTOUT	-
-	-	-	-	90	H12	V _{SS}	S	-	-	-	-
-	-	ı	-	91	J12	V_{DD}	S	ı	ı	-	



Table 8. STM32F20x pin and ball definitions (continued)

		Pi	ns			·		ø		,	
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
33	J1	51	73	92	P12	PB12	I/O	FT	1	SPI2_NSS, I2S2_WS, I2C2_SMBA, USART3_CK, TIM1_BKIN, CAN2_RX, OTG_HS_ULPI_D5, ETH_RMII_TXD0, ETH_MII_TXD0, OTG_HS_ID, EVENTOUT	-
34	H2	52	74	93	P13	PB13	I/O	FT	-	SPI2_SCK, I2S2_SCK, USART3_CTS, TIM1_CH1N, CAN2_TX, OTG_HS_ULPI_D6, ETH_RMII_TXD1, ETH_MII_TXD1, EVENTOUT	OTG_HS_ VBUS
35	H1	53	75	94	R14	PB14	I/O	FT	-	SPI2_MISO, TIM1_CH2N, TIM12_CH1, OTG_HS_DM USART3_RTS, TIM8_CH2N, EVENTOUT	-
36	G1	54	76	95	R15	PB15	I/O	FT	-	SPI2_MOSI, I2S2_SD, TIM1_CH3N, TIM8_CH3N, TIM12_CH2, OTG_HS_DP, RTC_50Hz, EVENTOUT	-
-	1	55	77	96	P15	PD8	I/O	FT	ı	FSMC_D13, USART3_TX, EVENTOUT	-
-	-	56	78	97	P14	PD9	I/O	FT	-	FSMC_D14, USART3_RX, EVENTOUT	-
-	-	57	79	98	N15	PD10	I/O	FT	-	FSMC_D15, USART3_CK, EVENTOUT	-
-	-	58	80	99	N14	PD11	I/O	FT	-	FSMC_A16,USART3_CTS, EVENTOUT	-
-	-	59	81	100	N13	PD12	I/O	FT	-	FSMC_A17,TIM4_CH1, USART3_RTS, EVENTOUT	-
-	-	60	82	101	M15	PD13	I/O	FT	-	FSMC_A18,TIM4_CH2, EVENTOUT	-
-	-	-	83	102	-	V_{SS}	S	-	-	-	-
-	-	-	84	103	J13	V_{DD}	S	-	-	-	-
-	-	61	85	104	M14	PD14	I/O	FT	1	FSMC_D0,TIM4_CH3, EVENTOUT	-
-	-	62	86	105	L14	PD15	I/O	FT	-	FSMC_D1,TIM4_CH4, EVENTOUT	-
-	-	-	87	106	L15	PG2	I/O	FT	-	FSMC_A12, EVENTOUT	-



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Table 8. STM32F20x pin and ball definitions (continued)

	64+2 100 144 176 suid							Φ		,	
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	88	107	K15	PG3	I/O	FT	-	FSMC_A13, EVENTOUT	-
-	-	-	89	108	K14	PG4	I/O	FT	-	FSMC_A14, EVENTOUT	-
-	-	-	90	109	K13	PG5	I/O	FT	-	FSMC_A15, EVENTOUT	-
-	-	-	91	110	J15	PG6	I/O	FT	-	FSMC_INT2, EVENTOUT	-
-	-	ı	92	111	J14	PG7	I/O	FT	-	FSMC_INT3, USART6_CK, EVENTOUT	-
-	-	ı	93	112	H14	PG8	I/O	FT	-	USART6_RTS, ETH_PPS_OUT, EVENTOUT	-
-	-	ı	94	113	G12	V _{SS}	S	-	-	-	-
-	-	-	95	114	H13	V_{DD}	S	-	-	-	-
37	G2	63	96	115	H15	PC6	I/O	FT	-	I2S2_MCK, TIM8_CH1, SDIO_D6, USART6_TX, DCMI_D0, TIM3_CH1, EVENTOUT	-
38	F2	64	97	116	G15	PC7	I/O	FT	-	I2S3_MCK, TIM8_CH2, SDIO_D7, USART6_RX, DCMI_D1, TIM3_CH2, EVENTOUT	-
39	F3	65	98	117	G14	PC8	I/O	FT	-	TIM8_CH3,SDIO_D0, TIM3_CH3, USART6_CK, DCMI_D2, EVENTOUT	-
40	D1	66	99	118	F14	PC9	I/O	FT	-	I2S2_CKIN, I2S3_CKIN, MCO2, TIM8_CH4, SDIO_D1, I2C3_SDA, DCMI_D3, TIM3_CH4, EVENTOUT	-
41	E2	67	100	119	F15	PA8	I/O	FT	-	MCO1, USART1_CK, TIM1_CH1, I2C3_SCL, OTG_FS_SOF, EVENTOUT	-
42	E3	68	101	120	E15	PA9	I/O	FT	-	USART1_TX, TIM1_CH2, I2C3_SMBA, DCMI_D0, EVENTOUT	OTG_FS_ VBUS
43	D3	69	102	121	D15	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, OTG_FS_ID,DCMI_D1, EVENTOUT	-
44	D2	70	103	122	C15	PA11	I/O	FT	-	USART1_CTS, CAN1_RX, TIM1_CH4,OTG_FS_DM, EVENTOUT	-



Table 8. STM32F20x pin and ball definitions (continued)

LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
45	C1	71	104	123	B15	PA12	I/O	FT	-	USART1_RTS, CAN1_TX, TIM1_ETR, OTG_FS_DP, EVENTOUT	-
46	B2	72	105	124	A15	PA13 (JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
47	C2	73	106	125	F13	VCAP_2	S	-	-	-	-
-	В1	74	107	126	F12	V _{SS}	S	-	-	-	-
48	A8	75	108	127	G13	V _{DD}	S	-	-	-	-
-	-	-	1	128	E12	PH13	I/O	FT	-	TIM8_CH1N, CAN1_TX, EVENTOUT	-
-	-	-	-	129	E13	PH14	I/O	FT	-	TIM8_CH2N, DCMI_D4, EVENTOUT	-
-	-	ı	1	130	D13	PH15	I/O	FT	-	TIM8_CH3N, DCMI_D11, EVENTOUT	-
-	-	ı	i	131	E14	PI0	I/O	FT	-	TIM5_CH4, SPI2_NSS, I2S2_WS, DCMI_D13, EVENTOUT	-
-	-	-	-	132	D14	PI1	I/O	FT	-	SPI2_SCK, I2S2_SCK, DCMI_D8, EVENTOUT	-
-	-	-	1	133	C14	Pl2	I/O	FT	-	TIM8_CH4,SPI2_MISO, DCMI_D9, EVENTOUT	-
-	-	i	i	134	C13	PI3	I/O	FT	-	TIM8_ETR, SPI2_MOSI, I2S2_SD, DCMI_D10, EVENTOUT	•
-	-	-	1	135	D9	V_{SS}	S	-	-	-	-
-	1	-	1	136	C9	V_{DD}	S	-	-	-	-
49	A1	76	109	137	A14	PA14 (JTCK-SWCLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
50	A2	77	110	138	A13	PA15 (JTDI)	I/O	FT	-	JTDI, SPI3_NSS, I2S3_WS,TIM2_CH1_ETR, SPI1_NSS, EVENTOUT	-
51	В3	78	111	139	B14	PC10	I/O	FT	-	SPI3_SCK, I2S3_SCK, UART4_TX, SDIO_D2, DCMI_D8, USART3_TX, EVENTOUT	-
52	C3	79	112	140	B13	PC11	I/O	FT	-	UART4_RX, SPI3_MISO, SDIO_D3, DCMI_D4,USART3_RX, EVENTOUT	-



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Table 8. STM32F20x pin and ball definitions (continued)

	Pins Pin name 9 11 1										
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
53	А3	80	113	141	A12	PC12	I/O	FT	-	UART5_TX, SDIO_CK, DCMI_D9, SPI3_MOSI, I2S3_SD, USART3_CK, EVENTOUT	-
-	-	81	114	142	B12	PD0	I/O	FT	-	FSMC_D2,CAN1_RX, EVENTOUT	-
-	-	82	115	143	C12	PD1	I/O	FT	-	FSMC_D3, CAN1_TX, EVENTOUT	-
54	C7	83	116	144	D12	PD2	I/O	FT	-	TIM3_ETR,UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
-	-	84	117	145	D11	PD3	I/O	FT	-	FSMC_CLK,USART2_CTS, EVENTOUT	-
-	-	85	118	146	D10	PD4	I/O	FT	-	FSMC_NOE, USART2_RTS, EVENTOUT	-
-	-	86	119	147	C11	PD5	I/O	FT	-	FSMC_NWE,USART2_TX, EVENTOUT	-
-	-	-	120	148	D8	V _{SS}	S	-	-	-	-
-	-	-	121	149	C8	V_{DD}	S	-	-	-	-
-	-	87	122	150	B11	PD6	I/O	FT	-	FSMC_NWAIT, USART2_RX, EVENTOUT	-
-	-	88	123	151	A11	PD7	I/O	FT	-	USART2_CK,FSMC_NE1, FSMC_NCE2, EVENTOUT	-
-	-	-	124	152	C10	PG9	I/O	FT	-	USART6_RX, FSMC_NE2,FSMC_NCE3, EVENTOUT	-
-	-	-	125	153	B10	PG10	I/O	FT	-	FSMC_NCE4_1, FSMC_NE3, EVENTOUT	-
-	-	-	126	154	В9	PG11	I/O	FT	-	FSMC_NCE4_2, ETH_MII_TX_EN, ETH_RMII_TX_EN, EVENTOUT	-
-	-	-	127	155	В8	PG12	I/O	FT	-	FSMC_NE4, USART6_RTS, EVENTOUT	-
-	-	-	128	156	A8	PG13	I/O	FT	-	FSMC_A24, USART6_CTS, ETH_MII_TXD0, ETH_RMII_TXD0, EVENTOUT	-



Table 8. STM32F20x pin and ball definitions (continued)

		Pi	ns							eminions (continued)	
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176 ⁽²⁾	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	1	-	129	157	A7	PG14	I/O	FT	-	FSMC_A25, USART6_TX, ETH_MII_TXD1, ETH_RMII_TXD1, EVENTOUT	-
-	-	-	130	158	D7	V_{SS}	S	-	-	-	-
-	-	-	131	159	C7	V _{DD}	S	-	-	-	-
-	-		132	160	B7	PG15	I/O	FT	1	USART6_CTS, DCMI_D13, EVENTOUT	-
55	A4	89	133	161	A10	PB3 (JTDO/TRACESWO)	I/O	FT	-	JTDO/ TRACESWO, SPI3_SCK, I2S3_SCK, TIM2_CH2, SPI1_SCK, EVENTOUT	-
56	B4	90	134	162	A9	PB4	I/O	FT	-	NJTRST, SPI3_MISO, TIM3_CH1, SPI1_MISO, EVENTOUT	-
57	A5	91	135	163	A6	PB5	I/O	FT	-	I2C1_SMBA, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT, TIM3_CH2, SPI1_MOSI, SPI3_MOSI, DCMI_D10, I2S3_SD, EVENTOUT	-
58	B5	92	136	164	В6	PB6	I/O	FT	-	I2C1_SCL,, TIM4_CH1, CAN2_TX, DCMI_D5,USART1_TX, EVENTOUT	-
59	A6	93	137	165	B5	PB7	I/O	FT	-	I2C1_SDA, FSMC_NL ⁽⁷⁾ , DCMI_VSYNC, USART1_RX, TIM4_CH2, EVENTOUT	-
60	В6	94	138	166	D6	BOOT0	1	В	-	-	V_{PP}
61	В7	95	139	167	A5	PB8	I/O	FT	-	TIM4_CH3,SDIO_D4, TIM10_CH1, DCMI_D6, ETH_MII_TXD3, I2C1_SCL, CAN1_RX, EVENTOUT	-
62	A7	96	140	168	B4	PB9	I/O	FT	-	SPI2_NSS, I2S2_WS, TIM4_CH4, TIM11_CH1, SDIO_D5, DCMI_D7, I2C1_SDA, CAN1_TX, EVENTOUT	-
-	-	97	141	169	A4	PE0	I/O	FT	-	TIM4_ETR, FSMC_NBL0, DCMI_D2, EVENTOUT	-



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Pins /O structure Pin type JFBGA176⁽²⁾ WLCSP64+2 Pin name LQFP176 LQFP100 LQFP144 Note **Additional** LQFP64 (function after **Alternate functions functions** reset)(1) FSMC NBL1, DCMI D3, 98 142 170 А3 PE1 I/O FT **EVENTOUT** D5 V_{SS} S _ _ D8 S 63 V_{SS} (8) 99 143 171 C6 **RFU** D9 100 144 172 S 64 C5 V_{DD} -TIM8_BKIN, DCMI_D5, I/O 173 Π4 PI4 FT **EVENTOUT** TIM8_CH1, DCMI_VSYNC, C4 PI5 I/O FT 174 **EVENTOUT** TIM8 CH2, DCMI D6, 175 C3 PI6 I/O FT **EVENTOUT** TIM8 CH3, DCMI D7, 176 C2 PI7 I/O FT **EVENTOUT** C8 **IRROFF** I/O -

Table 8. STM32F20x pin and ball definitions (continued)

- 1. Function availability depends on the chosen device.
- 2. For the UFBGA176 package F6, F7, F8, F9, F10, G6, G7, G8, G9, G10, H6, H7, H8, H9, H10, J6, J7, J8, J9, J10, K6, K7, K8, K9 and K10 are connected to V_{SS} , for heat dissipation and package mechanical stability.
- 3. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited: the speed should not exceed 2 MHz with a maximum load of 30 pF and these I/Os must not be used as a current source (e.g. to drive an LED).
- 4. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F20x and STM32F21x reference manual, available from the STMicroelectronics website www.st.com.
- 5. FT = 5 V tolerant except when in analog or oscillator mode (for PC14, PC15, PH0 and PH1).
- If the device is delivered in an UFBGA176 package and if the REGOFF pin is set to V_{DD} (Regulator OFF), then PA0 is used as an internal Reset (active low).
- FSMC_NL pin is also named FSMC_NADV on memory devices.
- 8. RFU means "reserved for future use". This pin can be tied to V_{DD} , V_{SS} or left unconnected.

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Table 9. FSMC pin definition

Pins CE NOP/PSPAM/SPAM NOP/PSPAM MUX NAND 16 bit										
Pins -	CF	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND 16 bit	LQFP100					
PE2	-	A23	A23	-	Yes					
PE3	-	A19	A19	-	Yes					
PE4	-	A20	A20	-	Yes					
PE5	-	A21	A21	-	Yes					
PE6	-	A22	A22	-	Yes					
PF0	A0	A0	-	-	-					
PF1	A1	A1	-	-	-					
PF2	A2	A2	-	-	-					
PF3	A3	A3	-	-	-					
PF4	A4	A4	-	-	-					
PF5	A5	A5	-	-	-					
PF6	NIORD	-	-	-	-					
PF7	NREG	-	-	-	-					
PF8	NIOWR	-	-	-	-					
PF9	CD	-	-	-	-					
PF10	INTR	-	-	-	-					
PF12	A6	A6	-	-	-					
PF13	A7	A7	-	-	-					
PF14	A8	A8	-	-	-					
PF15	A9	A9	-	-	-					
PG0	A10	A10	-	-	-					
PG1	-	A11	-	-	-					
PE7	D4	D4	DA4	D4	Yes					
PE8	D5	D5	DA5	D5	Yes					
PE9	D6	D6	DA6	D6	Yes					
PE10	D7	D7	DA7	D7	Yes					
PE11	D8	D8	DA8	D8	Yes					
PE12	D9	D9	DA9	D9	Yes					
PE13	D10	D10	DA10	D10	Yes					
PE14	D11	D11	DA11	D11	Yes					
PE15	D12	D12	DA12	D12	Yes					
PD8	D13	D13	DA13	D13	Yes					
PD9	D14	D14	DA14	D14	Yes					



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Table 9. FSMC pin definition (continued)

Dina		F	SMC		1.050400
Pins	CF	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND 16 bit	- LQFP100
PD10	D15	D15	DA15	D15	Yes
PD11	-	A16	A16	CLE	Yes
PD12	-	A17	A17	ALE	Yes
PD13	-	A18	A18	-	Yes
PD14	D0	D0	DA0	D0	Yes
PD15	D1	D1	DA1	D1	Yes
PG2	-	A12	-	-	-
PG3	-	A13	-	-	-
PG4	-	A14	-	-	-
PG5	-	A15	-	-	-
PG6	-	-	-	INT2	-
PG7	-	-	-	INT3	-
PD0	D2	D2	DA2	D2	Yes
PD1	D3	D3	DA3	D3	Yes
PD3	-	CLK	CLK	-	Yes
PD4	NOE	NOE	NOE	NOE	Yes
PD5	NWE	NWE	NWE	NWE	Yes
PD6	NWAIT	NWAIT	NWAIT	NWAIT	Yes
PD7	-	NE1	NE1	NCE2	Yes
PG9	-	NE2	NE2	NCE3	-
PG10	NCE4_1	NE3	NE3	-	-
PG11	NCE4_2	-	-	-	-
PG12	-	NE4	NE4	-	-
PG13	-	A24	A24	-	-
PG14	-	A25	A25	-	-
PB7	-	NADV	NADV	-	Yes
PE0	-	NBL0	NBL0	-	Yes
PE1	-	NBL1	NBL1	-	Yes



mapping
function
Alternate
6.
Table

•					-	2.5	ומוומוו	able 10. Aitemate Idilotion mapping	Jul 111 ap	81118						
AF0		AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13		
SYS		TIM 1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/12S2	SPI3/12S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/	оте_Fs/ оте_нѕ	ЕТН	FSMC/SDIO/ OTG_HS	DCMI	AF014	AF15
PA0-WKUP		TIM2_CH1_ETR	TIM 5_CH1	TIM8_ETR				USART2_CTS	UART4_TX			ETH_MII_CRS				EVENTOUT
,	ı	TIM2_CH2	TIM5_CH2	ı	1	1		USART2_RTS	UART4_RX		1	ETH_MII _RX_CLK ETH_RMII _REF_CLK	1	ı	,	EVENTOUT
PA2 -		TIM2_CH3	TIM5_CH3	TIM9_CH1				USART2_TX				ETH_MDIO				EVENTOUT
PA3 -		TIM2_CH4	TIM5_CH4	TIM9_CH2				USART2_RX			OTG_HS_ULPI_D0	ETH_MII_COL		,		EVENTOUT
PA4	1					SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK					OTG_HS_SOF	DCMI_HSYNC		EVENTOUT
PA5		TIM2_CH1_ETR	,	TIM8_CH1N		SPI1_SCK	,	,	,	,	OTG_HS_ULPI_C K	,		,		EVENTOUT
- PA6		TIM1_BKIN	TIM3_CH1	TIM8_BKIN		SPI1_MISO		•	-	TIM13_CH1				DCMI_PIXCK		EVENTOUT
PA7	,	TIM1_CH1N	TIM3_CH2	TIM8_CH1N		SPI1_MOSI		,	-	TIM14_CH1		ETH_MII_RX_DV ETH_RMII _CRS_DV	-		,	EVENTOUT
PA8 MC	MCO1	TIM1_CH1	,		I2C3_SCL		,	USART1_CK	,	,	OTG_FS_SOF	,	-	•	,	EVENTOUT
PA9		TIM1_CH2	,		I2C3_SMBA	1	,	USART1_TX				,		DCMI_D0	,	EVENTOUT
PA10		TIM1_CH3						USART1_RX			OTG_FS_ID			DCMI_D1		EVENTOUT
PA11		TIM1_CH4						USART1_CTS		CAN1_RX	OTG_FS_DM					EVENTOUT
PA12	١.	TIM1_ETR					,	USART1_RTS		CAN1_TX	OTG_FS_DP			,		EVENTOUT
PA13 JTI SW	JTMS- SWDIO							,								EVENTOUT
PA14 SW	JTCK- SWCLK		,					,		-	-	-	-	-		EVENTOUT
PA15	JTDI	TIM 2_CH1 TIM 2_ETR	,			SPI1_NSS	SPI3_NSS	,	-			-	-	-	,	EVENTOUT



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Table 10. Alternate function mapping (continued)

						מממו	able 10. Aitemate igniculon mapping (continued)	מנט ומווי		Sind		(m)					
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13		
	Port	SYS	TIM 1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SP13/12S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/	отс_ғѕ/ отс_нѕ	ЕТН	FSMC/SDIO/ OTG_HS	DCMI	AF014	AF15
	PB0		TIM1_CH2N	TIM3_CH3	TIM8_CH2N						-	OTG_HS_ULPI_D1	ETH_MII_RXD2		-		EVENTOUT
	PB1		TIM1_CH3N	TIM3_CH4	TIM8_CH3N		ı	i	i	i	-	OTG_HS_ULPI_D2 ETH_MII_RXD3	ETH_MII_RXD3		-	1	EVENTOUT
	PB2				-		1	i	i	i	-	1	1	1	-		EVENTOUT
	PB3	JTDO/ TRACESWO	TIM2_CH2		-	-	SPI1_SCK	SPI3_SCK I2S3_SCK	1	i	-	-	1	-	-	-	EVENTOUT
	PB4	JTRST		TIM3_CH1	-		SPI1_MISO	SPI3_MISO	i	i	-	1	1		-	1	EVENTOUT
	PB5	-		TIM3_CH2	1	I2C1_SMBA	SPI1_MOSI	SPI3_MOSI I2S3_SD		1	CAN2_RX	OTG_HS_ULPI_D7	ETH_PPS_OUT	-	DCMI_D10	-	EVENTOUT
	PB6			TIM4_CH1	-	I2C1_SCL	1	1	USART1_TX	1	CAN2_TX	•	ı		sa_IMDa		EVENTOUT
	PB7		1	TIM4_CH2	-	I2C1_SDA	ı	i	USART1_RX	i	-		i	FSMC_NL	DCMI_VSYNC	1	EVENTOUT
Port B	PB8			TIM4_CH3	TIM10_CH1	I2C1_SCL	1	i	i	i	CAN1_RX	1	ETH_MII_TXD3	SDIO_D4	90-ТМОО		EVENTOUT
	PB9			TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS I2S2_WS	i	i	i	CAN1_TX	-	1	SDIO_D5	DCMI_D7	-	EVENTOUT
	PB10	-	TIM2_CH3		-	I2C2_SCL	SPI2_SCK I2S2_SCK	1	USART3_TX	1	-	OTG_HS_ULPI_D3ETH_ MII_RX_ER	ETH_MII_RX_ER	-	-		EVENTOUT
	PB11		TIM2_CH4	-	-	I2C2_SDA	•	ī	USART3_RX	ī	-	OTG_HS_ULPI_D4	ETH MILTXEN ETH RMILTXEN		-	-	EVENTOUT
	PB12		TIM1_BKIN			I2C2_SMBA	SPI2_NSS I2S2_WS	i	USART3_CK	i	CAN2_RX	OTG_HS_ULPI_D5 ETH_RMII_TXD0	ETH_MII_TXD0 ETH_RMII_TXD0	OTG_HS_ID	-		EVENTOUT
	PB13	-	TIM1_CH1N		-	-	SPI2_SCK I2S2_SCK	-	USART3_CTS	-	CAN2_TX	OTG_HS_ULPI_D6	ETH_MII_TXD1 ETH_RMII_TXD1	-	-	-	EVENTOUT
	PB14		TIM1_CH2N		TIM8_CH2N		SPI2_MISO	,	USART3_RTS	,	TIM12_CH1			OTG_HS_DM			EVENTOUT
	PB15	RTC_50Hz	TIM1_CH3N		NEHO_8MIT		SPI2_MOSI I2S2_SD	ı	1	ı	TIM12_CH2		1	OTG_HS_DP	-		EVENTOUT



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		AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT
		AF014	-						-	1		-		-				
	AF13	DCMI		-			-	-	DCMI_D0	DCMI_D1	DCMI_D2	DCMI_D3	DCMI_D8	DCMI_D4	DCMI_D9	-		-
	AF12	FSMC/SDIO/ OTG_HS						-	spio_be	SDIO_D7	spio_bo	SDIO_D1	SDIO_D2	SDIO_D3	SDIO_CK			
	AF11	ЕТН		ETH_MDC	ETH_MII_TXD2	ETH _MII_TX_CLK	ETH_MII_RXD0 ETH_RMII_RXD0	ETH_MII_RXD1 ETH_RMII_RXD1										
ea)	AF10	отс_Fs/ отс_нѕ	OTG_HS_ULPI_ STP		OTG_HS_ULPI_ DIR	OTG_HS_ULPI_ NXT												-
John	AF9	CAN1/CAN2/ TIM12/13/14	,	1		,	1	•	,	1		,	1	,	,	1	,	,
) Billdd	AF8	UART4/5/ USART6	-	-			-	-	USART6_TX	USART6_RX	USART6_CK	-	UART4_TX	UART4_RX	UART5_TX	-		-
נוסוו ווומ	AF7	USART1/2/3		,		,	,	-	,	1		,	USART3_TX	USART3_RX	USART3_CK	1	,	
are Iuno	AF6	SPI3/I2S3		i	ı	i	i	-	-	I2S3_MCK	i	I2S3_CKIN	SPI3_SCK I2S3_SCK	SPI3_MISO	SPI3_MOSI I2S3_SD	-	i	1
iable iv. Aiterilate iunction mapping (continued)	AF5	12C1/12C2/12C3 SPI1/SP12/12S2	-	-	SPI2_MISO	SPI2_MOSI	-	-	I2S2_MCK	-	-	IZS2_CKIN				-	-	-
lable 10	AF4	12C1/12C2/12C3		,		,	,			,	,	I2C3_SDA			,		,	
	AF3	TIM8/9/10/11	-					-	TIM8_CH1	TIM8_CH2	TIM8_CH3	TIM8_CH4	,					
	AF2	TIM3/4/5		i	1	i	i	-	TIM3_CH1	TIM3_CH2	ено еміт	TIM3_CH4	ı			-	i	-
	AF1	TIM 1/2	-	,	,	,	,			1	1		1		,		,	,
	9F0	SYS			,			-				MCO2	,		,			,
		Port	PC0	PC1	PC2	PC3	PC4	PC5	PC6	PC7	PC8	PC9	PC10	PC11	PC12	PC13	PC14- OSC32_IN	PC15- OSC32_OU T
											Port C							

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Table 10. Alternate function mapping (continued)

Fig. Aria Aria <th< th=""><th>F</th><th></th><th></th><th></th><th>į</th><th>lable 10</th><th>lable 10. Alternate lunction mapping (continued)</th><th>ini air</th><th>CHOII IIIA</th><th>) fillidd</th><th>COLLINA</th><th></th><th></th><th>!</th><th></th><th></th><th></th></th<>	F				į	lable 10	lable 10. Alternate lunction mapping (continued)	ini air	CHOII IIIA) fillidd	COLLINA			!			
1000 1000 <th< th=""><th></th><th>AF0</th><th>AF1</th><th>AF2</th><th>AF3</th><th>AF4</th><th>AF5</th><th>AF6</th><th>AF7</th><th></th><th>AF9</th><th></th><th>AF11</th><th>AF12</th><th>AF13</th><th></th><th></th></th<>		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7		AF9		AF11	AF12	AF13		
1. 1. 1. 1. 1. 1. 1. 1.		SYS	TIM 1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/12S2	SPI3/12S3	USART1/2/3		CAN1/CAN2/ TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI	AF014	AF15
1. 1. 1. 1. 1. 1. 1. 1.	•				1						CAN1_RX			FSMC_D2	,		EVENTOUT
THILE,	1		,		1				,	,	CAN1_TX	,		FSMC_D3	,	1	EVENTOUT
1. 1. 1. 1. 1. 1. 1. 1.	1			TIM3_ETR	1					UART5_RX				SDIO_CMD	DCMI_D11		EVENTOUT
1. 1. 1. 1. 1. 1. 1. 1.	Ī				1				USART2_CTS					FSMC_CLK	,		EVENTOUT
1	1		,		1			,	USART2_RTS					FSMC_NOE	,		EVENTOUT
Harron H	Ĭ.								USART2_TX					FSMC_NWE	,		EVENTOUT
Figure F	1				1				USART2_RX			,		FSMC_NWAIT	,		EVENTOUT
1. 1. 1. 1. 1. 1. 1. 1.	1							,	USART2_CK					FSMC_NE1/ FSMC_NCE2			EVENTOUT
Harrow	I		,	,	1	,		,	USART3_TX	,	,	,		FSMC_D13	,	,	EVENTOUT
Final Fina	l		,	,	1				USART3_RX					FSMC_D14	,		EVENTOUT
LONART, CITY <t< td=""><td>1</td><td></td><td></td><td></td><td>1</td><td></td><td></td><td></td><td>USART3_CK</td><td></td><td></td><td></td><td></td><td>FSMC_D15</td><td></td><td>-</td><td>EVENTOUT</td></t<>	1				1				USART3_CK					FSMC_D15		-	EVENTOUT
TIMM_CHY LOBARTA_RIS FSMC_AN FSMC_AN 1.1. TIMM_CHY	l			,	1				USART3_CTS					FSMC_A16	,		EVENTOUT
TIMM_CH2 TO <	1		,	TIM4_CH1	ı			,	USART3_RTS					FSMC_A17	,	-	EVENTOUT
TIMIL CHA TOW T	1			TIM4_CH2	1									FSMC_A18	,	-	EVENTOUT
TIMALCHA TIMALCHA TIMALCHA TO TO <td></td> <td></td> <td></td> <td>TIM4_CH3</td> <td>1</td> <td></td> <td></td> <td>,</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td>FSMC_D0</td> <td>,</td> <td>1</td> <td>EVENTOUT</td>				TIM4_CH3	1			,						FSMC_D0	,	1	EVENTOUT
TIMI_CHR	I		,	TIM4_CH4	1									FSMC_D1	,		EVENTOUT
H. I.	l		,	TIM4_ETR	i	,		,	,	,	,			FSMC_NBL0	DCMI_D2		EVENTOUT
EFH_MILTXD FSMC_AG3 1 FSMC_AG3 1 FSMC_AG3				,	ı			,		,	,			FSMC_NBL1	DCMI_D3		EVENTOUT
HANDLER TIMILOR TIMILOR <t< td=""><td>Ĕ</td><td>PACECLK</td><td>,</td><td>,</td><td>i</td><td>1</td><td></td><td>,</td><td>,</td><td>,</td><td>,</td><td>1</td><td>ETH_MII_TXD3</td><td>FSMC_A23</td><td>ı</td><td>. 1</td><td>EVENTOUT</td></t<>	Ĕ	PACECLK	,	,	i	1		,	,	,	,	1	ETH_MII_TXD3	FSMC_A23	ı	. 1	EVENTOUT
FSMC_AZD DOMI_D4 TIM9_CHI FSMC_AZD DOMI_D4 TIM1_CHI FSMC_AZD DOMI_D4 TIM1_CHI FSMC_AZD DOMI_D4 TIM1_CHI FSMC_D4 FSMC_D4 TIM1_CHI FSMC_D6 FSMC_D6 FSMC_D6 FSMC_D6 FSMC_D7 FSMC_D6 FSMC_D6 <td>Ε.</td> <td>RACED0</td> <td>,</td> <td>,</td> <td>1</td> <td></td> <td></td> <td>,</td> <td>,</td> <td></td> <td>,</td> <td>,</td> <td></td> <td>FSMC_A19</td> <td>,</td> <td>,</td> <td>EVENTOUT</td>	Ε.	RACED0	,	,	1			,	,		,	,		FSMC_A19	,	,	EVENTOUT
HATELER TIMB_CHI TAB CHI <	ΙĒ	RACED1		,	ı			,		,	,			FSMC_A20	DCMI_D4		EVENTOUT
TIMI_CHIN TIMI_CHIN FSMC_AR2 DCM_LDT TIMI_CHIN FSMC_D6 <td< td=""><td>T,</td><td>RACED2</td><td></td><td>,</td><td>TIM9_CH1</td><td></td><td></td><td>,</td><td>,</td><td></td><td>,</td><td>,</td><td></td><td>FSMC_A21</td><td>DCMI_D6</td><td>1</td><td>EVENTOUT</td></td<>	T,	RACED2		,	TIM9_CH1			,	,		,	,		FSMC_A21	DCMI_D6	1	EVENTOUT
TIMI_CHI	Τ,	RACED3		,	TIM9_CH2			,	,	,	,	,		FSMC_A22	DCMI_D7	1	EVENTOUT
TIMI_CHIN FSMC_D6 TIMI_CHI FSMC_D6 TIMI_CH2 FSMC_D6 TIMI_CH2 FSMC_D6 TIMI_CH3 FSMC_D9 TIMI_CH3 FSMC_D9 TIMI_CH3 FSMC_D1 TIMI_CH3 FSMC_D1 TIMI_EKH FSMC_D1 TIMI_BKIN FSMC_D11			TIM1_ETR	,	i				,	,	1	ı		FSMC_D4	ı	1	EVENTOUT
TIMI_CH2N FSMC_D6 TIMI_CH2N FSMC_D7 TIMI_CH2N FSMC_D7 TIMI_CH3N FSMC_D9 TIMI_CH3 FSMC_D10 TIMI_CH4 FSMC_D10 TIMI_EKIN FSMC_D11			TIM1_CH1N		-	-					-	•		FSMC_D5	i		EVENTOUT
.			TIM1_CH1		-	-	-	-		-	-	•	-	FSMC_D6	1		EVENTOUT
.			TIM1_CH2N	,	i			,	,	,	,	,		FSMC_D7	,	1	EVENTOUT
			TIM1_CH2	,	i									FSMC_D8	ı	1	EVENTOUT
			TIM1_CH3N		1	-		,	,	,		1		FSMC_D9	1		EVENTOUT
			TIM1_CH3			-					-			FSMC_D10			EVENTOUT
			TIM1_CH4	,				,		,	,			FSMC_D11	1		EVENTOUT
			TIM1_BKIN	,	ı			,	,	,	,			FSMC_D12	,		EVENTOUT



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	AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT
	AF014	-	1		,	-	,	-			,	,	,			,		1		1			1	-		1							
AF13	DCMI		,		,		,		,		,		DCMI_D12			,		ı	,	,			,			ı	1	ı	1			,	200
AF12	FSMC/SDIO/ OTG_HS	FSMC_A0	FSMC_A1	FSMC_A2	FSMC_A3	FSMC_A4	FSMC_A5	FSMC_NIORD	FSMC_NREG	FSMC_NIOWR	FSMC_CD	FSMC_INTR		FSMC_A6	FSMC_A7	FSMC_A8	FSMC_A9	FSMC_A10	FSMC_A11	FSMC_A12	FSMC_A13	FSMC_A14	FSMC_A15	FSMC_INT2	FSMC_INT3	i	FSMC_NE2/ FSMC_NCE3	FSMC_NCE4_1/ FSMC_NE3	FSMC_NCE4_2	FSMC_NE4	FSMC_A24	FSMC_A25	
AF11	ЕТН	-	-	-	,		,		-		,		,			,		-		-						тио_гяч_нта		-	ETH_MII_TX_EN ETH _RMII_TX_EN		ETH_MII_TXD0 ETH_RMII_TXD0	ETH_MII_TXD1 ETH_RMII_TXD1	1
AF10	оте_ғѕ⁄ оте_нѕ		i					-	-									i	i	i			i			i	i	i					
AF9	CAN1/CAN2/ TIM12/13/14								,	TIM13_CH1	TIM14_CH1																						
AF8	UART4/5/ USART6		1		,		,		,		,	,	,	,		,		1	1	1			,		USART6_CK	USART6_RTS	USART6_RX	ı		USART6_RTS	UART6_CTS	USART6_TX	OTO STOVS
AF7	USART1/2/3								-																	-		-					
AF6	SPI3/12S3				,		,		,		,		,			,												-					
AF5	SPI1/SPI2/12S2			-																								-					
AF4	I2C1/I2C2/I2C3	I2C2_SDA	I2C2_SCL	I2C2_SMBA	,		,				,	,	,	,		,	,				,	,		,				-					
AF3	TIM8/9/10/11	-	1		,		,	TIM10_CH1	TIM11_CH1		,	1	,			,		-		1			ı			ı		1	1				
AF2	TIM3/4/5		ı		,		,		,		,	,	,	,		,		,	,	ı	,		,					1					
AF1	TIM 1/2		i	ı	1		1				1	i	1			1	1	ı	i	i		1	i			i	i	1	,			,	Ī
AF0	sxs	-	i	1	,		,	1	1		,	i	,	1		,	1	ı	1	i		1	i	,		i	i	i			1	,	
	Port	PF0	PF1	PF2	PF3	PF4	PF5	PF6	PF7	PF8	PF9	PF10	PF11	PF12	PF13	PF14	PF15	PG0	PG1	PG2	PG3	PG4	PG5	PG6	PG7	PG8	PG9	PG10	PG11	PG12	PG13	PG14	

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Table 10. Alternate function mapping (continued)

AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13		
SYS	TIM 1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SP12/12S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	оте_ғѕ/ оте_нѕ	ЕТН	FSMC/SDIO/ OTG_HS	DCMI	AF014	AF15
			,	1	,	,	1			1			1		EVENTOUT
						,									EVENTOUT
								-		,	ETH_MII_CRS		-		EVENTOUT
1										,	ETH_MII_COL				EVENTOUT
1				I2C2_SCL				-		OTG_HS_ULPI_N XT			-		EVENTOUT
				I2C2_SDA						,					EVENTOUT
	,			I2C2_SMBA	,	,	-	-	TIM12_CH1	,	ETH_MII_RXD2	,	-		EVENTOUT
				I2C3_SCL						,	ETH_MII_RXD3				EVENTOUT
				I2C3_SDA						,			DCMI_HSYNC		EVENTOUT
				I2C3_SMBA					TIM12_CH2	,			DCMI_D0		EVENTOUT
		TIM5_CH1				,				,			DCMI_D1		EVENTOUT
		TIM5_CH2				,				,	,		DCMI_D2		EVENTOUT
		TIM5_CH3								,			DCMI_D3		EVENTOUT
			TIM8_CH1N						CAN1_TX	,				-	EVENTOUT
			TIM8_CH2N		1	,	1	,		,		,	DCMI_D4		EVENTOUT
			TIM8_CH3N			,		,		,		,	DCMI_D11		EVENTOUT
		TIM5_CH4			SPI2_NSS I2S2_WS	1		1	-	,			DCMI_D13		EVENTOUT
					SPI2_SCK I2S2_SCK	,	1		-	,		,	DCMI_D8	-	EVENTOUT
			TIM8_CH4		SPI2_MISO				-	,		,	PCMI_D9		EVENTOUT
			TIM8_ETR		SPI2_MOSI I2S2_SD	,	1		-	,		,	DCMI_D10	-	EVENTOUT
			TIM8_BKIN							,			DCMI_D5		EVENTOUT
			TIM8_CH1		,	,	1		-	,		,	DCMI_VSYNC	-	EVENTOUT
			TIM8_CH2						-	•		,	DCMI_D6		EVENTOUT
			TIM8_CH3		1	1	1	1	-	,		,	DCMI_D7		EVENTOUT
	-								-	•		,	1		EVENTOUT
	-				1	-	-	-	CAN1_RX	•		,	-	-	EVENTOUT
							ı		-	,	ETH_MII_RX_ER			-	EVENTOUT
١.	,				,	,				OTG_HS_ULPI_ DIR	,	,			EVENTOUT



STM32F20xxx Memory mapping

5 Memory mapping

The memory map is shown in *Figure 16*.



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Memory mapping STM32F20xxx

Figure 16. Memory map

0xA000 1000 - 0xBFFF FFFF ESMC 0xA000 0000 - 0xA000 0FFF 0x9000 0000 - 0x9FFF FFFF SMC bank3 NAND (NAND2) SMC bank2 NAND (NAND1) 0x8000 0000 - 0x8FFF FFFF 0x7000 0000 - 0x7FFF FFFF 0x6C00 0000 - 0x6FFF FFFF FSMC bank1 NOR/PSRAM 3 0x6800 0000 - 0x6BFF FFFF x6400 0000 - 0x67FF FFFF FSMC bank1 NOR/PSRAM 1 x6000 0000 - 0x63FF FFFF 0x5006 1000 - 0x5FFF FFFF x5006 0800 - 0x5006 0FFF 0x5005 0400 - 0x5006 7FFF 0x5005 0000 - 0x5005 03FF 0x5004 0000 - 0x5004 0FFF 0x5000 0000 - 0x5003 FFFF 0x4002 9400 - 0x4FFF FFFF Reserved USB OTG 0x4004 0000 - 0x4007 FFFF 0x4002 9400 - 0x4003 FFFF 0x4002 8000 - 0x4002 93FF 0x4002 6800 - 0x4002 7FFF DMA2 DMA1 0x4002 6400 - 0x4002 67FF 0x4002 6000 - 0x4002 63FF 0x4002 5000 - 0x4002 5FFF 0x4002 4000 - 0x4002 4FFF Flash interfac 0x4002 3C00 - 0x4002 3FFF 0x4002 3800 - 0x4002 3BFF 0x4002 3600 - 0x4002 3FFF 0x4002 3400 - 0x4002 37FF 0x4002 3000 - 0x4002 33FF 0x4002 2400 - 0x4002 2FFF 0x4002 2000 - 0x4002 23FF 0x4002 2000 - 0x4002 25FF 0x4002 1C00 - 0x4002 1FFF 0x4002 1800 - 0x4002 1BFF 0x4002 1400 - 0x4002 17FF Port G 0x4002 1000 - 0x4002 13FF 0x4002 0C00 - 0x4002 0FFF 0x4002 0800 - 0x4002 0FFF 0x4002 0400 - 0x4002 0FFF 0x4002 0400 - 0x4002 07FF Port C Port B 0x4002 0000 - 0x4002 03FF 0x4002 0000 - 0x4001 FFFF 0x4001 4C00 - 0x4001 FFFF 0x4001 4800 - 0x4001 4FFF 0x4001 4400 - 0x4001 47FF TIM10 TIMS 0x4001 4000 - 0x4001 43FF 0x4001 3C00 - 0x4001 3FFF 0x4001 3800 - 0x4001 3BFF 0x4001 3400 - 0x4001 37FF SYSCF 0x4001 3000 - 0x4001 33FF 0xFFFF FFFF 0x4001 2C00 - 0x4001 2FFF 0x4001 2800 - 0x4001 2FFF 0x4001 2800 - 0x4001 2FFF 0x4001 2400 - 0x4001 27FF 512-Mbyte block 7 Reserve Cortex-M3's 0x4001 2000 - 0x4001 23FF 0x4001 2000 - 0x4001 23FF 0x4001 1800 - 0x4001 1FFF 0x4001 1400 - 0x4001 13FF 0x4001 0800 - 0x4001 0FFF 0xE000 0000 0xDFFF FFFF peripherals 512-Mbvte block 6 Not used TIM8 / PWM2 0x4001 0400 - 0x4001 07FF 0x4001 0000 - 0x4001 03FF 0x4000 7800 - 0x4000 FFFF 0x4000 7400 - 0x4000 77FF TIM1 / PWM1 0xC000 0000 0xBFFF FFFF 512-Mbyte DAC1/DAC 0x4000 7000 - 0x4000 73FF block 5 SMC registe 0x4000 6C00 - 0x4000 6FFF 0x4000 0C00 - 0x4000 0FFF 0x4000 6800 - 0x4000 6BFF 0x4000 6400 - 0x4000 67FF 0x4000 6000 - 0x4000 63FF 0xA000 0000 BxCAN1 512-Mbvte 0x4000 5C00 - 0x4000 5FFF 0x4000 5C00 - 0x4000 5FFF 0x4000 5800 - 0x4000 5BFF 0x4000 5400 - 0x4000 57FF 0x4000 5000 - 0x4000 53FF FSMC bank & bank4 0x8000 0000 0x7FFF FFFF UART5 UART4 USART: USART: 512-Mbyte 0x4000 4C00 - 0x4000 4FFF 0x4000 4600 - 0x4000 4FFF 0x4000 4800 - 0x4000 4FFF 0x4000 4400 - 0x4000 47FF 0x4000 4000 - 0x4000 43FF block 3 FSMC bank & bank2 0x4000 3C00 - 0x4000 3FFF 0x6000 0000 0x5FFF FFFF 0x4000 3800 - 0x4000 3REE 512-Mbyte 0x4000 3400 - 0x4000 37FF Reserved block 2 Peripherals 0x4000 3000 - 0x4000 33FF 0x4000 2C00 - 0x4000 2FFF WWDG BKP re 0x4000 2800 - 0x4000 2BFF 0x4000 0000 0x3FFF FFFF 0x4000 2000 - 0x4000 22FF 0x4000 2400 - 0x4000 23FF 0x4000 2000 - 0x4000 23FF 512-Mbyte block 1 SRAM 0x2002 0000 - 0x3FFF FFFF TIM13 0x4000 1C00 - 0x4000 1FFF SRAM (16 KB aliased by bit-banding) 0x2001 C000 - 0x2001 FFFF TIM1 0x4000 1800 - 0x4000 1BFF 0x4000 1400 - 0x4000 17FF 0x4000 1000 - 0x4000 13FF SRAM (112 KB aliased by bit-banding) 0x2000 0000 0x1FFF FFFF 2000 0000 - 0x2001 BFFF TIM5 0x4000 0C00 - 0x4000 0FFF 512-Mbyte 0x4000 0800 - 0x4000 0REE block 0 0x1FFF C008 - 0x1FFF FFFF 0x4000 0800 - 0x4000 0BF 0x4000 0400 - 0x4000 07FF 0x4000 0000 - 0x4000 03FF Reserved Code 0x1FFF C000 - 0x1FFF C007 0x1FFF 7A10 - 0x1FFF 7FFF Option Bytes 0x0000 0000 Reserved x1FFF 0000 - 0x1FFF 7A0F x0810 0000 - 0x0FFF FFFF Reserved Flash 0800 0000 - 0x080F FFFF Reserved Aliased to Flash, system emory or SRAM dependin on the BOOT pins x0001 C000 - 0x07FF FFFF 0x0000 0000 - 0x000F FFFF ai17615c



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3 σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 1.8 V \leq V_{DD} \leq 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

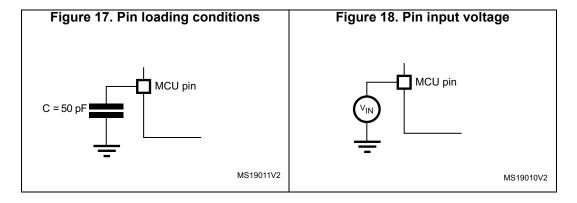
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 17.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 18*.





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Electrical characteristics STM32F20xxx

6.1.6 Power supply scheme

 V_{BAT} Backup circuitry Power switch (OSC32K,RTC, 1.65-3.6\ Wakeup logic Backup registers, backup RAM) QUT shifte Ю GP I/Os Logic evel Kernel logic (CPU, V_{CAP} digital $2 \times 2.2 \mu F$ & RAM) V_{DD} 1/2/...14/15 Voltage regulator 15 × 100 nF V_{SS} + 1 × 4.7 µF ■ **REGOFF** Flash memory **IRROFF** $^{\mathsf{V}}\mathsf{D}\mathsf{D}$ V_{DDA} V_{REF+} Analog 100 n 100 nF **ADC** + 1 µF V_{REF} RCs, PLL V_{SSA} ai17527f

Figure 19. Power supply scheme

- Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be
 placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality
 of the device.
- 2. To connect REGOFF and IRROFF pins, refer to Section 3.16: Voltage regulator.
- 3. The two 2.2 μF ceramic capacitors must be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
- 4. The 4.7 μ F ceramic capacitor must be connected to one of the V_{DD} pin.

Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB, to ensure good device operation. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect device operation.

ai14126

6.1.7 Current consumption measurement

IDD_VBAT_VBAT_IDD_VDD

VDDA

Figure 20. Current consumption measurement scheme

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 11*, *Table 12*, and *Table 13* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Max	Unit
V_{DD} – V_{SS}	External main supply voltage (including V_{DDA} , V_{DD}) ⁽¹⁾	-0.3	4.0	
V	Input voltage on five-volt tolerant pin ⁽²⁾	V _{SS} -0.3	V _{DD} +4	V
V _{IN}	Input voltage on any other pin	V _{SS} -0.3	4.0	
∆V _{DDx}	Variations between different V _{DD} power pins	-	50	mV
V _{SSX} - V _{SS}	Variations between all the different ground pins	-	50	1111
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Sectio	n 6.3.14	-

Table 11. Voltage characteristics

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

V_{IN} maximum value must always be respected. Refer to Table 12 for the values of the maximum allowed injected current.

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Symbol Ratings Max Unit Total current into V_{DD} power lines (source)⁽¹⁾ 120 I_{VDD} Total current out of V_{SS} ground lines (sink)⁽¹⁾ 120 I_{VSS} Output current sunk by any I/O and control pin I_{IO} Output current source by any I/Os and control pin mΑ 25 Injected current on five-volt tolerant I/O(3) -5/+0 $I_{INJ(PIN)}^{(2)}$ Injected current on any other pin (4) ±5

Table 12. Current characteristics

±25

Total injected current (sum of all I/O and control pins)(5)

- Negative injection disturbs the analog performance of the device. See note in Section 6.3.20: 12-bit ADC characteristics.
- Positive injection is not possible on these I/Os. A negative injection is induced by V_{IN}<V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
- 4. A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS} . $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
- 5. When several inputs are submitted to a current injection, the maximum ΣI_{INJ(PIN)} is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to +150	°C
T _J	Maximum junction temperature	125	°C

6.3 Operating conditions

 $\Sigma I_{\text{INJ(PIN)}}^{(4)}$

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency -		0	120	
f _{PCLK1}	Internal APB1 clock frequency -		0	30	MHz
f _{PCLK2}	Internal APB2 clock frequency	-	0	60	

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

Table 14. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	Standard operating voltage	-	1.8 ⁽¹⁾	3.6	
V _{DDA} ⁽²⁾	Analog operating voltage (ADC limited to 1 M samples)	Must be the same netential as V (3)	1.8 ⁽¹⁾	3.6	
	Analog operating voltage (ADC limited to 2 M samples)	Must be the same potential as V _{DD} ⁽³⁾	2.4	3.6	V
V _{BAT}	Backup operating voltage	-	1.65	3.6	
	land to the second FT size	2 V ≤ V _{DD} ≤ 3.6 V	-0.3	5.5	
.,	Input voltage on RST and FT pins	1.7 V ≤ V _{DD} ≤ 2 V	-0.3	5.2	
V _{IN}	Input voltage on TTa pins	-	-0.3	V _{DD} +0.3	
	Input voltage on BOOT0 pin -		0	9	
V _{CAP1}	Internal core voltage to be supplied externally in REGOFF mode		1.1	1.3	
	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7 ⁽⁴⁾	LQFP64	-	444	
		WLCSP64+2		392	
Б		LQFP100	-	434	mW
P _D		LQFP144	-	500	
		LQFP176	-	526	
		UFBGA176	-	513	
	Ambient temperature for 6 suffix	Maximum power dissipation	-40	85	°C
Та	version	Low-power dissipation ⁽⁵⁾	-40	105	
	Ambient temperature for 7 suffix	Maximum power dissipation	-40	105	
	version	Low-power dissipation ⁽⁵⁾	-40	125	
TJ	Junction temperature range	6 suffix version	-40	105	°C
	Juniction temperature range	7 suffix version	-40	125	

^{1.} On devices in WLCSP64+2 package, if IRROFF is set to V_{DD} , the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16).

^{2.} When the ADC is used, refer to Table 66: ADC characteristics.

^{3.} It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and power-down operation.

^{4.} If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} .

^{5.} In low-power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} .

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Table 15. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency (f _{Flashmax})	Number of wait states at maximum CPU frequency (f _{CPUmax} = 120 MHz) ⁽¹⁾	I/O operation	FSMC_CLK frequency for synchronous accesses	Possible Flash memory operations
V _{DD} =1.8 to 2.1 V ⁽²⁾	Conversion time up to 1 Msps	16 MHz with no Flash memory wait state	7 ⁽³⁾	Degraded speed performanceNo I/O compensation	Up to 30 MHz	8-bit erase and program operations only
V _{DD} = 2.1 to 2.4 V	Conversion time up to 1 Msps	18 MHz with no Flash memory wait state	6 ⁽³⁾	Degraded speed performanceNo I/O compensation	Up to 30 MHz	16-bit erase and program operations
V _{DD} = 2.4 to 2.7 V	Conversion time up to 2 Msps	24 MHz with no Flash memory wait state	4 ⁽³⁾	Degraded speed performanceI/O compensation works	Up to 48 MHz	16-bit erase and program operations
V _{DD} = 2.7 to 3.6 V ⁽⁴⁾	Conversion time up to 2 Msps	30 MHz with no Flash memory wait state	3 ⁽³⁾	Full-speed operationI/O compensation works	- Up to 60 MHz when V _{DD} = 3.0 to 3.6 V - Up to 48 MHz when V _{DD} = 2.7 to 3.0 V	32-bit erase and program operations

^{1.} The number of wait states can be reduced by reducing the CPU frequency (see Figure 21).

4. The voltage range for OTG USB FS can drop down to 2.7 V. However it is degraded between 2.7 and 3 V.

On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16).

^{3.} Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.

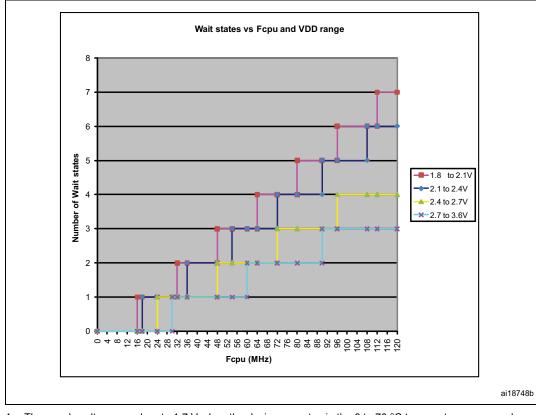


Figure 21. Number of wait states versus f_{CPU} and V_{DD} range

1. The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 $^{\circ}$ C temperature range and IRROFF is set to V_{DD} .

6.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor to the VCAP1/VCAP2 pins. C_{EXT} is specified in *Table 16*.

ESR R Leak

Figure 22. External capacitor C_{EXT}

1. Legend: ESR is the equivalent series resistance.

Table 16. VCAP1/VCAP2 operating conditions⁽¹⁾

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 μF
ESR	ESR of external capacitor	< 2 Ω

^{1.} When bypassing the voltage regulator, the two 2.2 μ F V_{CAP} capacitors are not required and must be replaced by two 100 nF decoupling capacitors.

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6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A .

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
4	V _{DD} rise time rate	20	8	µs/V
^t ∨DD	V _{DD} fall time rate	20	8	μ5/ ν

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

Table 18. Operating conditions at power-up / power-down (regulator OFF)

Symbol	Parameter	Conditions	Min	Max	Unit
t _{VDD}	V _{DD} rise time rate	Power-up	20	∞	
	V _{DD} fall time rate	Power-down	20	∞	
t	V _{CAP_1} and V _{CAP_2} rise time rate	Power-up	20	∞	µs/V
t _{VCAP}	V _{CAP_1} and V _{CAP_2} fall time rate	Power-down	20	8	

6.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 19* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
		PLS[2:0]=000 (rising edge)	2.09	2.14	2.19				
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08				
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37				
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25				
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51				
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39				
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65				
V	Programmable voltage	PLS[2:0]=011 (falling edge)	2.44	2.51	2.56				
V_{PVD}	detector level selection	PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V			
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71				
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99				
		PLS[2:0]=101 (falling edge)	2.75	2.84	3.02				
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10				
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99				
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21				
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09				
V _{PVDhyst} ⁽¹⁾	PVD hysteresis	-	-	100	-	mV			
	Power-on/power-down	Falling edge	1.60	1.68	1.76	V			
V _{POR/PDR}	reset threshold	Rising edge	1.64	1.72	1.80	V			
V _{PDRhyst} ⁽¹⁾	PDR hysteresis	-	-	40	-	mV			
	Brownout level 1	Falling edge	2.13	2.19	2.24				
V _{BOR1}	threshold	Rising edge	2.23	2.29	2.33				
V	Brownout level 2	Falling edge	2.44	2.50	2.56	V			
V _{BOR2}	threshold	Rising edge	2.53	2.59	2.63	v			
V	Brownout level 3	Falling edge	2.75	2.83	2.88				
V _{BOR3}	I., 	Rising edge	2.85	2.92	2.97				
V _{BORhyst} ⁽¹⁾	BOR hysteresis	-	-	100	ı	mV			
T _{RSTTEMPO} ⁽¹⁾⁽²⁾	Reset temporization	-	0.5	1.5	3.0	ms			

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{RUSH} ⁽¹⁾	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
E _{RUSH} ⁽¹⁾	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	V _{DD} = 1.8 V, T _A = 105 °C, I _{RUSH} = 171 mA for 31 μs	-	-	5.4	μC

Table 19. Embedded reset and power control block characteristics (continued)

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 20: Current consumption measurement scheme*.

All Run mode current consumption measurements given in this section are performed using $CoreMark^{\otimes}$ code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 30 MHz, 1 wait state from 30 to 60 MHz, 2 wait states from 60 to 90 MHz and 3 wait states from 90 to 120 MHz).
- When the peripherals are enabled HCLK is the system clock, f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2, except is explicitly mentioned.
- The maximum values are obtained for V_{DD} = 3.6 V and maximum ambient temperature (T_A) , and the typical values for T_A = 25 °C and V_{DD} = 3.3 V unless otherwise specified.

^{1.} Guaranteed by design, not tested in production.

The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

Table 20. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM $^{(1)}$

Symbol	Parameter	Conditions		Тур	Ма	x ⁽²⁾	Unit	
Symbol	Parameter	Conditions	f _{HCLK}	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C		
			120 MHz	49	63	72		
			90 MHz	38	51	61		
			60 MHz	26	39	49		
		(3)	30 MHz	14	27	37		
		External clock ⁽³⁾ , all peripherals enabled ⁽⁴⁾	25 MHz	11	24	34		
		peripriorale chasica	16 MHz ⁽⁵⁾	8	21	30		
			8 MHz	5	17	27		
			4 MHz	3	16	26		
	Supply current		2 MHz	2	15	25	mA	
I _{DD}	in Run mode		120 MHz	21	34	44	IIIA	
			90 MHz	17	30	40		
			60 MHz	12	25	35		
		(2)	30 MHz	7	20	30		
		External clock ⁽³⁾ , all peripherals disabled	25 MHz	5	18	28		
		periprierais disabled	16 MHz ⁽⁵⁾	4.0	17.0	27.0		
			8 MHz	2.5	15.5	25.5		
			4 MHz	2.0	14.7	24.8		
			2 MHz	1.6	14.5	24.6		

^{1.} Code and data processing running from SRAM1 using boot pins.

^{2.} Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.

^{3.} External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.

^{4.} When the ADC is on (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

^{5.} In this case HCLK = system clock/2.

Table 21. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	£	Тур	Ma	Unit	
Symbol	Parameter	er Conditions f _{HCLK}		T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Oilit
			120 MHz	61	81	93	
			90 MHz	48	68	80	
			60 MHz	33	53	65	
		(2)	30 MHz	18	38	50	
		External clock ⁽²⁾ , all peripherals enabled ⁽³⁾	25 MHz	14	34	46	
		periprierais chables	16 MHz ⁽⁴⁾	10	30	42	
			8 MHz	6	26	38	
			4 MHz	4	24	36	
	Supply current		2 MHz	3	23	35	mA
I _{DD}	in Run mode		120 MHz	33	54	66	IIIA
			90 MHz	27	47	59	
			60 MHz	19	39	51	
		(2)	30 MHz	11	31	43	
		External clock ⁽²⁾ , all peripherals disabled	25 MHz	8	28	41	
		periprierais disabled	16 MHz ⁽⁴⁾	6	26	38	
			8 MHz	4	24	36	
			4 MHz	3	23	35	
			2 MHz	2	23	34	

 $^{1. \}quad \text{Guaranteed by characterization results, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.}$

^{2.} External clock is 4 MHz and PLL is on when $\rm f_{HCLK}$ > 25 MHz.

^{3.} When the ADC is on (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

^{4.} In this case HCLK = system clock/2.

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Figure 23. Typical current consumption vs. temperature, Run mode, code with data processing running from RAM, and peripherals ON

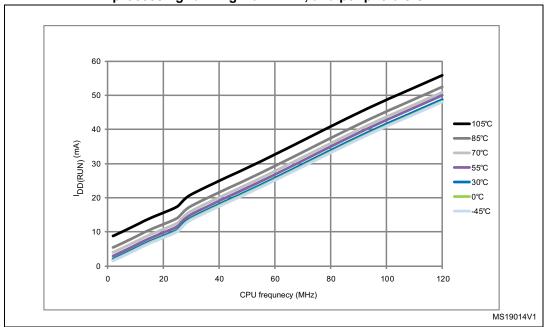
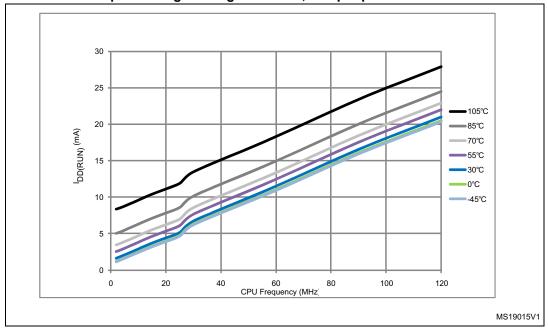


Figure 24. Typical current consumption vs. temperature, Run mode, code with data processing running from RAM, and peripherals OFF



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Figure 25. Typical current consumption vs. temperature, Run mode, code with data processing running from Flash, ART accelerator OFF, peripherals ON

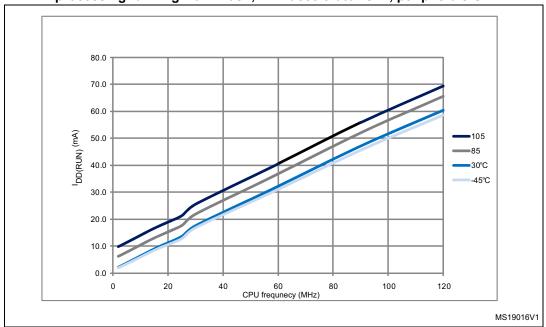


Figure 26. Typical current consumption vs. temperature, Run mode, code with data processing running from Flash, ART accelerator OFF, peripherals OFF

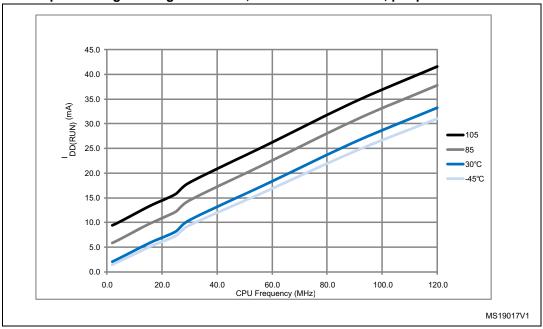


Table 22. Typical and maximum current consumption in Sleep mode

				Тур	Max	x ⁽¹⁾	
Symbol	Parameter	Conditions	f _{HCLK}	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit
			120 MHz	38	51	61	
			90 MHz	30	43	53	
			60 MHz	20	33	43	
		(2)	30 MHz	11	25	35	
		External clock ⁽²⁾ , all peripherals enabled ⁽³⁾	25 MHz	8	21	31	
		all periprietals chaptes	16 MHz	6	19	29	mA
			8 MHz	3.6	17.0	27.0	
			4 MHz	2.4	15.4	25.3	
	Supply current in		2 MHz	1.9	14.9	24.7	
I _{DD}	Sleep mode		120 MHz	8	21	31	
			90 MHz	7	20	30	
			60 MHz	5	18	28	
		(2)	30 MHz	3.5	16.0	26.0	- - - -
		External clock ⁽²⁾ , all peripherals disabled	25 MHz	2.5	16.0	25.0	
		policina diodolod	16 MHz	2.1	15.1	25.0	
			8 MHz	1.7	15.0	25.0	
			4 MHz	1.5	14.6	24.6	
			2 MHz	1.4	14.2	24.3	

 $^{1. \}quad \text{Guaranteed by characterization results, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.}$

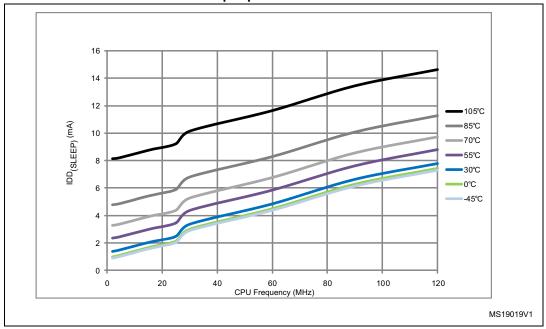
^{2.} External clock is 4 MHz and PLL is on when $\rm f_{HCLK} > 25~MHz.$

^{3.} Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).

50 45 40 **-**105℃ $\mathsf{IDD}(\mathsf{SLEEP})^{\,(\mathsf{mA})}$ 35 **—**85℃ 30 —70°C **-**55℃ 25 **-**30℃ 20 **—**0°C **—**-45℃ 15 0 120 CPU Frequency (MHz) MS19018V1

Figure 27. Typical current consumption vs. temperature in Sleep mode, peripherals ON

Figure 28. Typical current consumption vs. temperature in Sleep mode, peripherals OFF

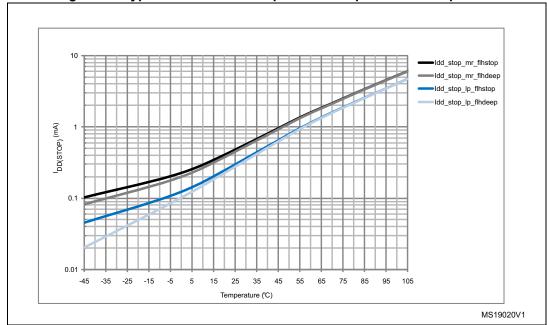


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Table 23. Typical and maximum current consumptions in Stop mode

			Тур		Max			
Symbol	Parameter	Conditions	T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit	
	Supply current in Stop mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.55	1.2	11.00	20.00		
	with main regulator in Run mode	Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.50	1.2	11.00	20.00	mA	
	Supply current in Stop mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.35	1.1	8.00	15.00	ША	
	with main regulator in Low-power mode	Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.30	1.1	8.00	15.00		

Figure 29. Typical current consumption vs. temperature in Stop mode



All typical and maximum values from table 18 and figure 26 will be reduced over time by up to 50% as part
of ST continuous improvement of test procedures. New versions of the datasheet will be released to reflect
these changes

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Symbol				Тур		Ma	ax ⁽¹⁾	
	Parameter	r Conditions	T _A = 25 °C			T _A = 85 °C	T _A = 105 °C	Unit
			V _{DD} = 1.8 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} :	= 3.6 V	
Supply current in Standby mode		Backup SRAM ON, low-speed oscillator and RTC ON	3.0	3.4	4.0	15.1	25.8	
	Backup SRAM OFF, low-speed oscillator and RTC ON	2.4	2.7	3.3	12.4	20.5	μA	
	mode	Backup SRAM ON, RTC OFF	2.4	2.6	3.0	12.5	24.8	
		Backup SRAM OFF, RTC OFF	1.7	1.9	2.2	9.8	19.2	

Table 24. Typical and maximum current consumptions in Standby mode

^{1.} Guaranteed by characterization results, not tested in production.

Table 25. Typical and maximum curren	t consumptions in V _{BAT} mode
--------------------------------------	---

				Тур		Ма	x ⁽¹⁾	
Symbol	Parameter	er Conditions	Т	A = 25 °	С	T _A = 85 °C	T _A = 105 °C	Unit
			V _{DD} = 1.8 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} =	= 3.6 V	
I _{DD_VBAT}	Backup domain supply current	Backup SRAM ON, low-speed oscillator and RTC ON	1.29	1.42	1.68	12	19	
		Backup SRAM OFF, low-speed oscillator and RTC ON	0.62	0.73	0.96	8	10	μΑ
		Backup SRAM ON, RTC OFF	0.79	0.81	0.86	9	16	
		Backup SRAM OFF, RTC OFF	0.10	0.10	0.10	5	7	

^{1.} Guaranteed by characterization results, not tested in production.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 26*. The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with one peripheral clocked on (with only the clock applied)
- The code is running from Flash memory and the Flash memory access time is equal to 3 wait states at 120 MHz
- Prefetch and Cache ON
- When the peripherals are enabled, HCLK = 120MHz, f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2
- The typical values are obtained for V_{DD} = 3.3 V and T_A= 25 °C, unless otherwise specified.



Table 26. Peripheral current consumption

	Peripheral ⁽¹⁾	Typical consumption at 25 °C	Unit
	GPIO A	0.45	
	GPIO B	0.43	
	GPIO C	0.46	
	GPIO D	0.44	
	GPIO E	0.44	
	GPIO F	0.42	
	GPIO G	0.44	
	GPIO H	0.42	
AHB1	GPIO I	0.43	
	OTG_HS + ULPI	3.64	
	CRC	1.17	mA
	BKPSRAM	0.21	
	DMA1	2.76	
	DMA2	2.85	
	ETH_MAC + ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	2.99	
AHB2	OTG_FS	3.16	
ANDZ	DCMI	0.60	
AHB3	FSMC	1.74	

Table 26. Peripheral current consumption (continued)

	Peripheral ⁽¹⁾	Typical consumption at 25 °C	Unit
	TIM2	0.61	
	TIM2 0.61 TIM3 0.49 TIM4 0.54 TIM5 0.62 TIM6 0.20 TIM7 0.20 TIM12 0.36 TIM13 0.28 TIM14 0.25 USART2 0.25 USART3 0.25 UART4 0.25 UART5 0.26 I2C1 0.25 I2C2 0.25 I2C2 0.25 I2C3 0.25 SPI2 0.20/0.10 SPI3 0.18/0.09 CAN1 0.31 CAN2 0.30 DAC channel 1(2) 1.11		
	TIM4	0.54	
	TIM5	0.62	
	TIM6	0.20	
	TIM2 0.61 TIM3 0.49 TIM4 0.54 TIM5 0.62 TIM6 0.20 TIM7 0.20 TIM12 0.36 TIM13 0.28 TIM14 0.25 USART2 0.25 USART3 0.25 UART4 0.25 UART5 0.26 I2C1 0.25 I2C2 0.25 I2C2 0.25 SPI2 0.20/0.10 SPI3 0.18/0.09 CAN1 0.31 CAN2 0.30		
	TIM12	0.36	
	TIM13	0.28	
	TIM14	0.25	
	USART2	0.25	
	USART3	0.25	
A DD4	UART4	0.25	4
APB1	UART5	0.26	mA
	I2C1	0.25	
	I2C2	0.25	
	I2C3	0.25	
	SPI2	0.20/0.10	
	SPI3	0.18/0.09	
	CAN1	0.31	
	CAN2	0.30	
	DAC channel 1 ⁽²⁾	1.11	
	DAC channel 1 ⁽³⁾	1.11	
	PWR	0.15	
	WWDG	0.15	

	Peripheral ⁽¹⁾	Typical consumption at 25 °C	Unit
	SDIO	0.69	
	TIM1	1.06	
	TIM8	1.03	
	TIM9	0.58	
	TIM10	0.37	
APB2	TIM11	0.39	mA
AFDZ	ADC1 ⁽⁴⁾	2.13	IIIA
	ADC2 ⁽⁴⁾	2.04	
	ADC3 ⁽⁴⁾	2.12	
	SPI1	1.20	
	USART1	0.38	
	USART6	0.37	

Table 26. Peripheral current consumption (continued)

- 1. External clock is 25 MHz (HSE oscillator with 25 MHz crystal) and PLL is on.
- 2. EN1 bit is set in DAC_CR register.
- 3. EN2 bit is set in DAC_CR register.
- 4. $f_{ADC} = f_{PCLK2}/2$, ADON bit set in ADC_CR2 register.

6.3.7 Wakeup time from Low-power mode

The wakeup times given in *Table 27* is measured on a wakeup phase with a 16 MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Min ⁽¹⁾	Typ ⁽¹⁾	Max ⁽¹⁾	Unit
t _{WUSLEEP} (2)	Wakeup from Sleep mode	-	1	-	μs
	Wakeup from Stop mode (regulator in Run mode)	-	13	-	
twustop ⁽²⁾	Wakeup from Stop mode (regulator in Low-power mode)	-	17	40	us
t _{WUSTOP} ⁽²⁾	Wakeup from Stop mode (regulator in Low-power mode and Flash memory in Deep power down mode)	-	110	-	r -
t _{WUSTDBY} (2)(3)	Wakeup from Standby mode	260	375	480	μs

Table 27. Low-power mode wakeup timings

- 1. Guaranteed by characterization results, not tested in production.
- 2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
- 3. $t_{WUSTDBY}$ minimum and maximum values are given at 105 °C and –45 °C, respectively.

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6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in *Table 28* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 14*.

Table 28. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSE_ext}	External user clock source frequency ⁽¹⁾		1	-	26	MHz
V _{HSEH}	OSC_IN input pin high level voltage		0.7V _{DD}	-	V_{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage	_	V_{SS}	ı	0.3V _{DD}	V
$t_{w(HSE)} \ t_{w(HSE)}$	OSC_IN high or low time ⁽¹⁾		5	ı	-	ns
$t_{r(HSE)} \ t_{f(HSE)}$	OSC_IN rise or fall time ⁽¹⁾		-	-	20	113
C _{in(HSE)}	OSC_IN input capacitance ⁽¹⁾	-	-	5	-	pF
DuCy _(HSE)	Duty cycle	-	45		55	%
ΙL	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

^{1.} Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

The characteristics given in *Table 29* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 14*.

Table 29. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE_ext}	User External clock source frequency ⁽¹⁾		-	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		0.7V _{DD}	-	V_{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	ı	$0.3V_{DD}$	V
$\begin{matrix} t_{\text{w(LSE)}} \\ t_{\text{f(LSE)}} \end{matrix}$	OSC32_IN high or low time ⁽¹⁾	-	450	ı	ı	ns
$\begin{matrix} t_{r(LSE)} \\ t_{f(LSE)} \end{matrix}$	OSC32_IN rise or fall time ⁽¹⁾		ı	ı	50	113
C _{in(LSE)}	OSC32_IN input capacitance ⁽¹⁾	-	ı	5	ı	pF
DuCy _(LSE)	Duty cycle	-	30	-	70	%
ΙL	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{D}$	-	-	±1	μΑ

^{1.} Guaranteed by design, not tested in production.

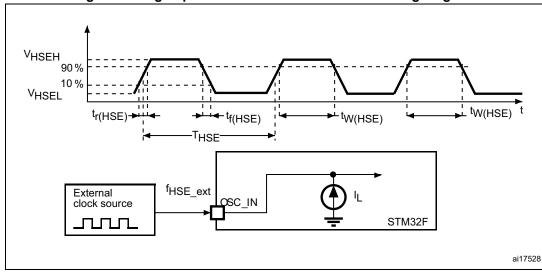
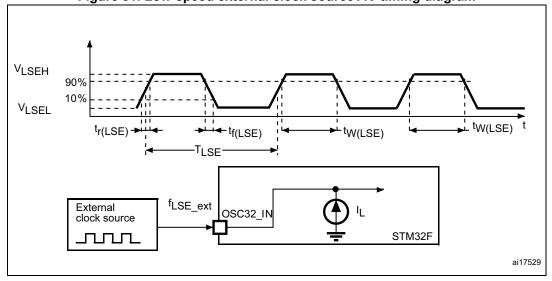


Figure 30. High-speed external clock source AC timing diagram





High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 30*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
	HSE current consumption	V_{DD} =3.3 V, ESR= 30 Ω , C_L =5 pF@25 MHz	-	449	-	
I _{DD}	nse current consumption	V_{DD} =3.3 V, ESR= 30 Ω , C_L =10 pF@25 MHz	-	532	-	μА
9 _m	Oscillator transconductance	Startup	5	-	-	mA/V
t _{SU(HSE} (3)	Startup time	V _{DD} is stabilized	-	2	-	ms

Table 30. HSE 4-26 MHz oscillator characteristics^{(1) (2)}

- 1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
- 2. Guaranteed by characterization results, not tested in production.
- t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 32*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note:

For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

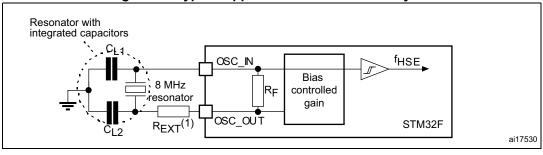


Figure 32. Typical application with an 8 MHz crystal

1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 31*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).



	· Late of the contract of the							
Symbol	Parameter	Conditions Min Typ Max				Unit		
R _F	Feedback resistor	-	-	18.4	-	MΩ		
I _{DD}	LSE current consumption	-	-	-	1	μA		
9 _m	Oscillator Transconductance	-	2.8	-	-	μA/V		
t _{SU(LSE)} ⁽²⁾	startup time	V _{DD} is stabilized	-	2	1	s		

Table 31. LSE oscillator characteristics ($f_{LSE} = 32.768 \text{ kHz}$) (1)

Note: For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Resonator with integrated capacitors OSC32 fLSE Bias 32.768 kHz RF controlled resonator gain OSC32 OUT STM32F ai17531

Figure 33. Typical application with a 32.768 kHz crystal

6.3.9 Internal clock source characteristics

The parameters given in Table 32 and Table 33 are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Symbol **Parameter** Conditions Unit Min Тур Max Frequency 16 MHz f_{HSI} HSI user-trimming step⁽²⁾ 1 % $T_{\Delta} = -40 \text{ to } 105 \,^{\circ}\text{C}^{(3)}$ **-**8 4.5 % **ACC_{HSI}** Accuracy of the $T_A = -10 \text{ to } 85 \, ^{\circ}\text{C}^{(3)}$ **-4** 4 % HSI oscillator $T_A = 25 \, {}^{\circ}C^{(\overline{4})}$ _ 1 _ 1 % t_{su(HSI)}⁽²⁾ HSI oscillator startup time 2.2 4.0 μs I_{DD(HSI)}(2) HSI oscillator power consumption 60 80 μΑ

Table 32. HSI oscillator characteristics (1)

- V_{DD} = 3.3 V, PLL OFF, T_A = -40 to 105 °C unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Guaranteed by characterization results.
- 4. Factory calibrated, parts not soldered.

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^{1.} Guaranteed by design, not tested in production.

 $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

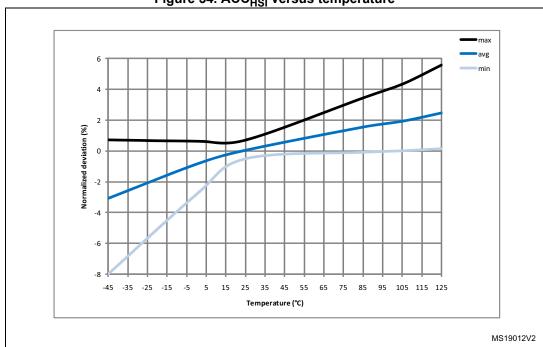


Figure 34. ACC_{HSI} versus temperature

Low-speed internal (LSI) RC oscillator

Table 33. LSI oscillator characteristics (1)

Symbol	Parameter	Min	Тур	Max	Unit
f _{LSI} ⁽²⁾	Frequency	17	32	47	kHz
t _{su(LSI)} (3)	LSI oscillator startup time	-	15	40	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.4	0.6	μΑ

^{1.} V_{DD} = 3 V, T_A = -40 to 105 °C unless otherwise specified.

^{2.} Guaranteed by characterization results, not tested in production.

^{3.} Guaranteed by design, not tested in production.

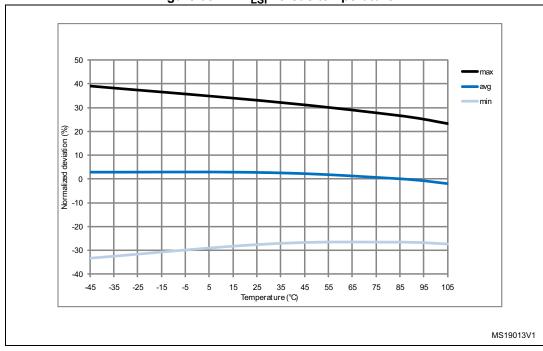


Figure 35. ACC_{LSI} versus temperature

6.3.10 PLL characteristics

The parameters given in *Table 34* and *Table 35* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Symbol Parameter Conditions Unit Min Тур Max PLL input clock⁽¹⁾ 0.95⁽²⁾ 2.10⁽²⁾ f_{PLL_IN} PLL multiplier output clock 120 f_{PLL_OUT} MHz 48 MHz PLL multiplier output clock 48 f_{PLL48}_OUT PLL VCO output 192 432 f_{VCO_OUT} VCO freq = 192 MHz 75 200 PLL lock time μs t_{LOCK} VCO freq = 432 MHz 100 300

Table 34. Main PLL characteristics

Table 34. Main PLL characteristics (continued)

Symbol	Parameter	Conditio	ns	Min	Тур	Max	Unit		
			RMS	ı	25	-			
	Cycle-to-cycle jitter	System clock 120 MHz	peak to peak	ı	±150	ı			
			RMS	-	15	-			
Jitter ⁽³⁾	Period Jitter					peak to peak	-	±200	-
	Main clock output (MCO) for RMII Ethernet	Cycle to cycle at on 1000 sample		-	32	-			
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at on 1000 sample		-	40	-			
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples		-	330	-			
I _{DD(PLL)} ⁽⁴⁾	PLL power consumption on VDD	VCO freq = 192 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	m A		
I _{DDA(PLL)} ⁽⁴	PLL power consumption on VDDA	VCO freq = 192 VCO freq = 432		0.30 0.55	-	0.40 0.85	mA		

Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.

Table 35. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f _{PLLI2S_IN}	PLLI2S input clock ⁽¹⁾	-		0.95 ⁽²⁾	1	2.10 ⁽²⁾	
f _{PLLI2S_OUT}	PLLI2S multiplier output clock	-		-	-	216	MHz
f _{VCO_OUT}	PLLI2S VCO output	-		192	-	432	
+	PLLI2S lock time	VCO freq = 192 MHz VCO freq = 432 MHz		75	-	200	ше
t _{LOCK}				100	-	300	μs
		Cycle to cycle at	RMS	-	90	-	
		12.288 MHz on 48 KHz period, N=432, R=5	peak to peak	-	±280	-	
Jitter ⁽³⁾	Master I2S clock jitter	Average frequency of 12.288 MHz N=432, R=5 on 1000 samples		-	90	-	ps
	WS I2S clock jitter	Cycle to cycle at on 1000 samples		-	400	-	



^{2.} Guaranteed by design, not tested in production.

^{3.} The use of 2 PLLs in parallel could degraded the Jitter up to +30%.

^{4.} Guaranteed by characterization results, not tested in production.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DD(PLLI2S)} ⁽⁴⁾	PLLI2S power consumption on V_{DD}	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45		0.40 0.75	mA
I _{DDA(PLLI2S)} (4)	PLLI2S power consumption on V_{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	ı	0.40 0.85	mA

Table 35, PLLI2S (audio PLL) characteristics (continued)

- 1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
- 2. Guaranteed by design, not tested in production.
- 3. Value given with main PLL running.
- 4. Guaranteed by characterization results, not tested in production.

6.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 42: EMI characteristics*). It is available only on the main PLL.

Symbol Parameter Max⁽¹⁾ Unit Min Тур Modulation frequency 10 KHz f_{Mod} Peak modulation depth md 0.25 2 % MODEPER * INCSTEP $2^{15}-1$

Table 36. SSCG parameters constraint

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = round[f_{PLL\ IN}/(4 \times f_{Mod})]$$

 $f_{PLL\ IN}$ and f_{Mod} must be expressed in Hz.

As an example:

If f_{PLL_IN} = 1 MHz and f_{MOD} = 1 kHz, the modulation depth (MODEPER) is given by equation 1:

MODEPER = round[
$$10^6/(4 \times 10^3)$$
] = 250

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

INCSTEP = round[
$$((2^{15} - 1) \times md \times PLLN)/(100 \times 5 \times MODEPER)$$
]

f_{VCO OUT} must be expressed in MHz.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

INCSTEP = round[
$$((2^{15} - 1) \times 2 \times 240)/(100 \times 5 \times 250)$$
] = 126md(quantitazed)%



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^{1.} Guaranteed by design, not tested in production.

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$\text{md}_{quantized}\% \,=\, (\text{MODEPER} \times \text{INCSTEP} \times 100 \times 5) / ((2^{15}-1) \times \text{PLLN})$$

As a result:

$$md_{quantized}\% = (250 \times 126 \times 100 \times 5)/((2^{15} - 1) \times 240) = 2.0002\%$$
(peak)

Figure 36 and *Figure 37* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL OUT} nominal.

 T_{mode} is the modulation period.

md is the modulation depth.

Figure 36. PLL output clock waveforms in center spread mode

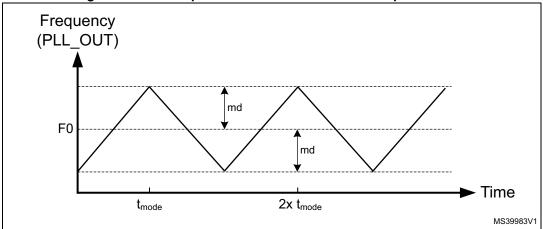
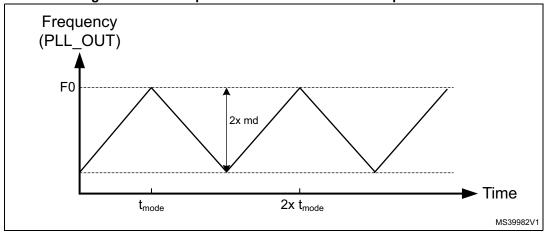


Figure 37. PLL output clock waveforms in down spread mode



6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = -40 to 105 $^{\circ}\text{C}$ unless otherwise specified.

Table 37. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DD} Supply cu		Write / Erase 8-bit mode V _{DD} = 1.8 V	-	5	-	
	Supply current	Write / Erase 16-bit mode V _{DD} = 2.1 V	-	8	-	mA
		Write / Erase 32-bit mode V _{DD} = 3.3 V	-	12	-	

Table 38. Flash memory programming

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
t _{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100 ⁽²⁾	μs
		Program/erase parallelism (PSIZE) = x 8	-	400	800	
t _{ERASE16KB}	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 16	1	300	600	ms
		Program/erase parallelism (PSIZE) = x 32	1	250	500	
t _{ERASE64KB}		Program/erase parallelism (PSIZE) = x 8	-	1200	2400	
	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 16	-	700	1400	ms
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
		Program/erase parallelism (PSIZE) = x 8	-	2	4	
t _{ERASE128KB}	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	s
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t _{ME}		Program/erase parallelism (PSIZE) = x 8	-	16	32	
	Mass erase time	Program/erase parallelism (PSIZE) = x 16	-	11	22	S
		Program/erase parallelism (PSIZE) = x 32	-	8	16	



Table 38. Flash memory programming (continued)

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
		32-bit program operation	2.7	-	3.6	
V_{prog}	Programming voltage	16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.8	-	3.6	

- 1. Guaranteed by characterization results, not tested in production.
- 2. The maximum programming time is measured after 100K erase operations.

Table 39. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
t _{prog}	Double word programming		-	16	100 ⁽²⁾	μs
t _{ERASE16KB}	Sector (16 KB) erase time	$T_A = 0$ to +40 °C	-	230	-	
t _{ERASE64KB}	Sector (64 KB) erase time	V _{DD} = 3.3 V	-	490	-	ms
t _{ERASE128KB}	Sector (128 KB) erase time	$V_{PP} = 8.5 \text{ V}$	-	875	-	
t _{ME}	Mass erase time		-	6.9	-	S
V _{prog}	Programming voltage	-	2.7	-	3.6	V
V _{PP}	V _{PP} voltage range	-	7	-	9	V
I _{PP}	Minimum current sunk on the V _{PP} pin	-	10	-	-	mA
t _{VPP} (3)	Cumulative time during which V _{PP} is applied	-	-	-	1	hour

- 1. Guaranteed by design, not tested in production.
- 2. The maximum programming time is measured after 100K erase operations.
- 3. V_{PP} must only be connected during programming/erasing.

Table 40. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
Symbol Parameter		Conditions	Min ⁽¹⁾	Oille
N _{END}	Endurance	$T_A = -40 \text{ to } +85 ^{\circ}\text{C} \text{ (6 suffix versions)}$ $T_A = -40 \text{ to } +105 ^{\circ}\text{C} \text{ (7 suffix versions)}$	10	kcycles
		1 kcycle ⁽²⁾ at T _A = 85 °C	30	
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 105 °C	10	Years
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	

- 1. Guaranteed by characterization results, not tested in production.
- $2. \quad \hbox{Cycling performed over the whole temperature range}.$

6.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling two LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 41*. They are based on the EMS levels and classes defined in application note AN1709.

Level/ Symbol **Parameter Conditions** Class $V_{DD} = 3.3 \text{ V, LQFP176, T}_{A} = +25 \text{ °C,}$ Voltage limits to be applied on any I/O pin to f_{HCLK} = 120 MHz, conforms to V_{FESD} 2B induce a functional disturbance IEC 61000-4-2 $V_{DD} = 3.3 \text{ V, LQFP176, T}_{A} =$ Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} +25 °C, f_{HCLK} = 120 MHz, conforms 4A V_{EFTB} pins to induce a functional disturbance to IEC 61000-4-2

Table 41. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. Note that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and pregualification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- · Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)



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Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC[®] code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Symbol Parameter		Conditions	Monitored	Max vs. [f _{HSE} /f _{CPU}]	Unit
Symbol	Farameter	Conditions	frequency band	25/120 MHz	Oilit
	V - 2.2 V T - 25 °C LOED176	0.1 to 30 MHz			
		V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running with ART enabled, peripheral clock disabled	30 to 130 MHz	25	dΒμV
			130 MHz to 1 GHz		
	Peak level		SAE EMI Level	4	-
S _{EMI}	reak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP176	0.1 to 30 MHz	28	
		package, conforming to SAE J1752/3	30 to 130 MHz	26	dΒμV
		EEMBC, code running with ART enabled, PLL spread spectrum	130 MHz to 1 GHz	22	
		enabled, peripheral clock disabled	SAE EMI level	4	-

Table 42. EMI characteristics

6.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Class **Symbol Ratings Conditions** Maximum value⁽¹⁾ Unit $T_A = +25 \, ^{\circ}C$ Electrostatic discharge voltage $2000^{(2)}$ 2 $V_{ESD(HBM)}$ (human body model) conforming to JESD22-A114 ٧ $T_A = +25 \, ^{\circ}C$ Electrostatic discharge voltage П 500 $V_{ESD(CDM)}$ (charge device model) conforming to JESD22-C101

Table 43. ESD absolute maximum ratings



- 1. Guaranteed by characterization results, not tested in production.
- 2. On V_{BAT} pin, $V_{ESD(HBM)}$ is limited to 1000 V.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 44. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +105 °C conforming to JESD78A	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below $V_{\rm SS}$ or above $V_{\rm DD}$ (for standard, 3 V-capable I/O pins) must be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in Table 45.

Table 45. I/O current injection susceptibility⁽¹⁾

Symbol		Functional s		
Symbol	Description	Negative injection	Positive injection	Unit
	Injected current on BOOT0 pin	-0	NA	
	Injected current on NRST pin	-0	NA	mA
I _{INJ}	Injected current on TTa pins: PA4 and PA5	-0	+5	IIIA
	Injected current on all FT pins	- 5	NA	

^{1.} NA stands for "not applicable".

Note:

It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.



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6.3.16 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 14: General operating conditions*.

All I/Os are CMOS and TTL compliant.

Table 46. I/O static characteristics

Symbol	Paran	neter	Conditions	Min	Тур	Max	Unit
	FT, TTa and NRS		1.7 V≤ V _{DD} ≤ 3.6 V	-	-	0.35V _{DD} -0.04 ⁽¹⁾ 0.3V _{DD} ⁽²⁾	-
V _{IL} BOOT0 I/O			1.75 V≤ V _{DD} ≤ 3.6 V, -40 °C≤ T _A ≤ 105 °C	-	-	0.1V _{DD} +0.1 ⁽¹⁾	V
	input low level vo	oltage	$1.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V},$ $0 \text{ °C} \le \text{T}_{A} \le 105 \text{ °C}$	-	-	0.1 V DD+0.1V	
	FT, TTa and NRS input high level v		1.7 V≤ V _{DD} ≤ 3.6 V	0.45V _{DD} +0.3 ⁽¹⁾ 0.7V _{DD} ⁽²⁾	-	-	
V _{IH}	BOOT0 I/O		$1.75 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V},$ -40 °C \le T_A \le 105 °C	0.17V _{DD} +0.7 ⁽¹⁾		_	٧
	input high level v	oltage	$1.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V},$ $0 \text{ °C} \le \text{T}_{A} \le 105 \text{ °C}$	0.17 V _{DD} +0.7 × 7	-	-	
	FT, TTa and NRS input hysteresis	ST I/O	1.7 V≤ V _{DD} ≤ 3.6 V	0.45V _{DD} +0.3 ⁽¹⁾	ı	-	
V _{HYS}	BOOT0 I/O		$1.75 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V},$ $-40 \text{ °C} \le \text{T}_{A} \le 105 \text{ °C}$	10%V _{DDIO} ⁽¹⁾⁽³⁾	-	-	V
	input hysteresis		$1.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V},$ $0 \text{ °C} \le \text{T}_{A} \le 105 \text{ °C}$	100 ⁽¹⁾	-	-	
I _{lkg}	I/O input leakage	current (4)	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA
ікд	I/O FT input leak	age current (5)	V _{IN} = 5 V	-	-	3	μπ
R _{PU}	Weak pull-up equivalent resistor ⁽⁶⁾	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{SS}$	30	40	50	
	resistor	PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	-	7	10	14	k0
R _{PD}	All pins except for PA10/PB12 Weak pull-down equivalent OTG_HS_ID, OTG_HS_ID)	$V_{IN} = V_{DD}$	30	40	50	kΩ	
	resistor ⁽⁷⁾ PA10/PB12 (OTG_FS_ID, OTG_HS_ID)		-	7	10	14	



Table 46. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{IO} (8)	I/O pin capacitance	-	-	5	-	pF

- 1. Guaranteed by design, not tested in production.
- 2. Guaranteed by tests in production.
- 3. With a minimum of 200 mV.
- Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to Table 45: I/O current injection susceptibility
- To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to Table 45: I/O current injection susceptibility
- 6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
- Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
- 8. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in *Figure 38*.

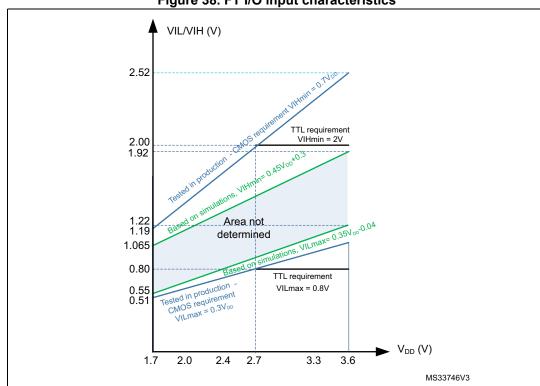


Figure 38. FT I/O input characteristics

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 that can sink

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or source up to ± 3 mA. When using the PC13 to PC15 GPIOs in output mode, the speed must not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins that can drive current must be limited to respect the absolute maximum rating specified in Section 6.2:

- The sum of the currents sourced by all the I/Os on V_{DD}, plus the maximum Run consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating I_{VDD} (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see *Table 12*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 47* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 47. Output voltage characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
V _{OL} ⁽²⁾	Output low level voltage for an I/O pin when 8 pins are sunk at same time	CMOS ports	-	0.4	
V _{OH} ⁽³⁾	Output high level voltage for an I/O pin when 8 pins are sourced at same time	2.7 V < V _{DD} < 3.6 V	V _{DD} -0.4	-	
V _{OL} (2)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	TTL ports I _{IO} =+ 8mA	-	0.4	
V _{OH} ⁽³⁾	Output high level voltage for an I/O pin when 8 pins are sourced at same time	2.7 V < V _{DD} < 3.6 V	2.4	-	V
V _{OL} ⁽²⁾⁽⁴⁾	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I _{IO} = +20 mA	-	1.3	V
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin when 8 pins are sourced at same time	2.7 V < V _{DD} < 3.6 V	V _{DD} -1.3	-	
V _{OL} ⁽²⁾⁽⁴⁾	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I _{IO} = +6 mA	-	0.4	
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin when 8 pins are sourced at same time	2 V < V _{DD} < 2.7 V	V _{DD} -0.4	-	

PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited: the speed must not exceed 2 MHz with a maximum load of 30 pF and these I/Os must not be used as a current source (e.g. to drive an LED).

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 39* and *Table 48*, respectively.



^{2.} The $I_{|O}$ current sunk by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of $I_{|O|}$ (I/O ports and control pins) must not exceed I_{VSS} .

^{3.} The $I_{\rm IO}$ current sourced by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of $I_{\rm IO}$ (I/O ports and control pins) must not exceed $I_{\rm VDD}$.

^{4.} Guaranteed by characterization results, not tested in production.

Unless otherwise specified, the parameters given in *Table 48* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 48. I/O AC characteristics⁽¹⁾

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
			$C_L = 50 \text{ pF, V}_{DD} > 2.7 \text{ V}$	C _L = 50 pF, V _{DD} > 2.7 V	-	-	4	
		Maximum fraguancy ⁽²⁾	C _L = 50 pF, V _{DD} > 1.8 V	-	-	2	MHz	
	'max(IO)out	f _{max(IO)out} Maximum frequency ⁽²⁾	C _L = 10 pF, V _{DD} > 2.7 V	-	-	8	IVII IZ	
00			C _L = 10 pF, V _{DD} > 1.8 V	-	-	4		
	t _{f(IO)out} / t _{r(IO)out}	Output high to low level fall time and output low to high level rise time	C _L = 50 pF, V _{DD} = 1.8 V to 3.6 V	-	-	100	ns	
			C _L = 50 pF, V _{DD} > 2.7 V	-	-	25		
	f _{max(IO)out}	f Mayir	Maximum fraguanay(2)	C _L = 50 pF, V _{DD} > 1.8 V	-	-	12.5	MHz
		Maximum frequency ⁽²⁾	C _L = 10 pF, V _{DD} > 2.7 V	-	-	50 ⁽³⁾	- IVITZ	
01			C _L = 10 pF, V _{DD} > 1.8 V	-	20	20		
01		Output high to low level fall	C _L = 50 pF, V _{DD} > 2.7 V	-	-	10		
	t _{f(IO)out} /		Output high to low level fall time and output low to high	C _L = 50 pF, V _{DD} > 1.8 V	-	-	20	no
	t _{r(IO)out}	level rise time	C _L = 10 pF, V _{DD} > 2.7 V	-	-	6	ns	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	10		
			C _L = 40 pF, V _{DD} > 2.7 V	-	-	25		
	f	Maximum frequency ⁽²⁾	C _L = 40 pF, V _{DD} > 1.8 V	-	-	20	MHz	
	^I max(IO)out	iviaximum nequency.	C _L = 10 pF, V _{DD} > 2.7 V	-	-	100 ⁽³⁾	IVITIZ	
10			C _L = 10 pF, V _{DD} > 1.8 V	-	-	50 ⁽³⁾		
			C _L = 40 pF, V _{DD} > 2.7 V	-	-	6	- ns	
	t _{f(IO)out} /	Output high to low level fall time and output low to high	C _L = 40 pF, V _{DD} > 1.8 V	-	-	10		
	t _{r(IO)out}	level rise time	C _L = 10 pF, V _{DD} > 2.7 V	-	-	4		
			C _L = 10 pF, V _{DD} > 1.8 V	-	-3	6		



Table 48. I/O A0	characteristics ⁽¹⁾	(continued)
------------------	--------------------------------	-------------

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
			C _L = 30 pF, V _{DD} > 2.7 V	-	-	100 ⁽³⁾	
a.(.o)out		C _L = 30 pF, V _{DD} > 1.8 V	-	-	50 ⁽³⁾	MHz	
		C _L = 10 pF, V _{DD} > 2.7 V	-	-	120 ⁽³⁾		
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	100 ⁽³⁾	
11			C _L = 30 pF, V _{DD} > 2.7 V	-	-	4	
t _{f(IO)} out [/] t _{r(IO)} out	t _{f(IO)out} /		C _L = 30 pF, V _{DD} > 1.8 V	-	-	6	200
	level rise time	C _L = 10 pF, V _{DD} > 2.7 V	-	-	2.5	ns	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	4	
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns

- The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F20/21xxx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
- 2. The maximum frequency is defined in Figure 39.
- 3. For maximum frequencies above 50 MHz and $\ensuremath{V_{DD}}$ above 2.4 V, the compensation cell must be used.

90% 1,0% **EXTERNAL** tr(IO)out ^{- t}f(IO)out OUTPUT ON CL Maximum frequency is achieved if $(t_r + t_f) \le (2/3)T$ and if the duty cycle is (45-55%) when loaded by CL specified in the table " I/O AC characteristics". ai14131d

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Figure 39. I/O AC characteristics definition

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6.3.17 **NRST** pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, RPIJ (see Table 49).

Unless otherwise specified, the parameters given in *Table 49* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{PU}	Weak pull-up equivalent resistor ⁽¹⁾	$V_{IN} = V_{SS}$	30	40	50	kΩ
V _{F(NRST)} ⁽²⁾	NRST input filtered pulse	-	-	-	100	ns
V _{NF(NRST)} ⁽²⁾	NRST input not filtered pulse	V _{DD} > 2.7 V	300	-	-	113
T _{NRST_OUT}	Generated reset pulse duration	Internal reset source	20	-	-	μs

Table 49. NRST pin characteristics

2. Guaranteed by design, not tested in production.

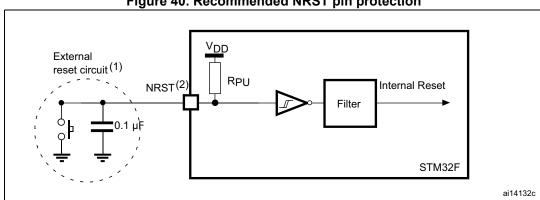


Figure 40. Recommended NRST pin protection

- The reset network protects the device against parasitic resets.
- The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 49*. Otherwise the reset is not taken into account by the device.

The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

6.3.18 TIM timer characteristics

The parameters given in *Table 50* and *Table 51* are guaranteed by design.

Refer to *Section 6.3.16: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 50. Characteristics of TIMx connected to the APB1 domain⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
	Timer resolution time	AHB/APB1 prescaler distinct from 1, f _{TIMxCLK} = 60 MHz	1	-	t _{TIMxCLK}
t _{res(TIM)}			16.7	-	ns
, ,		AHB/APB1 prescaler = 1, f _{TIMxCLK} = 30 MHz	1	-	t _{TIMxCLK}
			33.3	-	ns
f _{EXT}	Timer external clock		0	f _{TIMxCLK} /2	MHz
'EXI	frequency on CH1 to CH4		0	30	MHz
Res _{TIM}	Timer resolution		-	16/32	bit
	16-bit counter clock period	f _{TIMxCLK} = 60 MHz APB1= 30 MHz	1	65536	t _{TIMxCLK}
t	when internal clock is selected		0.0167	1092	μs
^t COUNTER	32-bit counter clock period when internal clock is selected		1	-	t _{TIMxCLK}
			0.0167	71582788	μs
tuan course	Maximum possible count		-	65536 × 65536	t _{TIMxCLK}
t _{MAX_COUNT}	IVIAAIITIUITI POSSIDIE COUITE		-	71.6	S

^{1.} TIMx is used as a general term to refer to the TIM2, TIM3, TIM4, TIM5, TIM6, TIM7, and TIM12 timers.

Table 51. Characteristics of TIMx connected to the APB2 domain⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t _{res(TIM)}	Timer resolution time	AHB/APB2 prescaler distinct from 1, f _{TIMxCLK} = 120 MHz	1	-	t _{TIMxCLK}
			8.3	-	ns
		AHB/APB2 prescaler = 1, f _{TIMxCLK} = 60 MHz	1	-	t _{TIMxCLK}
			16.7	-	ns

Symbol	Parameter	Conditions	Min	Max	Unit
f _{EXT}	Timer external clock		0	f _{TIMxCLK} /2	MHz
'EXI	frequency on CH1 to CH4		0	60	IVII IZ
Res _{TIM}	Timer resolution	400 MI	-	16	bit
+	16-bit counter clock period when internal clock is selected	f _{TIMxCLK} = 120 MHz APB2 = 60 MHz	1	65536	t _{TIMxCLK}
^t COUNTER			0.0083	546	μs
t _{MAX} COUNT	Maximum possible count		-	65536 × 65536	t _{TIMxCLK}
IVIAA_COUNT	maximum possible sount		-	35.79	s

Table 51. Characteristics of TIMx connected to the APB2 domain⁽¹⁾ (continued)

6.3.19 Communications interfaces

I²C interface characteristics

STM32F205xx and STM32F207xx I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 52*. Refer also to *Section 6.3.16*: I/O port characteristics for more details on the input/output alternate function characteristics (SDA and SCL).

Standard mode Fast mode $I^2C^{(1)(2)}$ $I^2C^{(1)(2)}$ **Symbol Parameter** Unit Min Min Max Max 1.3 SCL clock low time 4.7 tw(SCLL) μs SCL clock high time 4.0 0.6 tw(SCLH) 250 t_{su(SDA)} SDA setup time 100 3450⁽³⁾ 900(3) SDA data hold time t_{h(SDA)} t_{r(SDA)} ns SDA and SCL rise time 1000 300 $t_{r(SCL)}$ t_{f(SDA)} SDA and SCL fall time 300 300 t_{f(SCL)} Start condition hold time 4.0 0.6 t_{h(STA)} Repeated Start condition setup time 4.7 0.6 t_{su(STA)} μs Stop condition setup time 4.0 0.6 t_{su(STO)} Stop to Start condition time (bus free) 4.7 1.3 t_{w(STO:STA)}

Table 52. I²C characteristics

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^{1.} TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

	,						
Symbol	Parameter	Standard mode I ² C ⁽¹⁾⁽²⁾		Fast mode I ² C ⁽¹⁾⁽²⁾		Unit	
		Min	Max	Min	Max		
C _b	Capacitive load for each bus line	-	400	-	400	pF	
Pulse width of the spikes suppressed by the analog filter		0	50 ⁽⁴⁾	0	50	ns	

Table 52. I²C characteristics (continued)

- 1. Guaranteed by design, not tested in production.
- f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies, and a multiple of 10 MHz to reach the 400 kHz maximum I²C fast mode clock.
- The maximum Data hold time has only to be met if the interface does not stretch the low period of the SCL signal.
- 4. The minimum width of the spikes filtered by the analog filter is above $t_{SP(max)}$.

V_{DD_I2C} V_{DD} I2C STM32Fxx I2C bus START REPEATED START **START** tsu(STA) SDA + tsu(SDA) ^tw(STO:STA) **←** ^th(SDA) tw(SCLH) SCL tsu(STO) ^tr(SCL) → ai14979c

Figure 41. I²C bus AC waveforms and measurement circuit

- 1. R_S= series protection resistor.
- 2. R_P = external pull-up resistor.
- 3. V_{DD_I2C} is the I^2C bus power supply.

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 $f_{SCL} (kHz) \begin{tabular}{ll} & & & & & & \\ \hline $f_{SCL} (kHz)$ & & & & & \\ \hline $R_P = 4.7 \ k\Omega$ & & & \\ \hline 400 & & & & & \\ \hline 300 & & & & & \\ \hline 300 & & & & & \\ \hline 300 & & & & & \\ \hline 200 & & & & & \\ \hline 200 & & & & & \\ \hline 200 & & & & & \\ \hline 100 & & & & & \\ \hline 200 & & & & & \\ \hline 200 & & & & & \\ \hline 200 & & & \\ \hline 200 & & & & \\ \hline 200 & & \\ \hline 200 & & & \\ \hline 200 & & & \\ \hline 200 & & \\ \hline $$

Table 53. SCL frequency $(f_{PCLK1} = 30 \text{ MHz.}, V_{DD} = 3.3 \text{ V})^{(1)(2)}$

I²S - SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 54* for SPI or in *Table 55* for I^2S are derived from tests performed under the ambient temperature, f_{PCLKX} frequency and V_{DD} supply voltage conditions summarized in *Table 14*.

Refer to Section 6.3.16: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Symbol	Parameter	Conditions	Min	Max	Unit
f _{SCK}	SDI alook froguency	SPI1 master/slave mode	-	30	MHz
1/t _{c(SCK)}	SPI clock frequency	SPI2/SPI3 master/slave mode	-	15	IVITZ
t _{r(SCL)}	SPI clock rise and fall time	1 1		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	· I Slave mode		70	%
t _{su(NSS)} ⁽¹⁾	NSS setup time	Slave mode	4t _{PCLK}	-	
t _{h(NSS)} ⁽¹⁾	NSS hold time	Slave mode	2t _{PCLK}	-	
t _{w(SCLH)} (1) t _{w(SCLL)} (1)	SCK high and low time	Master mode, f _{PCLK} = 30 MHz, presc = 2	t _{PCLK} -3	t _{PCLK} +3	
t _{su(MI)} (1) t _{su(SI)} (1)	Data input setup time	Master mode	5	-	
t _{su(SI)} ⁽¹⁾	Data input setup time	Slave mode	5	-	ns
t _{h(MI)} (1)	Data input hold time	Master mode	5	-	
t _{h(MI)} (1) t _{h(SI)} (1)	Data input hold time	Slave mode	4	-	
t _{a(SO)} (1)(2)	Data output access time	Slave mode, f _{PCLK} = 30 MHz	0	3t _{PCLK}	
t _{dis(SO)} (1)(3)	Data output disable time	Slave mode	2	10	

Table 54. SPI characteristics

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^{1.} R_P = External pull-up resistance, f_{SCL} = I^2C speed,

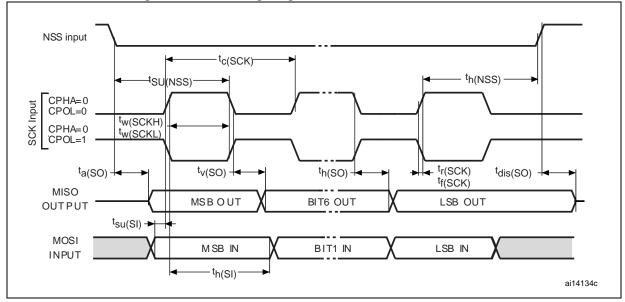
For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the
tolerance on the achieved speed ±2%. These variations depend on the accuracy of the external
components used to design the application.

Table 54. SPI characteristics (continued)

Symbol	Parameter Conditions			Max	Unit
t _{v(SO)} (1)	Data output valid time	Slave mode (after enable edge)	-	25	
t _{v(MO)} ⁽¹⁾	Data output vallu tillie	Master mode (after enable edge)	-	5	ns
t _{h(SO)} ⁽¹⁾	Data output hold time	Slave mode (after enable edge)	15	-	115
t _{h(MO)} ⁽¹⁾	Data output hold time	Master mode (after enable edge)	2	-	

- 1. Guaranteed by characterization results, not tested in production.
- 2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
- Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 42. SPI timing diagram - Slave mode and CPHA = 0



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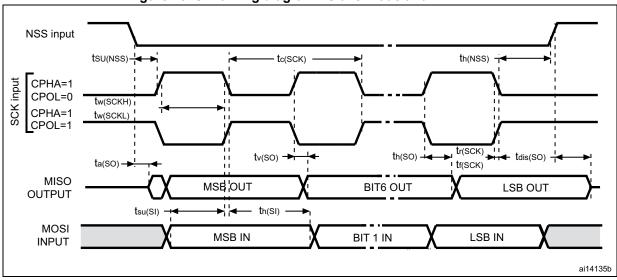
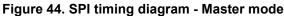


Figure 43. SPI timing diagram - Slave mode and CPHA = 1



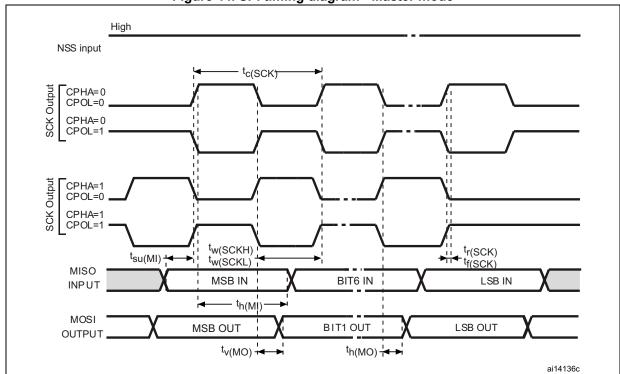


Table 55. I²S characteristics

Symbol	Parameter Conditions		Min	Max	Unit
f _{CK} 1/t _{c(CK)}	I ² S clock frequency	Master, 16-bit data, audio frequency = 48 kHz, main clock disabled	1.23	1.24	MHz
		Slave	0	64 F _S ⁽¹⁾	
$\begin{matrix} t_{r(CK)} \\ t_{f(CK)} \end{matrix}$	I ² S clock rise and fall time	Capacitive load C _L = 50 pF	-	(2)	
t _{v(WS)} (3)	WS valid time	Master	0.3	-	
t _{h(WS)} (3)	WS hold time	Master	0	-	
t _{su(WS)} (3)	WS setup time	Slave	3	-	
t _{h(WS)} (3)	WS hold time	Slave	0	-	
t _{w(CKH)} (3) t _{w(CKL)} (3)	CK high and low time	Master f _{PCLK} = 30 MHz	396	-	200
$t_{su(SD_MR)}^{(3)}_{(3)}$ $t_{su(SD_SR)}^{(3)}$	Data input setup time	Master receiver Slave receiver	45 0	-	ns
$t_{h(SD_MR)}^{(3)(4)}_{(3)(4)}$ $t_{h(SD_SR)}^{(3)(4)}$	Data input hold time	Master receiver: f _{PCLK} = 30 MHz, Slave receiver: f _{PCLK} = 30 MHz	13 0	-	
t _{v(SD_ST)} (3)(4)	Data output valid time	Slave transmitter (after enable edge)	-	30	
t _{h(SD_ST)} (3)	Data output hold time	Slave transmitter (after enable edge)	10	-	
t _{v(SD_MT)} (3)(4)	Data output valid time	Master transmitter (after enable edge)	-	6	
t _{h(SD_MT)} (3)	Data output hold time	Master transmitter (after enable edge)	0	-	

F_S is the sampling frequency. Refer to the I2S section of the STM32F20xxx/21xxx reference manual for more details. f_{CK} values reflect only the digital peripheral behavior which leads to a minimum of (I2SDIV/(2*I2SDIV+ODD), a maximum of (I2SDIV+ODD)/(2*I2SDIV+ODD) and F_S maximum values for each mode/condition.

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^{2.} Refer to Table 48: I/O AC characteristics.

^{3.} Guaranteed by design, not tested in production.

^{4.} Depends on f_{PCLK} . For example, if f_{PCLK} =8 MHz, then T_{PCLK} = 1/ f_{PLCLK} =125 ns.

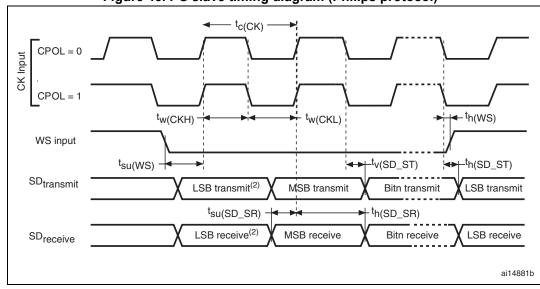


Figure 45. I²S slave timing diagram (Philips protocol)⁽¹⁾

1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

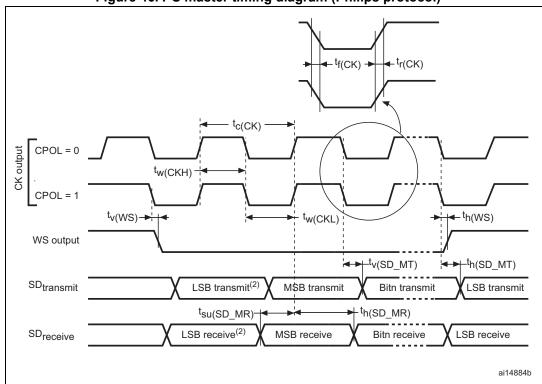


Figure 46. I²S master timing diagram (Philips protocol)⁽¹⁾

- 1. Guaranteed by characterization results, not tested in production.
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

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USB OTG FS characteristics

The USB OTG interface is USB-IF certified (Full-Speed). This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 56. USB OTG FS startup time

Symbol	Parameter	Max	Unit
t _{STARTUP} ⁽¹⁾	USB OTG FS transceiver startup time	1	μs

^{1.} Guaranteed by design, not tested in production.

Table 57. USB OTG FS DC electrical characteristics

Sym	bol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
	V _{DD} USB OTG FS operating voltage		3.0 ⁽²⁾	1	3.6	V	
Input V _{DI} ⁽³⁾		Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	1	-	
levels	V _{CM} ⁽³⁾ Differential common mode range Includes V _{DI} range		0.8	1	2.5	V	
V _{SE} ⁽³⁾		Single ended receiver threshold		1.3	1	2.0	
Output	V _{OL}	Static output level low	R_L of 1.5 k Ω to 3.6 $V^{(4)}$	ı	-	0.3	V
levels	V _{OH}	Static output level high	R_L of 15 kΩ to $V_{SS}^{(4)}$	2.8	-	3.6	V
R _F		PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	V _{IN} = V _{DD}	17	21	24	
I NE	PD	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	VIN - VDD	0.65	1.1	2.0	kΩ
		PA12, PB15 (USB_FS_DP, USB_HS_DP)	V _{IN} = V _{SS}	1.5	1.8	2.1	
R _{PU}		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	V _{IN} = V _{SS}	0.25	0.37	0.55	

^{1.} All the voltages are measured from the local ground potential.

^{2.} The STM32F205xx and STM32F207xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V $V_{\rm DD}$ voltage range.

^{3.} Guaranteed by design, not tested in production.

^{4.} R_L is the load connected on the USB OTG FS drivers

Cross over points

VCRS

VSS

tr

tr

ai14137b

Figure 47. USB OTG FS timings: definition of data signal rise and fall time

Table 58. USB OTG FS electrical characteristics⁽¹⁾

	Driver characteristics									
Symbol	Parameter	Conditions	Min	Max	Unit					
t _r	Rise time ⁽²⁾	C _L = 50 pF	4	20	ns					
t _f	Fall time ⁽²⁾	C _L = 50 pF	4	20	ns					
t _{rfm}	Rise/fall time matching	t _r /t _f	90	110	%					
V _{CRS}	Output signal crossover voltage	-	1.3	2.0	V					

^{1.} Guaranteed by design, not tested in production.

USB HS characteristics

Table 59 shows the USB HS operating voltage.

Table 59. USB HS DC electrical characteristics

Symb	ol	Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level	V_{DD}	USB OTG HS operating voltage	2.7	3.6	V

^{1.} All the voltages are measured from the local ground potential.

Table 60. Clock timing parameters

Parameter ⁽¹⁾		Symbol	Min	Nominal	Max	Unit
Frequency (first transition) 8-bit ±10%		F _{START_8BIT}	54	60	66	MHz
Frequency (steady state) ±500 ppm		F _{STEADY}	59.97	60	60.03	IVII IZ
Duty cycle (first transition) 8-bit ±10%		D _{START_8BIT}	40	50	60	%
Duty cycle (steady state) ±500	D _{STEADY}	49.975	50	50.025	/0	
Time to reach the steady state duty cycle after the first transit		T _{STEADY}	-	-	1.4	
Clock startup time after the	Peripheral	T _{START_DEV}	-	-	5.6	ms
de-assertion of SuspendM	Host	T _{START_HOST}	-	-	-	
PHY preparation time after the first transition of the input clock		T _{PREP}	-	-	-	μs

^{1.} Guaranteed by design, not tested in production.



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Measured from 10% to 90% of the data signal. For more detailed informations, refer to USB Specification -Chapter 7 (version 2.0).

Clock tsc tHC Control In (ULPI_DIR, ÙLPI_NXT) t_{SD+} -tHD data In (8-bit) - t_{DC} ^tDC Control out (ULPI_STP) t_{DD} data out (8-bit) ai17361c

Figure 48. ULPI timing diagram

Table 61. ULPI timing

Symbol	Parameter	Valu	ле ⁽¹⁾	Unit
	Parameter	Min	Max	Unit
4	Control in (ULPI_DIR) setup time		2.0	
t _{SC}	Control in (ULPI_NXT) setup time	-	1.5	
t _{HC}	Control in (ULPI_DIR, ULPI_NXT) hold time	0	-	
t _{SD}	Data in setup time	-	2.0	ns
t _{HD}	Data in hold time 0 -			
t _{DC}	Control out (ULPI_STP) setup time and hold time		9.2	
t _{DD}	Data out available from clock rising edge	-	10.7	

^{1.} V_{DD} = 2.7 V to 3.6 V and T_A = -40 to 85 °C.

Ethernet characteristics

Table 62 shows the Ethernet operating voltage.

Table 62. Ethernet DC electrical characteristics

Symb	ool	Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level	V_{DD}	Ethernet operating voltage	2.7	3.6	V

^{1.} All the voltages are measured from the local ground potential.

Table 63 gives the list of Ethernet MAC signals for the SMI (station management interface) and *Figure 49* shows the corresponding timing diagram.

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^tMDC ETH MDC ^td(MDIO) → ETH_MDIO(O) tsu(MDIO) th(MDIO) ETH_MDIO(I) ai15666d

Figure 49. Ethernet SMI timing diagram

Table 63. Dynamics characteristics: Ethernet MAC signals for SMI

Symbol	Rating	Min	Тур	Max	Unit
t_{MDC}	MDC cycle time (2.38 MHz)	411	420	425	
t _{d(MDIO)}	MDIO write data valid time	6	10	13	ns
t _{su(MDIO)}	Read data setup time	12	-	-	115
t _{h(MDIO)}	Read data hold time	0	-	-	

Table 64 gives the list of Ethernet MAC signals for the RMII and Figure 50 shows the corresponding timing diagram.

RMII_REF_CLK $t_{d(TXEN)}$ $t_{d(TXD)}$ $\mathsf{RMII}_\mathsf{TX}_\mathsf{EN}$ RMII_TXD[1:0] $t_{ih(RXD)}$ $t_{su(RXD)}$ $t_{su(CRS)}$ t_{ih(CRS)} RMII_RXD[1:0] RMII_CRS_DV ai15667

Figure 50. Ethernet RMII timing diagram

Table 64. Dynamics characteristics: Ethernet MAC signals for RMII

Symbol	Rating	Min	Тур	Max	Unit
$t_{su(RXD)}$	Receive data setup time	1	-	-	
t _{ih(RXD)}	Receive data hold time	1.5	-	-	
t _{su(CRS)}	Carrier sense set-up time	0	-	-	ne
t _{ih(CRS)}	Carrier sense hold time	2	-	-	ns
t _{d(TXEN)}	Transmit enable valid delay time	9	11	13	
t _{d(TXD)}	Transmit data valid delay time	9	11.5	14	



DS6329 Rev 18 119/181 *Table 65* gives the list of Ethernet MAC signals for MII and *Figure 50* shows the corresponding timing diagram.

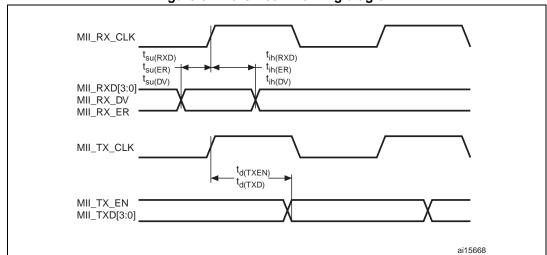


Figure 51. Ethernet MII timing diagram

Table 65. Dynamics characteristics: Ethernet MAC signals for MII

Symbol	Rating	Min	Тур	Max	Unit
t _{su(RXD)}	Receive data setup time	7.5	-	-	
t _{ih(RXD)}	Receive data hold time	1	-	-	
t _{su(DV)}	Data valid setup time	4	-	-	
t _{ih(DV)}	Data valid hold time	0	-	-	20
t _{su(ER)}	Error setup time	3.5	-	-	ns
t _{ih(ER)}	Error hold time	0	-	-	
t _{d(TXEN)}	Transmit enable valid delay time	-	11	14	
t _{d(TXD)}	Transmit data valid delay time	-	11	14	

CAN (controller area network) interface

Refer to Section 6.3.16: I/O port characteristics for more details on the input/output alternate function characteristics (CANTX and CANRX).

A7/

6.3.20 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 66* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 14*.

Table 66. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DDA}	Power supply	-	1.8 ⁽¹⁾	-	3.6	V
V _{REF+}	Positive reference voltage	-	1.8 ⁽¹⁾⁽²⁾	-	V_{DDA}	V
f	ADC clock frequency	$V_{DDA} = 1.8^{(1)}$ to 2.4 V	0.6	-	15	MHz
f _{ADC}	ADC Glock frequency	V _{DDA} = 2.4 to 3.6 V	0.6	-	30	IVII IZ
f _{TRIG} (3)	External trigger frequency	f _{ADC} = 30 MHz with 12-bit resolution	-	-	1764	kHz
		-	-	ı	17	1/f _{ADC}
V _{AIN}	Conversion voltage range ⁽⁴⁾	-	0 (V _{SSA} or V _{REF-} tied to ground)	1	V _{REF+}	V
R _{AIN} ⁽³⁾	External input impedance	See <i>Equation 1</i> for details	-	-	50	kΩ
R _{ADC} ⁽³⁾⁽⁵⁾	Sampling switch resistance	-	1.5	-	6	
C _{ADC} ⁽³⁾	Internal sample and hold capacitor	-	-	4	-	pF
t _{lat} (3)	Injection trigger conversion	f _{ADC} = 30 MHz	-	-	0.100	μs
'lat`'	latency	-	-	-	3 ⁽⁶⁾	1/f _{ADC}
t _{latr} (3)	Regular trigger conversion latency	f _{ADC} = 30 MHz	-	ı	0.067	μs
'latr'	regular ingger conversion ratericy	-	-	ı	2 ⁽⁶⁾	1/f _{ADC}
t _S (3)	Sampling time	f _{ADC} = 30 MHz	0.100	ı	16	μs
is.	Sampling time	-	3	-	480	1/f _{ADC}
t _{STAB} (3)	Power-up time	-	-	2	3	μs
		f _{ADC} = 30 MHz 12-bit resolution	0.5	-	16.40	
		f _{ADC} = 30 MHz 10-bit resolution	0.43	-	16.34	·
t _{CONV} ⁽³⁾	Total conversion time (including sampling time)	f _{ADC} = 30 MHz 8-bit resolution	0.37	-	16.27	- µs
		f _{ADC} = 30 MHz 6-bit resolution	0.3	-	16.20	
		9 to 492 (t _S for samplinapproximation)	ng +n-bit resolution	for succ	cessive	1/f _{ADC}



	Tubic 00. A	bo characteristics (continuca			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		12-bit resolution Single ADC	-	-	2	
f _S ⁽³⁾	Sampling rate (f _{ADC} = 30 MHz)	12-bit resolution Interleaved Dual ADC mode	-	-	3.75	Msps
		12-bit resolution Interleaved Triple ADC mode	-	-	6	
I _{VREF+} (3)	ADC V _{REF} DC current consumption in conversion mode	-	-	300	500	μA
I _{VDDA} ⁽³⁾	ADC VDDA DC current consumption in conversion mode	-	-	1.6	1.8	mA

Table 66. ADC characteristics (continued)

- 1. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD} , the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16).
- 2. It is recommended to maintain the voltage difference between V_{REF+} and V_{DDA} below 1.8 V.
- 3. Guaranteed by characterization results, not tested in production.
- 4. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} .
- 5. $\rm R_{ADC}$ maximum value is given for $\rm V_{DD}$ =1.8 V, and minimum value for $\rm V_{DD}$ =3.3 V.
- 6. For external triggers, a delay of 1/f_{PCLK2} must be added to the latency specified in *Table* 66.

Equation 1: R_{AIN} max formula

$$\mathsf{R}_{\mathsf{AIN}} \, = \, \frac{(\mathsf{k} - 0.5)}{\mathsf{f}_{\mathsf{ADC}} \times \mathsf{C}_{\mathsf{ADC}} \times \mathsf{In}(2^{\mathsf{N} + 2})} - \mathsf{R}_{\mathsf{ADC}}$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 67. ADC accuracy (1)

Symbol	Parameter	Test conditions	Тур	Max ⁽²⁾	Unit
ET	Total unadjusted error		±2	±5	
EO	Offset error	f _{PCLK2} = 60 MHz,	±1.5	±2.5	
EG	Gain error	$f_{ADC} = 30 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega,$ $V_{DDA} = 1.8^{(3)} \text{ to } 3.6 \text{ V}$	±1.5	±3	LSB
ED	Differential linearity error	$V_{DDA} = 1.8^{(3)} \text{ to } 3.6 \text{ V}$	±1	±2	
EL	Integral linearity error		±1.5	±3	

- 1. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
- 2. Guaranteed by characterization results, not tested in production.
- On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16).

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins must be avoided as this significantly reduces the accuracy of the conversion



being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in Section 6.3.16 does not affect the ADC accuracy.

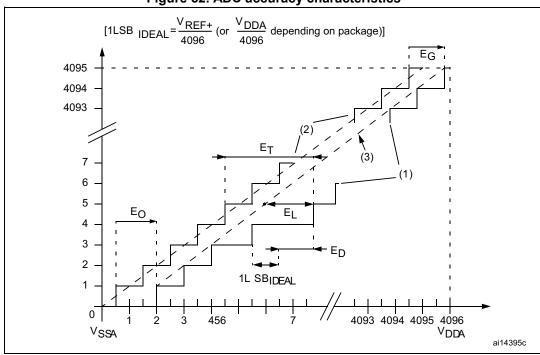
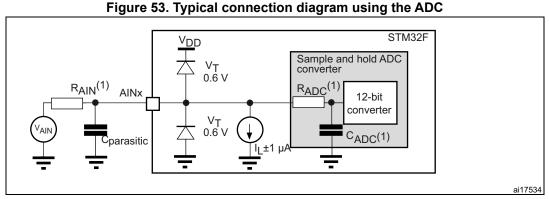


Figure 52. ADC accuracy characteristics

- Example of an actual transfer curve.
- 2. Ideal transfer curve.

correlation line.

- 3. End point correlation line.
- 4. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves. EO = Offset Error: deviation between the first actual transition and the first ideal one. EG = Gain Error: deviation between the last ideal transition and the last actual one. ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one. EL = Integral Linearity Error: maximum deviation between any actual transition and the end point



- 1. Refer to *Table 66* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
- C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C_{parasitic} value downgrades conversion accuracy. To remedy this, f_{ADC} must be reduced.

4

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General PCB design guidelines

Power supply decoupling must be performed as shown in Figure 54 or Figure 55, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors must be ceramic (good quality), placed as close as possible to the chip.

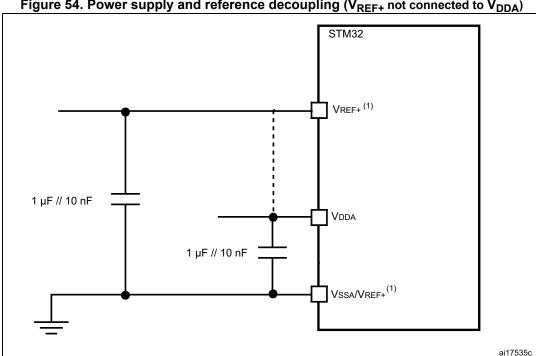


Figure 54. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



 V_{REF+} and V_{REF-} inputs are both available on UFBGA176 package. V_{REF+} is also available on all packages except for LQFP64. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .

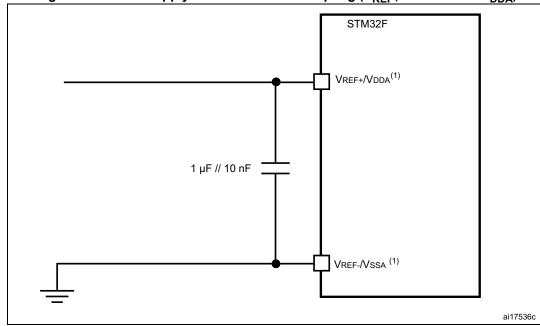


Figure 55. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})

6.3.21 DAC electrical characteristics

Table 68. DAC characteristics

Symbol	Parameter	Min	Тур	Max	Unit	Comments
V_{DDA}	Analog supply voltage	1.8 ⁽¹⁾	-	3.6		-
V _{REF+}	Reference supply voltage	1.8 ⁽¹⁾	-	3.6	V	$V_{REF+} \le V_{DDA}$
V_{SSA}	Ground	0	-	0		-
R _{LOAD} (2)	Resistive load with buffer ON	5	-	-		-
R _O ⁽²⁾	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 M Ω
C _{LOAD} ⁽²⁾	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min ⁽²⁾	Lower DAC_OUT voltage with buffer ON	0.2	-	-	.,	Gives the maximum output excursion of the DAC. Corresponds to 12-bit input
DAC_OUT max ⁽²⁾	Higher DAC_OUT voltage with buffer ON	-	ı	V _{DDA} – 0.2	V	code (0x0E0) to (0xF1C) at V _{REF+} = 3.6 V and (0x1C7) to (0xE38) at V _{REF+} = 1.8 V
DAC_OUT min ⁽²⁾	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	Gives the maximum output excursion of
DAC_OUT max ⁽²⁾	Higher DAC_OUT voltage with buffer OFF	-	-	V _{REF+} – 1LSB	٧	the DAC.



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V_{REF+} and V_{REF-} inputs are both available on UFBGA176 package. V_{REF+} is also available on all packages except for LQFP64. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

Table 68. DAC characteristics (continued)

Symbol	Parameter	Min	Тур	Max	Unit	Comments
I _{VREF+} (4)	DAC DC V _{REF} current consumption in quiescent	-	170	240	μΑ	With no load, worst code (0x800) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
VREF+`	mode (Standby mode)	-	50	75	μΑ	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
	DAC DC V _{DDA} current	-	280	380		With no load, middle code (0x800) on the inputs
I _{DDA} ⁽⁴⁾	consumption in quiescent mode ⁽³⁾	-	475	625	μA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
DNL ⁽⁴⁾	Differential non linearity Difference between two	-	-	±0.5		Given for the DAC in 10-bit configuration.
	consecutive code-1LSB)	-	ı	±2		Given for the DAC in 12-bit configuration.
INL ⁽⁴⁾	Integral non linearity (difference between measured value at Code i	-	-	±1	LSB	Given for the DAC in 10-bit configuration.
INL	and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±4		Given for the DAC in 12-bit configuration.
	Offset error	-	-	±10	mV	-
Offset ⁽⁴⁾	(difference between measured value at Code	-	-	±3	LSB	Given for the DAC in 10-bit at V _{REF+} = 3.6 V
	(0x800) and the ideal value = V _{REF+} /2)	-	-	±12	LOD	Given for the DAC in 12-bit at $V_{REF+} = 3.6 \text{ V}$
Gain error ⁽⁴⁾	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
t _{SETTLING} ⁽⁴⁾	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±4LSB	-	3	6	μs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ k Ω
THD ⁽⁴⁾	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$
Update rate ⁽²⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50 \text{ pF},$ $R_{LOAD} \geq 5 \text{ k}\Omega$



Symbol	Parameter	Min	Тур	Max	Unit	Comments
t _{WAKEUP} ⁽⁴⁾	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10		$\begin{split} &C_{LOAD} \leq \ 50 \ \text{pF}, \ R_{LOAD} \geq 5 \ \text{k}\Omega \\ &\text{input code between lowest and highest} \\ &\text{possible ones}. \end{split}$
PSRR+ ⁽²⁾	Power supply rejection ratio (to V _{DDA}) (static DC measurement)	-	– 67	-40	dB	No R _{LOAD} , C _{LOAD} = 50 pF

Table 68. DAC characteristics (continued)

- On devices in WLCSP64+2 package, if IRROFF is set to V_{DD} , the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see Section 3.16).
- Guaranteed by design, not tested in production.
- The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
- 4. Guaranteed by characterization results, not tested in production.

Buffered/Non-buffered DAC Buffer(1) R_L DAC_OUTx 12-bit digital to analog converter ai17157V2

Figure 56. 12-bit buffered/non-buffered DAC

The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly, without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.22 Temperature sensor characteristics

Table 69. Temperature sensor characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T _L ⁽¹⁾	V _{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope ⁽¹⁾	Average slope	-	2.5	-	mV/°C
V ₂₅ ⁽¹⁾	Voltage at 25 °C	-	0.76	-	V
t _{START} (2)	Startup time	-	6	10	μs
T _{S_temp} ⁽²⁾	ADC sampling time when reading the temperature (1 °C accuracy)	10	-	-	μs

- 1. Guaranteed by characterization results, not tested in production.
- 2. Guaranteed by design, not tested in production.

6.3.23 V_{BAT} monitoring characteristics

Table 70. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Тур	Max	Unit
R	Resistor bridge for V _{BAT}	-	50	-	ΚΩ
Q	Ratio on V _{BAT} measurement	-	2	-	
Er ⁽¹⁾	Error on Q	-1	-	+1	%
T _{S_vbat} ⁽²⁾⁽²⁾	ADC sampling time when reading the V _{BAT} (1 mV accuracy)	5	-	-	μs

- 1. Guaranteed by design, not tested in production.
- 2. Shortest sampling time can be determined in the application by multiple iterations.

6.3.24 Embedded reference voltage

The parameters given in *Table 71* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 71. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{REFINT}	Internal reference voltage	-40 °C < T _A < +105 °C	1.18	1.21	1.24	V
T _{S_vrefint} (1)	ADC sampling time when reading the internal reference voltage	-	10	-	-	μs
V _{RERINT_s} ⁽²⁾	Internal reference voltage spread over the temperature range	V _{DD} = 3 V	-	3	5	mV
T _{Coeff} ⁽²⁾	Temperature coefficient	-	-	30	50	ppm/°C
t _{START} (2)	Startup time	-	-	6	10	μs

^{1.} Shortest sampling time can be determined in the application by multiple iterations.

6.3.25 FSMC characteristics

Asynchronous waveforms and timings

Figure 57 through *Figure 60* represent asynchronous waveforms, while *Table 72* through *Table 75* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- AddressSetupTime = 1
- AddressHoldTime = 1
- DataSetupTime = 1
- BusTurnAroundDuration = 0x0

In all timing tables, the T_{HCLK} is the HCLK clock period.

Ay/

^{2.} Guaranteed by design, not tested in production.

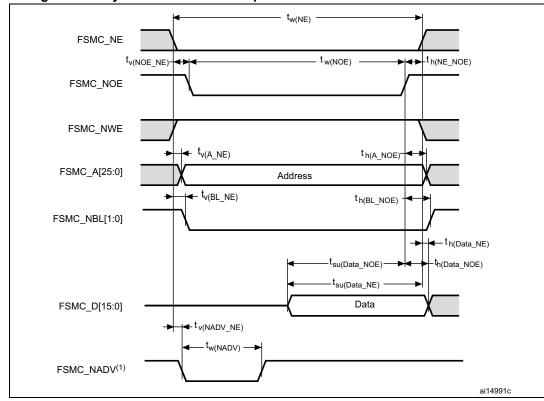


Figure 57. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms

1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Table 72. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	FSMC_NE low time	2 T _{HCLK} – 0.5	2 T _{HCLK} + 0.5	
t _{v(NOE_NE)}	FSMC_NEx low to FSMC_NOE low	0.5	2.5	
t _{w(NOE)}	FSMC_NOE low time	2 T _{HCLK} - 1	2 T _{HCLK} + 0.5	
t _{h(NE_NOE)}	FSMC_NOE high to FSMC_NE high hold time	0	-	
t _{v(A_NE)}	FSMC_NEx low to FSMC_A valid	-	4	
t _{h(A_NOE)}	Address hold time after FSMC_NOE high	0	-	
t _{v(BL_NE)}	FSMC_NEx low to FSMC_BL valid	-	0.5	ns
t _{h(BL_NOE)}	FSMC_BL hold time after FSMC_NOE high	0	-	115
t _{su(Data_NE)}	Data to FSMC_NEx high setup time	T _{HCLK} + 0.5	-	
t _{su(Data_NOE)}	Data to FSMC_NOEx high setup time	T _{HCLK} + 0.5	-	
t _{h(Data_NOE)}	Data hold time after FSMC_NOE high	0	-	
t _{h(Data_NE)}	Data hold time after FSMC_NEx high	0	-	
t _{v(NADV_NE)}	FSMC_NEx low to FSMC_NADV low	-	2.5	
t _{w(NADV})	FSMC_NADV low time	-	T _{HCLK} – 0.5	

^{1.} $C_L = 30 pF$.

2. Guaranteed by characterization results, not tested in production.



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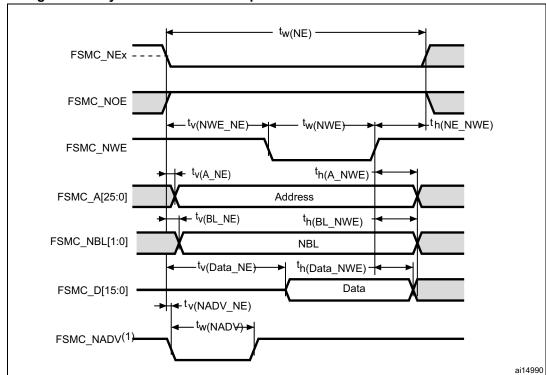


Figure 58. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms

1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Table 73. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	FSMC_NE low time	3 T _{HCLK}	3 T _{HCLK} + 4	
t _{v(NWE_NE})	FSMC_NEx low to FSMC_NWE low	T _{HCLK} – 0.5	T _{HCLK} + 0.5	
t _{w(NWE)}	FSMC_NWE low time	T _{HCLK} – 0.5	T _{HCLK} + 3	
t _{h(NE_NWE)}	FSMC_NWE high to FSMC_NE high hold time	T _{HCLK}	-	
t _{v(A_NE)}	FSMC_NEx low to FSMC_A valid	-	0	
t _{h(A_NWE)}	Address hold time after FSMC_NWE high	T _{HCLK} - 3	-	ns
t _{v(BL_NE)}	FSMC_NEx low to FSMC_BL valid	-	0.5	115
t _{h(BL_NWE)}	FSMC_BL hold time after FSMC_NWE high	T _{HCLK} – 1	-	
t _{v(Data_NE)}	Data to FSMC_NEx low to Data valid	-	T _{HCLK} + 5	
t _{h(Data_NWE)}	Data hold time after FSMC_NWE high	T _{HCLK} + 0.5	-	
t _{v(NADV_NE)}	FSMC_NEx low to FSMC_NADV low	-	2	
t _{w(NADV)}	FSMC_NADV low time	-	T _{HCLK} + 1.5	

^{1.} C_L = 30 pF.

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^{2.} Guaranteed by characterization results, not tested in production.

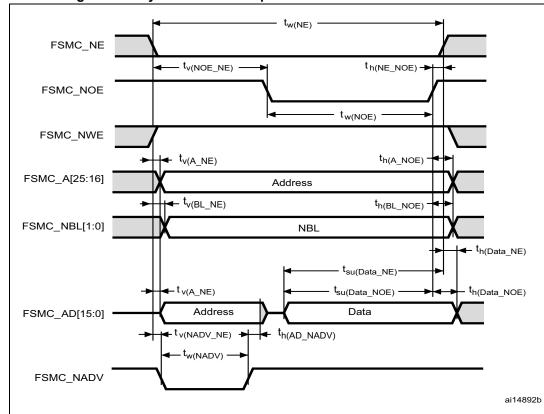


Figure 59. Asynchronous multiplexed PSRAM/NOR read waveforms

Table 74. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	FSMC_NE low time	3 T _{HCLK} - 1	3 T _{HCLK} + 1	
t _{v(NOE_NE)}	FSMC_NEx low to FSMC_NOE low	2 T _{HCLK}	2 T _{HCLK} + 0.5	
t _{w(NOE)}	FSMC_NOE low time	T _{HCLK} - 1	T _{HCLK} + 1	
t _{h(NE_NOE)}	FSMC_NOE high to FSMC_NE high hold time	0	-	
t _{v(A_NE)}	FSMC_NEx low to FSMC_A valid	-	2	
t _{v(NADV_NE)}	FSMC_NEx low to FSMC_NADV low	1	2.5	
t _{w(NADV)}	FSMC_NADV low time	T _{HCLK} – 1.5	T _{HCLK}	ns
t _{h(AD_NADV)}	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T _{HCLK}	-	
t _{h(A_NOE)}	Address hold time after FSMC_NOE high	T _{HCLK}	-	
t _{h(BL_NOE)}	FSMC_BL time after FSMC_NOE high	0	-	
t _{v(BL_NE)}	FSMC_NEx low to FSMC_BL valid	-	1	
t _{su(Data_NE)}	Data to FSMC_NEx high setup time	T _{HCLK} + 2	-	
t _{su(Data_NOE)}	Data to FSMC_NOE high setup time	T _{HCLK} + 3	-	



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Table 74. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
t _{h(Data_NE)}	Data hold time after FSMC_NEx high	0	-	ne
t _{h(Data_NOE)}	Data hold time after FSMC_NOE high	0	-	ns

^{1.} $C_L = 30 pF$.

Figure 60. Asynchronous multiplexed PSRAM/NOR write waveforms

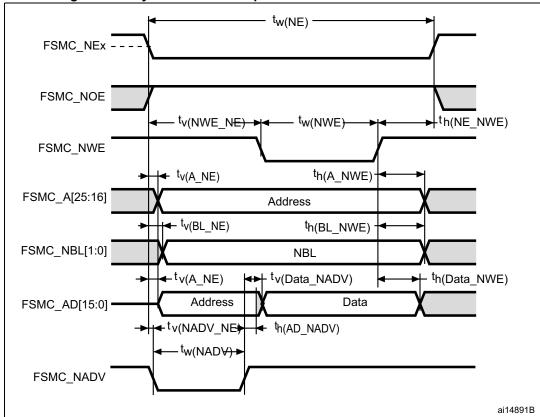


Table 75. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	FSMC_NE low time	4 T _{HCLK} - 1	4 T _{HCLK} + 1	
t _{v(NWE_NE)}	FSMC_NEx low to FSMC_NWE low	T _{HCLK} - 1	T _{HCLK}	
t _{w(NWE)}	FSMC_NWE low tim e	2 T _{HCLK}	2 T _{HCLK} + 1	
t _{h(NE_NWE)}	FSMC_NWE high to FSMC_NE high hold time	T _{HCLK} - 1	-	
t _{v(A_NE)}	FSMC_NEx low to FSMC_A valid	-	0	ns
t _{v(NADV_NE)}	FSMC_NEx low to FSMC_NADV low	1	2	
t _{w(NADV)}	FSMC_NADV low time	T _{HCLK} – 2	T _{HCLK} + 2	
t _{h(AD_NADV)}	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T _{HCLK}	-	



^{2.} Guaranteed by characterization results, not tested in production.

Unit **Symbol Parameter** Min Max T_{HCLK} - 0.5 Address hold time after FSMC NWE high t_{h(A_NWE)} FSMC BL hold time after FSMC NWE high T_{HCLK} - 1 t_{h(BL_NWE)} FSMC_NEx low to FSMC_BL valid 0.5 ns t_{v(BL NE)} FSMC NADV high to Data valid $T_{HCLK} + 2$ t_{v(Data_NADV)} Data hold time after FSMC_NWE high $T_{HCLK} - 0.5$ t_{h(Data_NWE)}

Table 75. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾⁽²⁾ (continued)

Synchronous waveforms and timings

Figure 61 through *Figure 64* represent synchronous waveforms, and *Table 77* through *Table 79* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FSMC_BurstAccessMode_Enable;
- MemoryType = FSMC_MemoryType_CRAM;
- WriteBurst = FSMC_WriteBurst_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F20xxx/21xxx reference manual)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the T_{HCLK} is the HCLK clock period.



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^{1.} $C_L = 30 pF$.

^{2.} Guaranteed by characterization results, not tested in production.

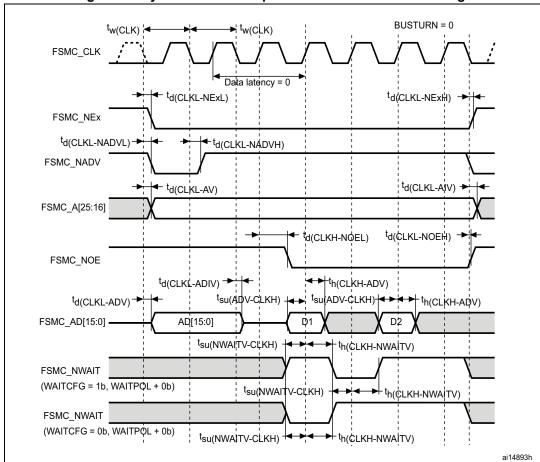


Figure 61. Synchronous multiplexed NOR/PSRAM read timings

Table 76. Synchronous multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	FSMC_CLK period	2 T _{HCLK}	-	
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x=02)	-	0	
t _{d(CLKL-NExH)}	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	
t _{d(CLKL-NADVL)}	FSMC_CLK low to FSMC_NADV low	-	1.5	
t _{d(CLKL-NADVH)}	FSMC_CLK low to FSMC_NADV high	2.5	-	
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	
t _{d(CLKL-AIV)}	FSMC_CLK low to FSMC_Ax invalid (x=1625)	0	-	ns
t _{d(CLKH-NOEL)}	FSMC_CLK high to FSMC_NOE low	-	1	
t _{d(CLKL-NOEH)}	FSMC_CLK low to FSMC_NOE high	1	-	
t _{d(CLKL-ADV)}	FSMC_CLK low to FSMC_AD[15:0] valid	-	3	
t _{d(CLKL-ADIV)}	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	
t _{su(ADV-CLKH)}	FSMC_A/D[15:0] valid data before FSMC_CLK high	5	-	
t _{h(CLKH-ADV)}	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	

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- 1. $C_L = 30 pF$.
- 2. Guaranteed by characterization results, not tested in production.

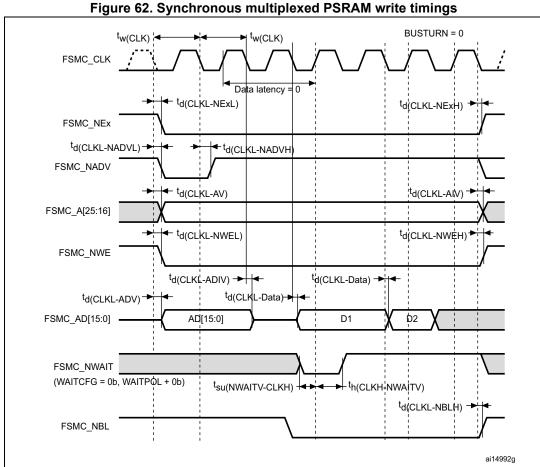


Table 77. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	FSMC_CLK period	2 T _{HCLK} - 1	-	
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x=02)	-	0	
t _{d(CLKL-NExH)}	FSMC_CLK low to FSMC_NEx high (x= 02)	2	-	
t _{d(CLKL-NADVL)}	FSMC_CLK low to FSMC_NADV low	-	2	
t _{d(CLKL-NADVH)}	FSMC_CLK low to FSMC_NADV high	3	-	ns
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	115
t _{d(CLKL-AIV)}	FSMC_CLK low to FSMC_Ax invalid (x=1625)	7	-	
t _{d(CLKL-NWEL)}	FSMC_CLK low to FSMC_NWE low	-	1	
t _{d(CLKL-NWEH)}	FSMC_CLK low to FSMC_NWE high	0	-	
t _{d(CLKL-ADIV)}	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	



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Table 77. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
t _{d(CLKL-DATA})	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	2	ns
t _{d(CLKL-NBLH)}	FSMC_CLK low to FSMC_NBL high	0.5	-	115

^{1.} $C_L = 30 pF$.

Figure 63. Synchronous non-multiplexed NOR/PSRAM read timings

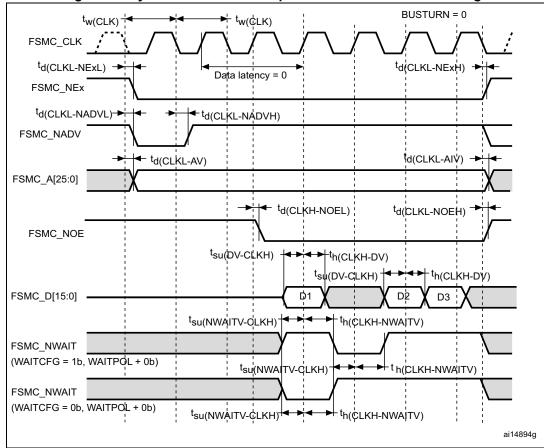


Table 78. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	FSMC_CLK period	2 T _{HCLK}	-	
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x=02)	-	0	
t _{d(CLKL-NExH)}	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	
t _{d(CLKL-NADVL)}	FSMC_CLK low to FSMC_NADV low	-	2.5	ns
t _{d(CLKL-NADVH)}	FSMC_CLK low to FSMC_NADV high	4	-	
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	
t _{d(CLKL-AIV)}	FSMC_CLK low to FSMC_Ax invalid (x=1625)	3	-	

^{2.} Guaranteed by characterization results, not tested in production.

Table 78. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
t _{d(CLKH-NOEL)}	FSMC_CLK high to FSMC_NOE low	-	1	
t _{d(CLKL-NOEH)}	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
t _{su(DV-CLKH)}	FSMC_D[15:0] valid data before FSMC_CLK high	8	-	115
t _{h(CLKH-DV)}	FSMC_D[15:0] valid data after FSMC_CLK high	0	ı	

- 1. $C_L = 30 pF$.
- 2. Guaranteed by characterization results, not tested in production.

Figure 64. Synchronous non-multiplexed PSRAM write timings

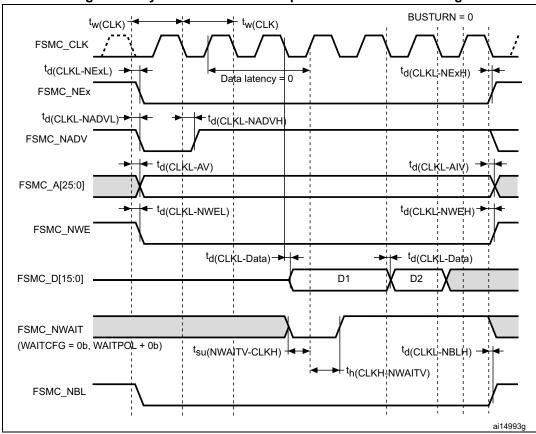


Table 79. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	FSMC_CLK period	2 T _{HCLK} - 1	-	
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x=02)	-	1	
t _{d(CLKL-NExH)}	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	ns
t _{d(CLKL-} NADVL)	FSMC_CLK low to FSMC_NADV low	-	5	

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Table 79. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
t _{d(CLKL-} NADVH)	FSMC_CLK low to FSMC_NADV high	6	-	
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	
t _{d(CLKL-AIV)}	FSMC_CLK low to FSMC_Ax invalid (x=1625)	8	-	
t _{d(CLKL-NWEL)}	FSMC_CLK low to FSMC_NWE low	-	1	ns
t _{d(CLKL-NWEH)}	FSMC_CLK low to FSMC_NWE high	1	-	
t _{d(CLKL-Data)}	FSMC_D[15:0] valid data after FSMC_CLK low	-	2	
t _{d(CLKL-NBLH)}	FSMC_CLK low to FSMC_NBL high	2	-	

^{1.} $C_L = 30 pF$.

PC Card/CompactFlash controller waveforms and timings

Figure 65 through *Figure 70* represent synchronous waveforms, with *Table 80* and *Table 81* providing the corresponding timings. The results shown in these table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x04;
- COM.FSMC WaitSetupTime = 0x07;
- COM.FSMC_HoldSetupTime = 0x04;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x04;
- ATT.FSMC_WaitSetupTime = 0x07;
- ATT.FSMC_HoldSetupTime = 0x04;
- ATT.FSMC_HiZSetupTime = 0x00;
- IO.FSMC_SetupTime = 0x04;
- IO.FSMC WaitSetupTime = 0x07;
- IO.FSMC_HoldSetupTime = 0x04;
- IO.FSMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

In all timing tables, the T_{HCLK} is the HCLK clock period.

^{2.} Guaranteed by characterization results, not tested in production.

STM32F20xxx Electrical characteristics

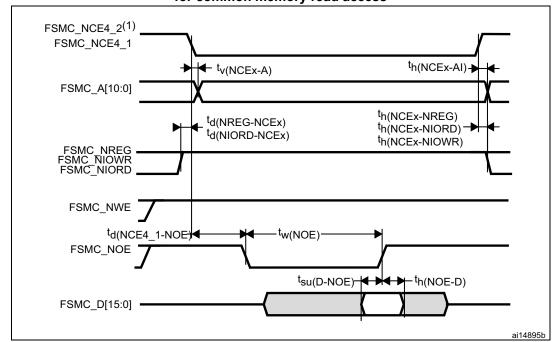
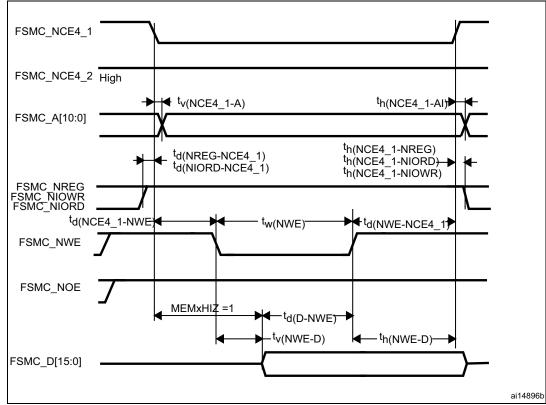


Figure 65. PC Card/CompactFlash controller waveforms for common memory read access

1. FSMC_NCE4_2 remains high (inactive during 8-bit access.





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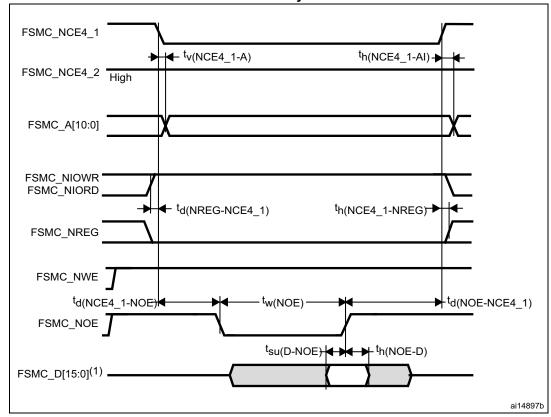


Figure 67. PC Card/CompactFlash controller waveforms for attribute memory read access

1. Only data bits 0...7 are read (bits 8...15 are disregarded).

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FSMC_NCE4_1 FSMC_NCE4_2 High th(NCE4_1-AI)→ FSMC_A[10:0] FSMC_NIOWR FSMC_NIORD th(NCE4_1-NREG) → FSMC_NREG td(NCE4_1-NWE) tw(NWE) FSMC_NWE td(NWE-NCE4_1) FSMC_NOE ^{-t}v(NWE-D) FSMC_D[7:0](1) ai14898b

Figure 68. PC Card/CompactFlash controller waveforms for attribute memory write access

1. Only data bits 0...7 are driven (bits 8...15 remains Hi-Z).

Figure 69. PC Card/CompactFlash controller waveforms for I/O space read access FSMC_NCE4_1 FSMC_NCE4_2 th(NCE4_1-AI) tv(NCEx-A) FSMC_A[10:0] FSMC_NREG. FSMC_NWE FSMC_NOE FSMC_NIOWR td(NIORD-NCE4 1) · ^tw(NIORD) FSMC_NIORD $t_{su(D-NIORD)} + t_{d(NIORD-D)}$ FSMC_D[15:0] ai14899B

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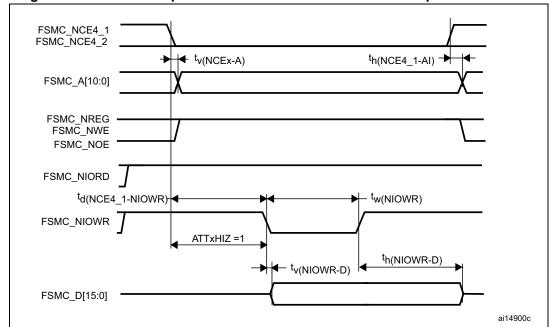


Figure 70. PC Card/CompactFlash controller waveforms for I/O space write access

Table 80. Switching characteristics for PC Card/CF read and write cycles in attribute/common space $^{(1)(2)}$

Symbol	Parameter	Min	Max	Unit
t _{v(NCEx-A)}	FSMC_Ncex low to FSMC_Ay valid	-	0	ns
t _{h(NCEx_AI)}	FSMC_NCEx high to FSMC_Ax invalid	4	-	
t _{d(NREG-NCEx)}	FSMC_NCEx low to FSMC_NREG valid	-	3.5	
t _{h(NCEx-NREG)}	FSMC_NCEx high to FSMC_NREG invalid	T _{HCLK} + 4	-	
t _{d(NCEx-NWE)}	FSMC_NCEx low to FSMC_NWE low	-	5T _{HCLK} + 1	
t _{d(NCEx-NOE)}	FSMC_NCEx low to FSMC_NOE low	-	5T _{HCLK}	
t _{w(NOE)}	FSMC_NOE low width	8T _{HCLK} - 0.5	8T _{HCLK} + 1	
t _{d(NOE_NCEx)}	FSMC_NOE high to FSMC_NCEx high	5T _{HCLK} + 2.5	-	
t _{su (D-NOE)}	FSMC_D[15:0] valid data before FSMC_NOE high	4	-	
t _{h (N0E-D)}	FSMC_N0E high to FSMC_D[15:0] invalid	2	-	
t _{w(NWE)}	FSMC_NWE low width	8T _{HCLK} - 1	8T _{HCLK} + 4	
t _{d(NWE_NCEx})	FSMC_NWE high to FSMC_NCEx high	5T _{HCLK} + 1.5	-	
t _{d(NCEx-NWE)}	FSMC_NCEx low to FSMC_NWE low	-	5T _{HCLK} + 1	
t _{v (NWE-D)}	FSMC_NWE low to FSMC_D[15:0] valid	-	0	
t _{h (NWE-D)}	FSMC_NWE high to FSMC_D[15:0] invalid	8T _{HCLK}	-	
t _{d (D-NWE)}	FSMC_D[15:0] valid before FSMC_NWE high	13T _{HCLK}	-	

^{1.} $C_1 = 30 pF$.

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^{2.} Guaranteed by characterization results, not tested in production.

Symbol Parameter Min Max Unit FSMC NIOWR low width 8T_{HCLK} - 0.5 t_{w(NIOWR)} FSMC NIOWR low to FSMC D[15:0] valid 5T_{HCLK}-1 t_{v(NIOWR-D)} FSMC NIOWR high to FSMC D[15:0] invalid 8T_{HCLK}-3 t_{h(NIOWR-D)} FSMC NCE4 1 low to FSMC NIOWR valid 5T_{HCLK}+ 1.5 t_{d(NCE4_1-NIOWR)} FSMC_NCEx high to FSMC_NIOWR invalid 5T_{HCLK} th(NCEx-NIOWR) ns FSMC NCEx low to FSMC NIORD valid 5T_{HCLK}+ 1 t_{d(NIORD-NCEx)} FSMC NCEx high to FSMC NIORD) valid 5T_{HCLK}- 0.5 t_{h(NCEx-NIORD)} FSMC_NIORD low width 8T_{HCLK}+ 1 _ t_{w(NIORD)} FSMC D[15:0] valid before FSMC NIORD high 9.5 t_{su(D-NIORD)} FSMC_D[15:0] valid after FSMC_NIORD high t_{d(NIORD-D)} 0 -

Table 81. Switching characteristics for PC Card/CF read and write cycles in I/O space⁽¹⁾⁽²⁾

NAND controller waveforms and timings

Figure 71 through *Figure 74* represent synchronous waveforms, together with *Table 82* and *Table 83* provides the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x01;
- COM.FSMC WaitSetupTime = 0x03;
- COM.FSMC_HoldSetupTime = 0x02;
- COM.FSMC_HiZSetupTime = 0x01;
- ATT.FSMC_SetupTime = 0x01;
- ATT.FSMC_WaitSetupTime = 0x03;
- ATT.FSMC_HoldSetupTime = 0x02;
- ATT.FSMC HiZSetupTime = 0x01;
- Bank = FSMC_Bank_NAND;
- MemoryDataWidth = FSMC_MemoryDataWidth_16b;
- ECC = FSMC ECC Enable;
- ECCPageSize = FSMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

In all timing tables, the T_{HCLK} is the HCLK clock period.

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^{1.} $C_1 = 30 \text{ pF}.$

^{2.} Guaranteed by characterization results, not tested in production.

FSMC_NCEX

ALE (FSMC_A17)
CLE (FSMC_A16)

FSMC_NWE

FSMC_NOE (NRE)

Tsmc_NOE (NRE)

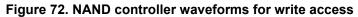
tsu(D-NOE)

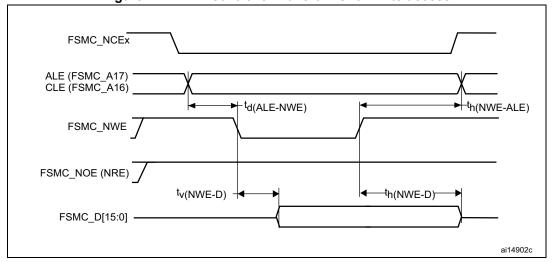
th(NOE-ALE)

th(NOE-D)

ai14901c

Figure 71. NAND controller waveforms for read access





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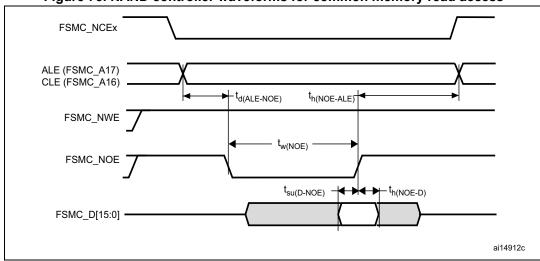


Figure 73. NAND controller waveforms for common memory read access

Figure 74. NAND controller waveforms for common memory write access

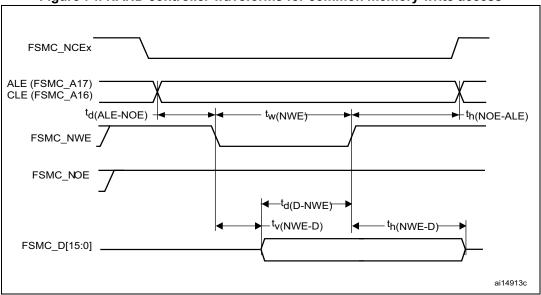


Table 82. Switching characteristics for NAND Flash read cycles⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(N0E)}	FSMC_NOE low width	4T _{HCLK} - 1	4T _{HCLK} + 2	
t _{su(D-NOE)}	FSMC_D[15-0] valid data before FSMC_NOE high	9	-	
t _{h(NOE-D})	FSMC_D[15-0] valid data after FSMC_NOE high	3	-	ns
t _{d(ALE-NOE)}	FSMC_ALE valid before FSMC_NOE low	-	3T _{HCLK}	
t _{h(NOE-ALE)}	FSMC_NWE high to FSMC_ALE invalid	3T _{HCLK} + 2	-	

^{1.} $C_L = 30 pF$.

2. Guaranteed by characterization results, not tested in production.

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Symbol	Parameter	Min	Max	Unit			
t _{w(NWE)}	FSMC_NWE low width	4T _{HCLK} - 1	4T _{HCLK} + 3				
t _{v(NWE-D)}	FSMC_NWE low to FSMC_D[15-0] valid	-	0				
t _{h(NWE-D)}	FSMC_NWE high to FSMC_D[15-0] invalid	3T _{HCLK}	-	ne			
t _{d(D-NWE)}	FSMC_D[15-0] valid before FSMC_NWE high	5T _{HCLK}	-	ns			
t _{d(ALE-NWE)}	FSMC_ALE valid before FSMC_NWE low	-	3T _{HCLK} + 2				
t _{h(NWE-ALE)}	FSMC_NWE high to FSMC_ALE invalid	3T _{HCLK} - 2	-				

Table 83. Switching characteristics for NAND Flash write cycles⁽¹⁾⁽²⁾

6.3.26 Camera interface (DCMI) timing specifications

Table 84. DCMI characteristics

Symbol	Parameter	Conditions	Min	Max
-	Frequency ratio DCMI_PIXCLK/f _{HCLK}	DCMI_PIXCLK= 48 MHz	-	0.4

6.3.27 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 85* are derived from tests performed under ambient temperature, f_{PCLKX} frequency and V_{DD} supply voltage conditions summarized in *Table 14*.

Refer to Section 6.3.16: I/O port characteristics for more details on the input/output alternate function characteristics (D[7:0], CMD, CK).

CK

D, CMD
(output)

D, CMD
(input)

ai14887

Figure 75. SDIO high-speed mode

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^{1.} $C_L = 30 pF$.

^{2.} Guaranteed by characterization results, not tested in production.

Figure 76. SD default mode

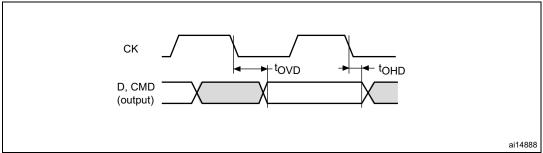


Table 85. SD/MMC characteristics

Symbol	Parameter	Conditions	Min	Max	Unit		
f _{PP}	Clock frequency in data transfer mode	$C_L \leq 30 \text{ pF}$	0	48	MHz		
-	SDIO_CK/f _{PCLK2} frequency ratio	-	-	8/3	-		
t _{W(CKL)}	Clock low time, f _{PP} = 16 MHz	$C_L \leq 30 \text{ pF}$	32	-			
t _{W(CKH)}	Clock high time, f _{PP} = 16 MHz	$C_L \leq 30 \text{ pF}$	31	-			
t _r	Clock rise time	$C_L \leq 30 \text{ pF}$	-	3.5	ns		
t _f	Clock fall time	$C_L \leq 30 \text{ pF}$	-	5			
CMD, D inp	outs (referenced to CK)				•		
t _{ISU}	Input setup time	$C_L \leq 30 \text{ pF}$	2	-	no		
t _{IH}	Input hold time	$C_L \leq 30 \text{ pF}$	0	-	ns		
CMD, D ou	tputs (referenced to CK) in MMC and	SD HS mode			•		
t _{OV}	Output valid time	$C_L \leq 30 \text{ pF}$	-	6	no		
t _{OH}	Output hold time	$C_L \leq 30 \text{ pF}$	0.3	-	ns		
CMD, D outputs (referenced to CK) in SD default mode ⁽¹⁾							
t _{OVD}	Output valid default time	$C_L \leq 30 \text{ pF}$	-	7	200		
t _{OHD}	Output hold default time	$C_L \leq 30 \text{ pF}$	0.5	-	ns		

^{1.} Refer to SDIO_CLKCR, the SDI clock control register to control the CK output.

6.3.28 RTC characteristics

Table 86. RTC characteristics

Symbo	Parameter	Parameter Conditions		Max
-	f _{PCLK1} /RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

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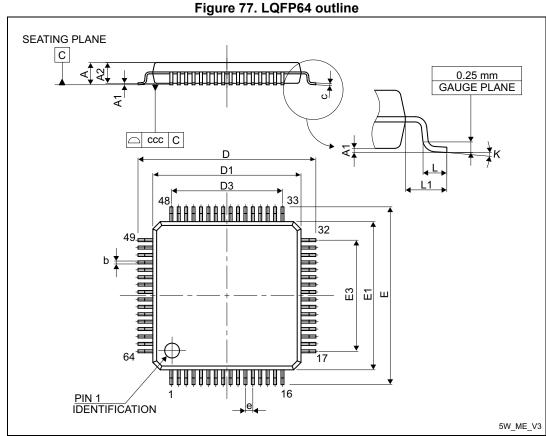
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Package information 7

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

LQFP64 package information 7.1

LQFP64 is a 64-pin, 10 x 10 mm low-profile quad flat package.



1. Drawing is not to scale.

Table 87. LQFP64 mechanical data

Symbol	millimeters				inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571

Table 87. LQFP64 mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
Е	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-
е	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

0.3 12.7 10.3 -10.3 12.7 ai14909c

Figure 78. LQFP64 recommended footprint

1. Dimensions are expressed in millimeters.

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Device marking

Figure 79 gives an example of topside marking orientation versus pin 1 identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Product identification (1)

RETL

Pin 1 identification

Revision code

Figure 79. Device marking (package top view)

STM32F20xxx Package information

7.2 WLCSP64+2 package information

WLCSP64+2 is a 66-ball, 3.639 x 3.971 mm, 0.4 mm pitch wafer level chip scale package.

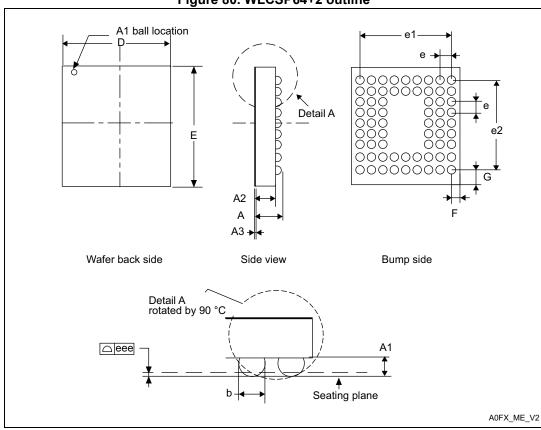


Figure 80. WLCSP64+2 outline

1. Drawing is not to scale.

Table 88. WLCSP64+2 mechanical data

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
А	0.540	0.570	0.600	0.0213	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	-	0.380	-	-	0.0150	-
A3	-	0.025	-	-	0.0100	-
b ⁽²⁾	0.240	0.270	0.300	0.0094	0.0106	0.0118
D	3.604	3.639	3.674	0.1419	0.1433	0.1446
Е	3.936	3.971	4.006	0.1550	0.1563	0.1577
е	-	0.400	-	-	0.0157	-
e1	-	3.200	-	-	0.1260	-
e2	-	3.200	-	-	0.1260	-

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Symbol		millimeters		inches ⁽¹⁾			
Symbol	Min	Тур	Max	Min	Тур	Max	
F	-	0.220	-	-	0.0087	-	
G	-	0.386	-	-	0.0152	-	
aaa	-	-	0.100	-	-	0.0039	
bbb	-	-	0.100	-	-	0.0039	
ccc	-	-	0.100	-	-	0.0039	
ddd	-	-	0.050	-	-	0.0020	
eee	-	-	0.050	-	-	0.0020	

- 1. Values in inches are converted from mm and rounded to four decimal digits.
- 2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 81. WLCSP64+2 recommended footprint

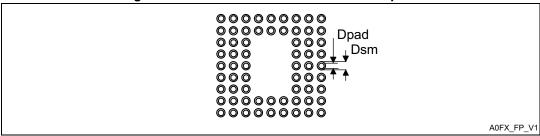


Table 89. WLCSP64+2 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values
Pitch	0.4
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm

STM32F20xxx Package information

7.3 LQFP100 package information

LQFP100 is a 100-pin, 14 x 14 mm low-profile quad flat package.

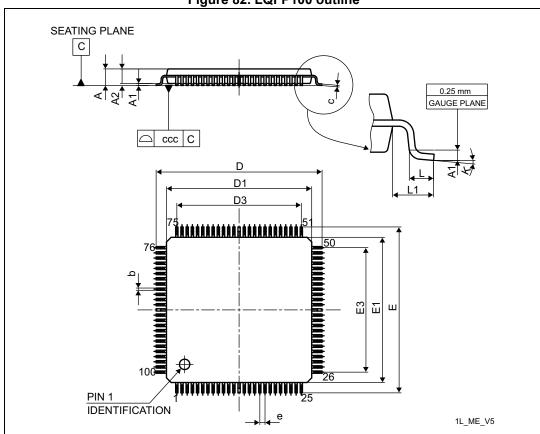


Figure 82. LQFP100 outline

1. Drawing is not to scale.

Table 90. LQPF100 mechanical data

Comple at	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591



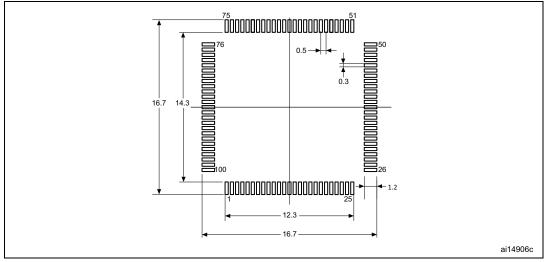
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Table 90. LQPF100 mechanical data (continued)

Comple ed	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
E3	-	12.000	-	-	0.4724	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

Figure 83. LQFP100 recommended footprint



1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking and pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

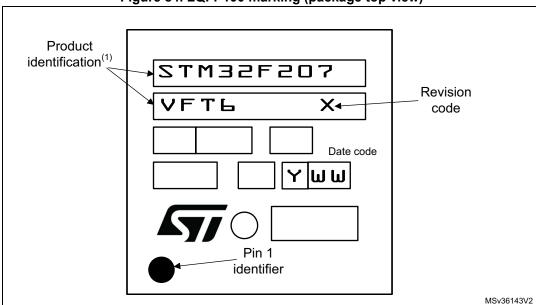


Figure 84. LQFP100 marking (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

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7.4 LQFP144 package information

LQFP144 is a 144-pin, 20 x 20 mm low-profile quad flat package.

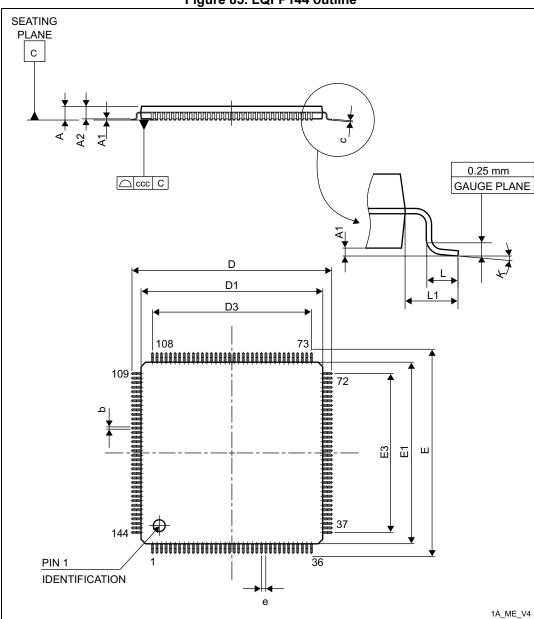


Figure 85. LQFP144 outline

1. Drawing is not to scale.



Table 91. LQFP144 mechanical data

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-		0.0031

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

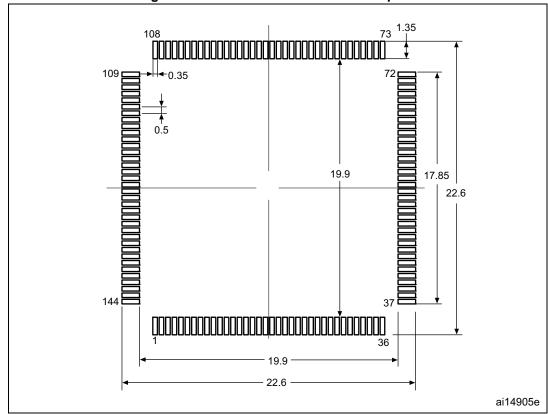


Figure 86. LQFP144 recommended footprint

1. Dimensions are expressed in millimeters.

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Device marking

The following figure gives an example of topside marking and pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Product identification⁽¹⁾

STM32F207ZGTL

Date code

YWW

Pin 1 identifier

Figure 87. LQFP144 marking (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

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7.5 LQFP176 package information

LQFP176 is a 176-pin, 24 x 24 mm low profile quad flat package.

C Seating plane

O.25 mm
gauge plane

PIN 1
IDENTIFICATION

ZE

TI_ME_V2

Figure 88. LQFP176 outline

1. Drawing is not to scale.

Table 92. LQFP176 mechanical data

		Dimensions				
Symbol		millimeters			inches ⁽¹⁾	
	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
С	0.090	-	0.200	0.0035	-	0.0079

STM32F20xxx Package information

Table 92. LQFP176 mechanical data (continued)

	Dimensions					
Symbol		millimeters			inches ⁽¹⁾	
	Min	Тур	Max	Min	Тур	Max
D	23.900	-	24.100	0.9409	-	0.9488
HD	25.900	-	26.100	1.0197	-	1.0276
ZD	-	1.250	-	-	0.0492	-
E	23.900	-	24.100	0.9409	-	0.9488
HE	25.900	-	26.100	1.0197	-	1.0276
ZE	=	1.250	-	-	0.0492	-
е	=	0.500	-	-	0.0197	-
L ⁽²⁾	0.450	-	0.750	0.0177	-	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	-	7°	0°	-	7°
ccc	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

^{2.} $\,$ L dimension is measured at gauge plane at 0.25 mm above the seating plane.

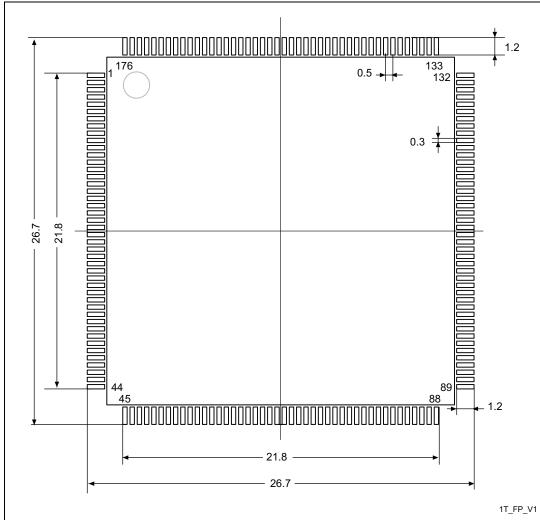


Figure 89. LQFP176 recommended footprint

1. Dimensions are expressed in millimeters.

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STM32F20xxx Package information

7.6 UFBGA176+25 package information

UFBGA176+25 is a 201-ball, 10 x 10 mm, 0.65 mm pitch ultra fine pitch ball grid array package.

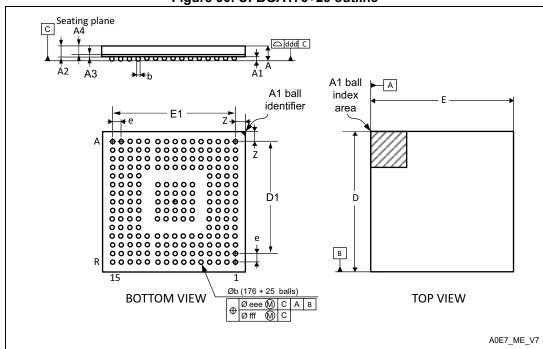


Figure 90. UFBGA176+25 outline

1. Drawing is not to scale.

Table 93. UFBGA176+25 mechanical data

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	9.100	-	-	0.3583	-
Е	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	9.100	-	-	0.3583	-
е	-	0.650	-	-	0.0256	-
Z	-	0.450	-	-	0.0177	-
ddd	-	-	0.080	-	-	0.0031

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Table 93. UFBGA176+25 mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

Figure 91. UFBGA176+25 recommended footprint

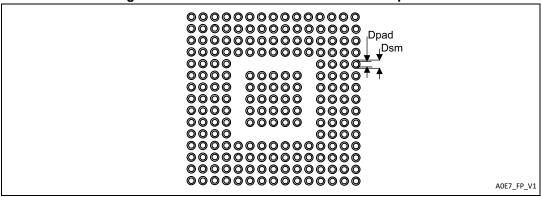


Table 94. UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65 mm
Dpad	0.300 mm
Dsm	0.400 mm typ (depends on the soldermask registration tolerance)
Stencil opening	0.300 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Device marking

The following figure gives an example of topside marking and ball A1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

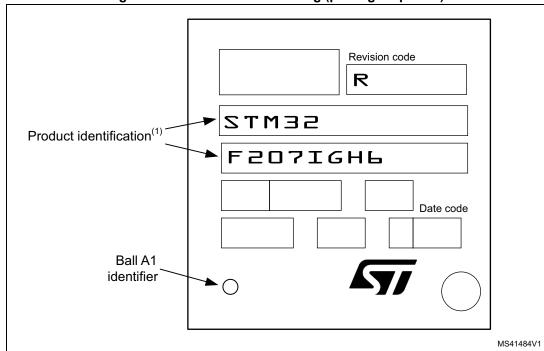


Figure 92. UFBGA176+25 marking (package top view)

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^{1.} Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.7 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \max = T_A \max + (P_D \max x \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$ max),
- P_{INT} max is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins where:

$$P_{I/O}$$
 max = $\Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DD} - V_{OH}) \times I_{OH})$,

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol Parameter Value Unit Thermal resistance junction-ambient 45 LQFP 64 - 10 × 10 mm / 0.5 mm pitch Thermal resistance junction-ambient 51 WLCSP64+2 - 0.400 mm pitch Thermal resistance junction-ambient 46 LQFP100 - 14 × 14 mm / 0.5 mm pitch Θ_{JA} °C/W Thermal resistance junction-ambient 40 LQFP144 - 20 × 20 mm / 0.5 mm pitch Thermal resistance junction-ambient 38 LQFP176 - 24 × 24 mm / 0.5 mm pitch Thermal resistance junction-ambient 39 UFBGA176 - 10× 10 mm / 0.5 mm pitch

Table 95. Package thermal characteristics

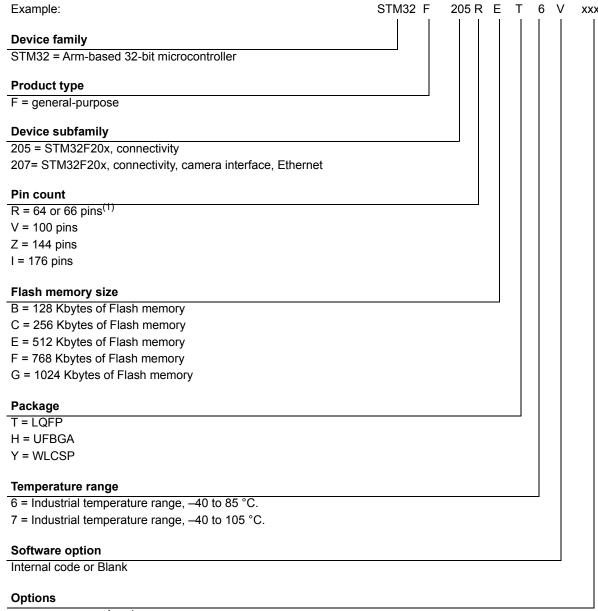
Reference document

Downloaded from Arrow.com.

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.



8 Ordering information



xxx = programmed parts

TR = tape and reel

1. The 66 pins is available on WLCSP package only.

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, contact your nearest ST sales office.

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9 Revision history

Table 96. Document revision history

Date	Revision	Changes
05-Jun-2009	1	Initial release.
09-Oct-2009	2	Document status promoted from Target specification to Preliminary data. In Table 8: STM32F20x pin and ball definitions: - Note 4 updated - V _{DD_SA} and V _{DD_3} pins inverted (Figure 12: STM32F20x LQFP100 pinout, Figure 13: STM32F20x LQFP144 pinout and Figure 14: STM32F20x LQFP176 pinout corrected accordingly). Section: In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark. changed to LQFP with no exposed pad.
01-Feb-2010	3	LFBGA144 package removed. STM32F203xx part numbers removed. Part numbers with 128 and 256 Kbyte Flash densities added. Encryption features removed. PC13-TAMPER-RTC renamed to PC13-RTC_AF1 and PI8-TAMPER-RTC renamed to PI8-RTC_AF2.
13-Jul-2010	4	Renamed high-speed SRAM, system SRAM. Removed combination: 128 KBytes Flash memory in LQFP144. Added UFBGA176 package. Added note 1 related to LQFP176 package in Table 2, Figure 14, and Table . Added information on ART accelerator and audio PLL (PLLI2S). Added Table 6: USART feature comparison. Several updates on Table 8: STM32F20x pin and ball definitions and Table 10: Alternate function mapping. ADC, DAC, oscillator, RTC_AF, WKUP and VBUS signals removed from alternate functions and moved to the "other functions" column in Table 8: STM32F20x pin and ball definitions. TRACESWO added in Figure 4: STM32F20x block diagram, Table 8: STM32F20x pin and ball definitions, and Table 10: Alternate function mapping. XTAL oscillator frequency updated on cover page, in Figure 4: STM32F20x block diagram and in Section 3.11: External interrupt/event controller (EXTI). Updated list of peripherals used for boot mode in Section 3.13: Boot modes. Added Regulator bypass mode in Section 3.16: Voltage regulator, and Section 6.3.4: Operating conditions at power-up / power-down (regulator OFF). Updated Section 3.17: Real-time clock (RTC), backup SRAM and backup registers. Added Note Note: in Section 3.18: Low-power modes. Added SPI TI protocol in Section 3.23: Serial peripheral interface (SPI).



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Table 96. Document revision history (continued)

Date	Revision	Changes
Date		Changes Added USB OTG_FS features in Section 3.28: Universal serial bus onthe-go full-speed (OTG_FS). Updated V _{CAP_1} and V _{CAP_2} capacitor value to 2.2 µF in Figure 19: Power supply scheme. Removed DAC, modified ADC limitations, and updated I/O compensation for 1.8 to 2.1 V range in Table 15: Limitations depending on the operating power supply range. Added V _{BORL} , V _{BORM} , V _{BORH} and I _{RUSH} in Table 19: Embedded reset and power control block characteristics. Removed table Typical current consumption in Sleep mode with Flash memory in Deep power down mode. Merged typical and maximum current consumption sections and added Table 21: Typical and maximum
13-Jul-2010	4 (cont'd)	current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled), Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM, Table 22: Typical and maximum current consumption in Sleep mode, Table 23: Typical and maximum current consumptions in Stop mode, Table 24: Typical and maximum current consumptions in Standby mode, and Table 25: Typical and maximum current consumptions in V _{BAT} mode. Update Table 34: Main PLL characteristics and added Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics. Added Note 8 for CIO in Table 48: I/O AC characteristics. Updated Section 6.3.18: TIM timer characteristics. Added T _{NRST_OUT} in Table 49: NRST pin characteristics. Updated Table 52: I ² C characteristics.
		timing diagram. Removed note related to ADC calibration in Table 67. Section 6.3.20: 12-bit ADC characteristics: ADC characteristics tables merged into one single table; tables ADC conversion time and ADC accuracy removed. Updated Table 68: DAC characteristics. Updated Section 6.3.22: Temperature sensor characteristics and Section 6.3.23: V _{BAT} monitoring characteristics. Update Section 6.3.26: Camera interface (DCMI) timing specifications. Added Section 6.3.27: SD/SDIO MMC card host interface (SDIO) characteristics, and Section 6.3.28: RTC characteristics. Added Section 7.7: Thermal characteristics. Updated Table 91: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm package mechanical data and Figure 86: LQFP176 - Low profile quad flat package outline. Changed tape and reel code to TX in Table : Added Table 101: Main applications versus package for STM32F2xxx microcontrollers. Updated figures in Appendix A.2: USB OTG full speed (FS) interface solutions and A.3: USB OTG high speed (HS) interface solutions. Updated Figure 94: Audio player solution using PLL, PLLI2S, USB and 1 crystal and Figure 95: Audio PLL (PLLI2S) providing accurate I2S clock.



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Table 96. Document revision history (continued)

Date	Revision	Changes	
	. 10 1 101011		
		Update I/Os in Section: Features. Added WLCSP64+2 package. Added note 1 related to LQFP176 on cover page.	
		Added trademark for ART accelerator. Updated Section 3.2: Adaptive real-time memory accelerator (ART Accelerator™).	
		Updated Figure 5: Multi-AHB matrix.	
		Added case of BOR inactivation using IRROFF on WLCSP devices in Section 3.15: Power supply supervisor.	
		Reworked Section 3.16: Voltage regulator to clarify regulator off modes. Renamed PDROFF, IRROFF in the whole document.	
		Added Section 3.19: V _{BAT} operation.	
		Updated LIN and IrDA features for UART4/5 in <i>Table 6: USART feature comparison</i> .	
		Table 8: STM32F20x pin and ball definitions: Modified V _{DD_3} pin, and added note related to the FSMC_NL pin; renamed BYPASS-REG REGOFF, and add IRROFF pin; renamed USART4/5 UART4/5. USART4 pins renamed UART4.	
		Changed V_{SS_SA} to V_{SS} , and V_{DD_SA} pin reserved for future use.	
		Updated maximum HSE crystal frequency to 26 MHz.	
05.110040		_	Section 6.2: Absolute maximum ratings: Updated V _{IN} minimum and maximum values and note related to five-volt tolerant inputs in <i>Table 11:</i> Voltage characteristics. Updated I _{INJ(PIN)} maximum values and related notes in <i>Table 12: Current characteristics</i> .
25-Nov-2010	5	Updated V _{DDA} minimum value in <i>Table 14: General operating conditions</i> .	
		Added Note 2 and updated Maximum CPU frequency in <i>Table 15:</i> Limitations depending on the operating power supply range, and added Figure 21: Number of wait states versus f_{CPU} and V_{DD} range.	
		Added brownout level 1, 2, and 3 thresholds in <i>Table 19: Embedded reset</i> and power control block characteristics.	
		Changed f _{OSC_IN} maximum value in <i>Table 30: HSE 4-26 MHz oscillator</i> characteristics.	
		Changed f _{PLL_IN} maximum value in <i>Table 34: Main PLL characteristics</i> , and updated jitter parameters in <i>Table 35: PLLI2S (audio PLL)</i> characteristics.	
		Section 6.3.16: I/O port characteristics: updated V_{IH} and V_{IL} in Table 48: I/O AC characteristics.	
		Added Note 1 below Table 47: Output voltage characteristics.	
		Updated R _{PD} and R _{PU} parameter description in <i>Table 57: USB OTG FS DC electrical characteristics</i> .	
		Updated V _{REF+} minimum value in <i>Table 66: ADC characteristics</i> .	
		Updated Table 71: Embedded internal reference voltage.	
		Removed Ethernet and USB2 for 64-pin devices in <i>Table 101: Main applications versus package for STM32F2xxx microcontrollers</i> .	
		Added A.2: USB OTG full speed (FS) interface solutions, removed "OTG FS connection with external PHY" figure, updated Figure 87, Figure 88, and Figure 90 to add STULPI01B.	



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Table 96. Document revision history (continued)

Date	Revision	le 96. Document revision history (continued) Changes
Date	Kevision	Changes
		Changed datasheet status to "Full Datasheet". Introduced concept of SRAM1 and SRAM2. LQFP176 package now in production and offered only for 256 Kbyte and
		1 Mbyte devices. Availability of WLCSP64+2 package limited to 512 Kbyte and 1 Mbyte devices.
		Updated Figure 3: Compatible board design between STM32F10x and STM32F2xx for LQFP144 package and Figure 2: Compatible board design between STM32F10x and STM32F2xx for LQFP100 package.
		Added camera interface for STM32F207Vx devices in <i>Table 2:</i> STM32F205xx features and peripheral counts.
		Removed 16 MHz internal RC oscillator accuracy in Section 3.12: Clocks and startup.
		Updated Section 3.16: Voltage regulator. Modified I ² S sampling frequency range in Section 3.12: Clocks and
		startup, Section 3.24: Inter-integrated sound (I ² S), and Section 3.30: Audio PLL (PLLI2S).
		Updated Section 3.17: Real-time clock (RTC), backup SRAM and backup registers and description of TIM2 and TIM5 in Section 3.20.2: General-purpose timers (TIMx).
		Modified maximum baud rate (oversampling by 16) for USART1 in Table 6: USART feature comparison.
22-Apr-2011	6	Updated note related to RFU pin below Figure 12: STM32F20x LQFP100 pinout, Figure 13: STM32F20x LQFP144 pinout, Figure 14: STM32F20x LQFP176 pinout, Figure 15: STM32F20x UFBGA176 ballout, and Table 8: STM32F20x pin and ball definitions.
		In <i>Table 8: STM32F20x pin and ball definitions</i> ,:changed I2S2_CK and I2S3_CK to I2S2_SCK and I2S3_SCK, respectively; added PA15 and TT (3.6 V tolerant I/O).
		Added RTC_50Hz as PB15 alternate function in <i>Table 8: STM32F20x pin and ball definitions</i> and <i>Table 10: Alternate function mapping</i> .
		Removed ETH _RMII_TX_CLK for PC3/AF11 in <i>Table 10: Alternate function mapping</i> .
		Updated Table 11: Voltage characteristics and Table 12: Current characteristics.
		T _{STG} updated to –65 to +150 in <i>Table 13: Thermal characteristics</i> . Added CEXT, ESL, and ESR in <i>Table 14: General operating conditions</i> as well as Section 6.3.2: VCAP1/VCAP2 external capacitor.
		Modified Note 4 in Table 15: Limitations depending on the operating power supply range.
		Updated Table 17: Operating conditions at power-up / power-down (regulator ON), and Table 18: Operating conditions at power-up / power-down (regulator OFF).
		Added OSC_OUT pin in Figure 17: Pin loading conditions. and Figure 18: Pin input voltage.
		Updated <i>Figure 19: Power supply scheme</i> to add IRROFF and REGOFF pins and modified notes.
		Updated V _{PVD} , V _{BOR1} , V _{BOR2} , V _{BOR3} , T _{RSTTEMPO} typical value, and I _{RUSH} , added E _{RUSH} and <i>Note 2</i> in <i>Table 19: Embedded reset and power control block characteristics</i> .



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Table 96. Document revision history (continued)

Date	Revision	le 96. Document revision history (continued) Changes
	7.04131011	
		Updated Typical and maximum current consumption conditions, as well as Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled) and Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM. Added Figure 23, Figure 24, Figure 25, and Figure 26.
		Updated <i>Table 22: Typical and maximum current consumption in Sleep mode</i> , and added <i>Figure 27</i> and <i>Figure 28</i> .
		Updated Table 23: Typical and maximum current consumptions in Stop mode. Added Figure 29: Typical current consumption vs. temperature in Stop mode.
		Updated Table 24: Typical and maximum current consumptions in Standby mode and Table 25: Typical and maximum current consumptions in V _{BAT} mode.
		Updated On-chip peripheral current consumption conditions and Table 26: Peripheral current consumption.
		Updated t _{WUSTDBY} and t _{WUSTOP} , and added <i>Note 3</i> in <i>Table 27: Low-power mode wakeup timings</i> .
		Maximum f _{HSE_ext} and minimum t _{w(HSE)} values updated in <i>Table 28: High-speed external user clock characteristics</i> .
		Updated C and g_m in <i>Table 30: HSE 4-26 MHz oscillator characteristics</i> . Updated R_F , I_2 , g_m , and $t_{su(LSE)}$ in <i>Table 31: LSE oscillator characteristics</i> (f_{LSE} = 32.768 kHz).
22-Apr-2011	6 (cont'd)	Added <i>Note 1</i> and updated ACC _{HSI} , IDD _{(HSI} , and t _{su(HSI)} in <i>Table 32: HSI oscillator characteristics</i> . Added <i>Figure 34: ACC_{HSI} versus temperature</i> .
		Updated f _{LSI} , t _{su(LSI)} and IDD _(LSI) in <i>Table 33: LSI oscillator</i> characteristics. Added Figure 35: ACC _{LSI} versus temperature
		Table 34: Main PLL characteristics: removed note 1, updated t _{LOCK} , jitter, IDD _(PLL) and IDD _{A(PLL)} , added <i>Note 2</i> for f _{PLL_IN} minimum and maximum values.
		Table 35: PLLI2S (audio PLL) characteristics: removed note 1, updated t_{LOCK} , jitter, $IDD_{(PLLI2S)}$ and $IDD_{A(PLLI2S)}$, added Note 2 for f_{PLLI2S_IN} minimum and maximum values.
		Added Note 1 in Table 36: SSCG parameters constraint.
		Updated <i>Table 37: Flash memory characteristics</i> . Modified <i>Table 38: Flash memory programming</i> and added <i>Note 2</i> for t _{prog} . Updated t _{prog} and added <i>Note 1</i> in <i>Table 39: Flash memory programming with V_{PP}</i> .
		Modified Figure 40: Recommended NRST pin protection.
		Updated <i>Table 42: EMI characteristics</i> and EMI monitoring conditions in <i>Section : Electromagnetic Interference (EMI)</i> . Added <i>Note 2</i> related to V _{ESD(HBM)} in <i>Table 43: ESD absolute maximum ratings</i> .
		Updated Table 48: I/O AC characteristics.
		Added Section 6.3.15: I/O current injection characteristics.
		Modified maximum frequency values and conditions in <i>Table 48: I/O AC characteristics</i> .
		Updated t _{res(TIM)} in <i>Table 50: Characteristics of TIMx connected to the APB1 domain.</i> Modified t _{res(TIM)} and f _{EXT} <i>Table 51: Characteristics of TIMx connected to the APB2 domain.</i>



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Table 96. Document revision history (continued)

Date	Revision	Changes
22-Apr-2011	Revision 6 (cont'd)	Changed t _{w(SCKH)} to t _{w(SCLH)} , t _{w(SCKL)} to t _{w(SCLL)} , t _{r(SCK)} to t _{r(SCL)} , and t _{r(SCK)} to t _{r(SCL)} in Table 52: I ² C characteristics and in Figure 41: I ² C bus AC waveforms and measurement circuit. Added Table 57: USB OTG FS DC electrical characteristics and updated Table 58: USB OTG FS electrical characteristics. Updated V _{DD} minimum value in Table 62: Ethernet DC electrical characteristics. Updated Table 66: ADC characteristics and R _{AIN} equation. Updated R _{AIN} equation. Updated Table 68: DAC characteristics. Updated t _{START} in Table 69: Temperature sensor characteristics. Updated R typical value in Table 70: V _{BAT} monitoring characteristics. Updated Table 71: Embedded internal reference voltage. Modified FSMC_NOE waveform in Figure 57: Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms. Shifted end of FSMC_NEx/NADV/addresses/NWE/NOE/NWAIT of a half FSMC_CLK period, changed t _{d(CLKH-NExH)} to t _{d(CLKL-NEXH)} , t _{d(CLKH-AIV)} to t _{d(CLKL-NIV)} , t _{d(CLKH-NOEH)} to t _{d(CLKL-NIV)} , and updated data latency from 1 to 0 in Figure 61: Synchronous multiplexed
		NOR/PSRAM read timings, Figure 62: Synchronous multiplexed PSRAM write timings, Figure 63: Synchronous non-multiplexed NOR/PSRAM read timings, and Figure 64: Synchronous non-multiplexed PSRAM write timings, Changed t _{d(CLKH-NExH)} to t _{d(CLKL-NExH)} , t _{d(CLKH-AIV)} to t _{d(CLKL-AIV)} , t _{d(CLKH-NOEH)} , to t _{d(CLKL-NWEH)} , and
		modified t _{w(CLK)} minimum value in <i>Table 76</i> , <i>Table 77</i> , <i>Table 78</i> , and <i>Table 79</i> . Updated note 2 in <i>Table 72</i> , <i>Table 73</i> , <i>Table 74</i> , <i>Table 75</i> , <i>Table 76</i> , <i>Table 77</i> , <i>Table 78</i> , and <i>Table 79</i> .
		Modified t _{h(NIOWR-D)} in <i>Figure 70: PC Card/CompactFlash controller</i> waveforms for I/O space write access.
		Modified FSMC_NCEx signal in Figure 71: NAND controller waveforms for read access, Figure 72: NAND controller waveforms for write access, Figure 73: NAND controller waveforms for common memory read access, and Figure 74: NAND controller waveforms for common memory write access
		Specified Full speed (FS) mode for Figure 89: USB OTG HS peripheral- only connection in FS mode and Figure 90: USB OTG HS host-only connection in FS mode.



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Table 96. Document revision history (continued)

		le 96. Document revision history (continued)
Date	Revision	Changes
		Added SDIO in <i>Table 2: STM32F205xx features and peripheral counts</i> . Updated V _{IN} for 5V tolerant pins in <i>Table 11: Voltage characteristics</i> . Updated jitter parameters description in <i>Table 34: Main PLL characteristics</i> .
14-Jun-2011	7	Remove jitter values for system clock in <i>Table 35: PLLI2S (audio PLL)</i> characteristics. Updated <i>Table 42: EMI characteristics</i> . Updated Note 2 in <i>Table 52: I²C characteristics</i> . Updated Avg_Slope typical value and T _{S_temp} minimum value in <i>Table 69: Temperature sensor characteristics</i> . Updated T _{S_vbat} minimum value in <i>Table 70: V_{BAT} monitoring characteristics</i> . Updated T _{S_vrefint} minimum value in <i>Table 71: Embedded internal reference voltage</i> . Added Software option in <i>Section 8: Ordering information</i> . In <i>Table 101: Main applications versus package for STM32F2xxx microcontrollers</i> , renamed USB1 and USB2, USB OTG FS and USB OTG HS, respectively; and removed USB OTG FS and camera interface
20-Dec-2011	8	Updated SDIO register addresses in Figure 16: Memory map. Updated Figure 3: Compatible board design between STM32F10x and STM32F2xx for LQFP144 package, Figure 2: Compatible board design between STM32F10x and STM32F2xx for LQFP144 package, Figure 2: Compatible board design between STM32F10x and STM32F2xx for LQFP100 package, Figure 1: Compatible board design between STM32F10x and STM32F2xx for LQFP100 package, Figure 1: Compatible board design between STM32F10x and STM32F2xx for LQFP164 package, and added Figure 4: Compatible board design between STM32F10xx and STM32F2xx for LQFP176 package. Updated Section 3.3: Memory protection unit. Updated Section 3.6: Embedded SRAM. Updated Section 3.6: Embedded SRAM. Updated Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS) to remove external FS OTG PHY support. In Table 8: STM32F20x pin and ball definitions: changed SPI2_MCK and SPI3_MCK to I2S2_MCK and I2S3_MCK, respectively. Added ETH _RMII_TX_EN alternate function to PG11. Added EVENTOUT in the list of alternate functions for I/O pin/balls. Removed OTG_FS_SDA, OTG_FS_SCL and OTG_FS_INTN alternate functions. In Table 10: Alternate function mapping: changed I2S3_SCK to I2S3_MCK for PC7/AF6, added FSMC_NCE3 for PG9, FSMC_NE3 for PG10, and FSMC_NCE2 for PD7. Removed OTG_FS_SDA, OTG_FS_SCL and OTG_FS_INTN alternate functions. Changed I2S3_SCK into I2S3_MCK for PC7/AF6. Updated peripherals corresponding to AF12. Removed CEXT and ESR from Table 14: General operating conditions. Added maximum power consumption at TA=25 °C in Table 23: Typical and maximum current consumptions in Stop mode. Updated md minimum value in Table 36: SSCG parameters constraint. Added examples in Section 6.3.11: PLL spread spectrum clock



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Table 96. Document revision history (continued)

B-4:		Changes
Date	Revision	Changes
20-Dec-2011	8 (cont'd)	Updated Table 54: SPI characteristics and Table 55: I ² S characteristics. Updated Figure 48: ULPI timing diagram and Table 61: ULPI timing. Updated Table 63: Dynamics characteristics: Ethernet MAC signals for SMI, Table 64: Dynamics characteristics: Ethernet MAC signals for RMII, and Table 65: Dynamics characteristics: Ethernet MAC signals for RMII. Section 6.3.25: FSMC characteristics: updated Table 72 to Table 83, changed C _L value to 30 pF, and modified FSMC configuration for asynchronous timings and waveforms. Updated Figure 62: Synchronous multiplexed PSRAM write timings. Updated Table 84: DCMI characteristics. Updated Table 92: UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm mechanical data. Appendix A.2: USB OTG full speed (FS) interface solutions: updated Figure 87: USB OTG FS (full speed) host-only connection and added Note 2, updated Figure 88: OTG FS (full speed) connection dual-role with internal PHY and added Note 3 and Note 4, modified Figure 89: OTG HS (high speed) device connection, host and dual-role in high-speed mode with external PHY and added Note 2. Appendix A.3: USB OTG high speed (HS) interface solutions: removed figures USB OTG HS device-only connection in FS mode and USB OTG HS host-only connection in FS mode, updated Figure 89: OTG HS (high speed) device connection, host and dual-role in high-speed mode with external PHY.
		Added Appendix A.4: Ethernet interface solutions.
		Updated disclaimer on last page.
24-Apr-2012	9	Updated V _{DD} minimum value in <i>Section 2: Description</i> . Updated number of USB OTG HS and FS, modified packages for STM32F207lx part numbers, added <i>Note 1</i> related to FSMC and <i>Note 2</i> related to SPI/I2S, and updated <i>Note 3</i> in <i>Table 2: STM32F205xx</i> features and peripheral counts and <i>Table 3: STM32F207xx</i> features and peripheral counts. Added <i>Note 2</i> and update TIM5 in <i>Figure 4: STM32F20x block diagram</i> . Updated maximum number of maskable interrupts in <i>Section 3.10: Nested vectored interrupt controller (NVIC)</i> . Updated V _{DD} minimum value in <i>Section 3.14: Power supply schemes</i> . Updated <i>Note a</i> in <i>Section 3.16.1: Regulator ON</i> . Removed STM32F205xx in <i>Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS)</i> . Removed support of I2C for OTG PHY in <i>Section 3.29: Universal serial bus on-the-go high-speed (OTG_HS)</i> . Removed OTG_HS_SCL, OTG_HS_SDA, OTG_FS_INTN in <i>Table 8: STM32F20x pin and ball definitions</i> and <i>Table 10: Alternate function mapping</i> . Renamed PH10 alternate function into TIM5_CH1 in <i>Table 10: Alternate function mapping</i> . Added <i>Table 9: FSMC pin definition</i> .



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Table 96. Document revision history (continued)

	I	le 96. Document revision history (continued)
Date	Revision	Changes
		Updated Note 1 in Table 14: General operating conditions, Note 2 in Table 15: Limitations depending on the operating power supply range, and Note 1 below Figure 21: Number of wait states versus f_{CPU} and V_{DD} range.
		Updated V _{POR/PDR} in <i>Table 19: Embedded reset and power control block characteristics</i> .
		Updated typical values in Table 24: Typical and maximum current consumptions in Standby mode and Table 25: Typical and maximum current consumptions in V_{BAT} mode.
		Updated Table 30: HSE 4-26 MHz oscillator characteristics and Table 31: LSE oscillator characteristics (f_{LSE} = 32.768 kHz).
	9 (cont'd)	Updated <i>Table 37: Flash memory characteristics</i> , <i>Table 38: Flash memory programming</i> , and <i>Table 39: Flash memory programming with V_{PP}</i> . Updated <i>Section : Output driving current</i> .
24-Apr-2012		Updated <i>Note 3</i> and removed note related to minimum hold time value in <i>Table 52: I²C characteristics</i> .
		Updated Table 64: Dynamics characteristics: Ethernet MAC signals for RMII.
		Updated <i>Note 1</i> , C _{ADC} , I _{VREF+} , and I _{VDDA} in <i>Table 66: ADC</i> characteristics.
		Updated <i>Note 3</i> and note concerning ADC accuracy vs. negative injection current in <i>Table 67: ADC accuracy</i> .
		Updated Note 1 in Table 68: DAC characteristics.
		Updated Section Figure 88.: UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm, package outline.
		Appendix A.1: Main applications versus package: removed number of address lines for FSMC/NAND in Table 101: Main applications versus package for STM32F2xxx microcontrollers.
		Appendix A.4: Ethernet interface solutions: updated Figure 92: Complete audio player solution 1 and Figure 93: Complete audio player solution 2.
		Changed minimum supply voltage from 1.65 to 1.8 V.
	10	Updated number of AHB buses in Section 2: Description and
		Section 3.12: Clocks and startup. Removed Figure 4. Compatible board design between STM32F10xx and
29-Oct-2012		STM32F2xx for LQFP176 package.
		Updated Note 2 below Figure 4: STM32F20x block diagram.
		Changed System memory to System memory + OTP in <i>Figure 16: Memory map</i> .
		Added Note 1 below Table 16: VCAP1/VCAP2 operating conditions.
		Updated V _{DDA} and V _{REF+} decoupling capacitor in <i>Figure 19: Power</i> supply scheme and updated <i>Note 3</i> .
		Changed simplex mode into half-duplex mode in Section 3.24: Inter- integrated sound (I ² S).
		Replaced DAC1_OUT and DAC2_OUT by DAC_OUT1 and DAC_OUT2, respectively.Changed TIM2_CH1/TIM2_ETR into TIM2_CH1_ETR for PA0 and PA5 in <i>Table 10: Alternate function mapping</i> .



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Table 96. Document revision history (continued)

Date	Revision	Changes
29-Oct-2012	10 (cont'd)	Updated note applying to I _{DD} (external clock and all peripheral disabled) in Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled). Updated Note 3 below Table 22: Typical and maximum current consumption in Sleep mode. Removed fi _{HSE_ext} typical value in Table 28: High-speed external user clock characteristics. Updated master I2S clock jitter conditions and values in Table 35: PLLI2S (audio PLL) characteristics. Updated equations in Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics. Updated V _{IL} (NRST) and V _{IH} (NRST) in Table 49: NRST pin characteristics. Updated V _{IL} (NRST) and V _{IH} (NRST) in Table 49: NRST pin characteristics. Updated Table 54: SPI characteristics and Table 55: I ² S characteristics. Updated Table 54: SPI characteristics and Table 55: I ² S characteristics. Updated Table 54: SPI characteristics and Table 55: I ² S characteristics. Removed note 1 related to measurement points below Figure 43: SPI timing diagram - Slave mode and CPHA = 1, Figure 44: SPI timing diagram - Master mode, and Figure 45: I ² S slave timing diagram (Philips protocol) ⁽¹¹⁾ . Updated Table 61: ULPI timing. Updated Figure 49: Ethernet SMI timing diagram, Table 63: Dynamics characteristics: Ethernet MAC signals for SMI and Table 65: Dynamics characteristics: Ethernet MAC signals for MII. Updated I _{DDA} description in Table 68: DAC characteristics. Updated note below Figure 54: Power supply and reference decoupling (V _{REF+} not connected to V _{DDA}) and Figure 55: Power supply and reference decoupling (V _{REF+} ton connected to V _{DDA}). Replaced t _d (CLK-NOEL) by t _d (CLK-NOEL) in Table 76: Synchronous nonmultiplexed NOR/PSRAM read timings, Table 78: Synchronous nonmultiplexed NOR/PSRAM read timings, Table 78: Synchronous nonmultiplexed NOR/PSRAM read timings. Added Figure 87: LQFP176 recommended footprint. Added Note 2 below Figure 86: Regulator OFF/internal reset ON. Updated device subfamily
04-Nov-2013	11	In the whole document, updated notes related to WLCSP64+2 usage with IRROFF set to V _{DD} . Updated Section 3.14: Power supply schemes, Section 3.15: Power supply supervisor, Section 3.16.1: Regulator ON and Section 3.16.2: Regulator OFF. Added Section 3.16.3: Regulator ON/OFF and internal reset ON/OFF availability. Added note related to WLCSP64+2 package. Restructured RTC features and added reference clock detection in Section 3.17: Real-time clock (RTC), backup SRAM and backup registers. Added V _{IN} in Table 14: General operating conditions.



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Table 96. Document revision history (continued)

Date	Revision	Changes
04-Nov-2013	11 (cont'd)	Added note indicating the package view below <i>Figure 10: STM32F20x LQFP64 pinout, Figure 12: STM32F20x LQFP100 pinout, Figure 13: STM32F20x LQFP144 pinout,</i> and <i>Figure 14: STM32F20x LQFP176 pinout.</i> Added <i>Table 7: Legend/abbreviations used in the pinout table. Table 8: STM32F20x pin and ball definitions:</i> content reformatted; removed indexes on V _{SS} and V _{DD} ; updated PA4, PA5, PA6, PC4, BOOT0; replaced DCMI_12 by DCMI_D12, TIMB_CHIN by TIMB_CH1N, ETH_MII_RX_D0 by ETH_MII_RX_D0. ETH_MII_RX_D1 by ETH_MII_RX_D0. ETH_MII_RX_D1 by ETH_MII_RX_D1. ETH_RMII_RX_D1. ETH_RM

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Table 96. Document revision history (continued)

Date	Revision	Changes
Date	I/GAI2IOU	· ·
27-Oct-2014	12	Updated V _{BAT} voltage range in <i>Figure 19: Power supply scheme</i> . Added caution note in <i>Section 6.1.6: Power supply scheme</i> . Updated V _{IN} in <i>Table 14: General operating conditions</i> . Removed note 1 in <i>Table 23: Typical and maximum current consumptions in Stop mode</i> . Updated <i>Table 45: I/O current injection susceptibility</i> , <i>Section 6.3.16: I/O port characteristics</i> and <i>Section 6.3.17: NRST pin characteristics</i> . Removed note 3 in <i>Table 69: Temperature sensor characteristics</i> . Updated <i>Figure 79: WLCSP64+2 - 0.400 mm pitch wafer level chip size package outline</i> and <i>Table 88: WLCSP64+2 - 0.400 mm pitch wafer level chip size package mechanical data</i> . Added <i>Figure 84: LQFP100 marking (package top view)</i> and <i>Figure 87: LQFP144 marking (package top view)</i> .
2-Feb-2016	13	Updated Section 1: Introduction. Updated Table 32: HSI oscillator characteristics and its footnotes. Updated Figure 36: PLL output clock waveforms in center spread mode, Figure 37: PLL output clock waveforms in down spread mode, Figure 54: Power supply and reference decoupling (V_{REF+} not connected to V_{DDA}) and Figure 55: Power supply and reference decoupling (V_{REF+} connected to V_{DDA}). Updated Section 7: Package information and its subsections.
24-Jun-2016	14	Updated figures 1, 2 and 3 in Section 2.1: Full compatibility throughout the family. Updated Device marking and Figure 84 in Section 7.3: LQFP100 package information. Updated Device marking and Figure 87 in Section 7.4: LQFP144 package information. Updated Section 7.6: UFBGA176+25 package information with introduction of Device marking and Figure 92. Updated Table 96: Ordering information scheme.
11-Aug-2016	15	Updated Features, Section 7.2: WLCSP64+2 package information and title of Section 8: Ordering information. Updated Figure 54: Power supply and reference decoupling (V_{REF+} not connected to V_{DDA}).
29-Mar-2019	16	Updated Section 1: Introduction and Section 2: Description. Updated Table 72: Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings. Updated Figure 38: FT I/O input characteristics. Updated paragraph introducing all package marking schematics to add the new sentence "The printed markings may differ depending on the supply chain". Minor text edits across the whole document.
26-Nov-2019	17	Updated caption of figures and tables in Section 7: Package information.



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Table 96. Document revision history (continued)

Date	Revision	Changes
02-Jul-2020	18	Updated Section 3.29: Universal serial bus on-the-go high-speed (OTG_HS). Updated Table 19: Embedded reset and power control block characteristics, Table 48: I/O AC characteristics and Table 80: Switching characteristics for PC Card/CF read and write cycles in attribute/common space. Added footnote 2 to Table 8: STM32F20x pin and ball definitions and updated footnote 1 of Table 32: HSI oscillator characteristics. Added Device marking. Minor text edits across the whole document.

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